Rethinking Memory System Design

(and the Platforms We Design Around It)

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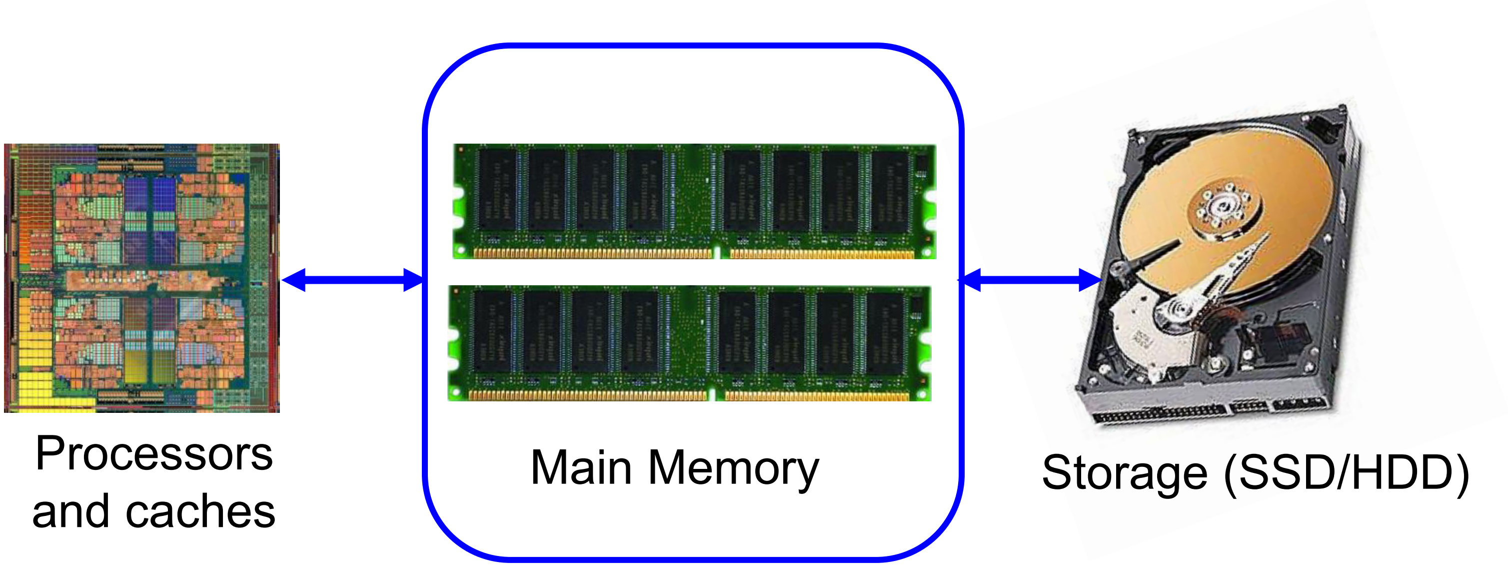
January 17, 2018

Many-Core Computing: Hardware and Software

The Main Memory System



Processors
and caches

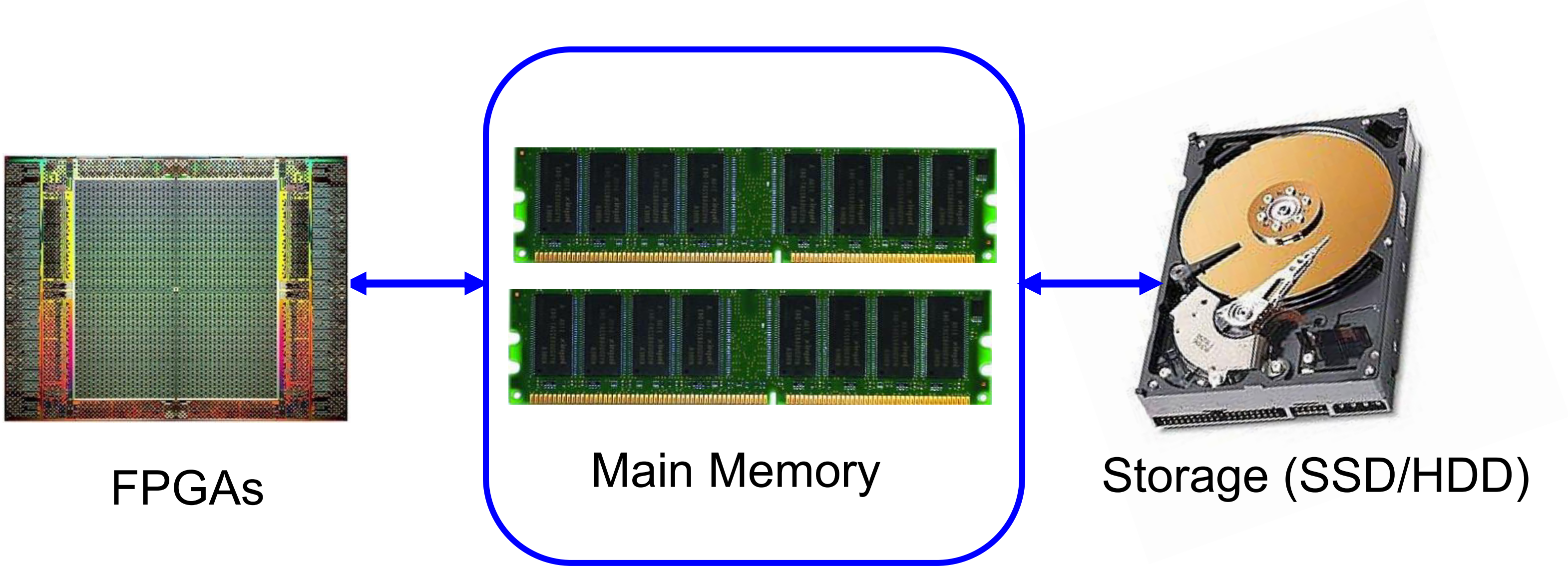
Main Memory

Storage (SSD/HDD)

- Main memory is a critical component of all computing systems: server, mobile, embedded, desktop, sensor

- Main memory system must scale (in *size*, *technology*, *efficiency*, *cost*, and *management algorithms*) to maintain performance growth and technology scaling benefits

The Main Memory System



FPGAs

Main Memory

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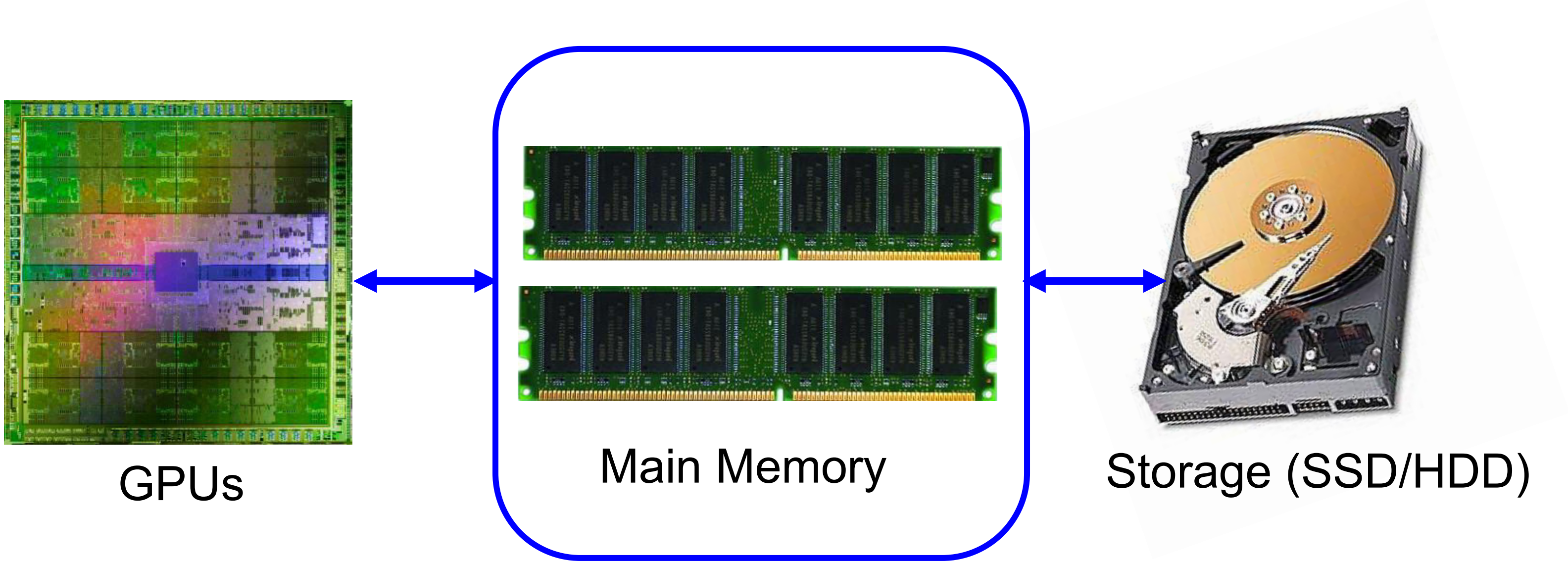

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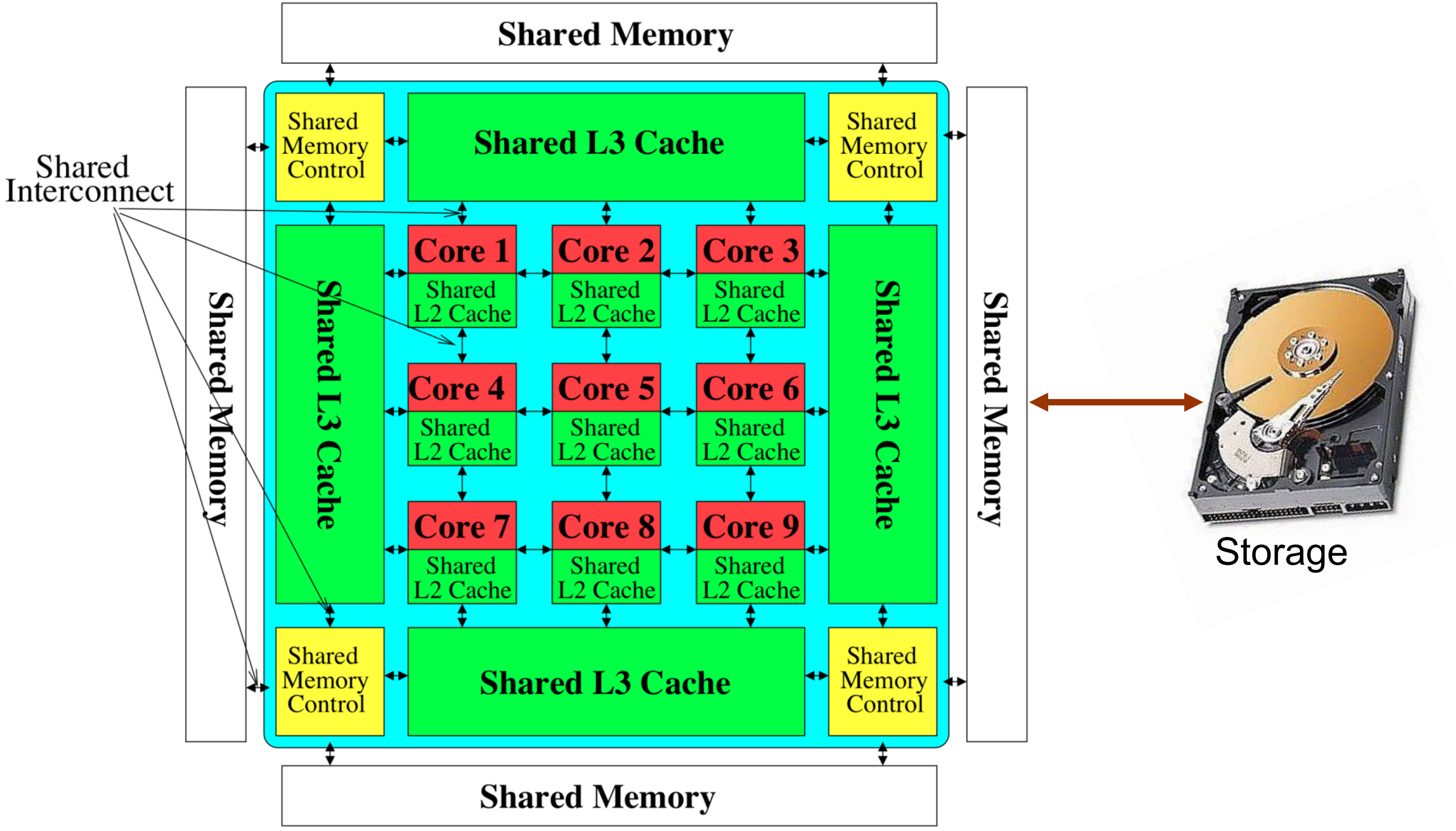
Memory System: A ***Shared Resource*** View



Most of the system is dedicated to storing and moving data

State of the Main Memory System

- Recent technology, architecture, and application trends
  - lead to new requirements
  - exacerbate old requirements

- DRAM and memory controllers, as we know them today, are (will be) unlikely to satisfy all requirements

- Some emerging non-volatile memory technologies (e.g., PCM) enable new opportunities: memory+storage merging

- We need to rethink the main memory system
  - to fix DRAM issues and enable emerging technologies
  - to satisfy all requirements

Agenda

- Major Trends Affecting Main Memory
- The Memory Scaling Problem and Solution Directions
  - New Memory Architectures
  - Enabling Emerging (NVM) Technologies
- Cross-Cutting Principles
- Summary

Major Trends Affecting Main Memory (I)

- Need for main memory capacity, bandwidth, QoS increasing

- Main memory energy/power is a key system design concern

- DRAM technology scaling is ending

Major Trends Affecting Main Memory (II)

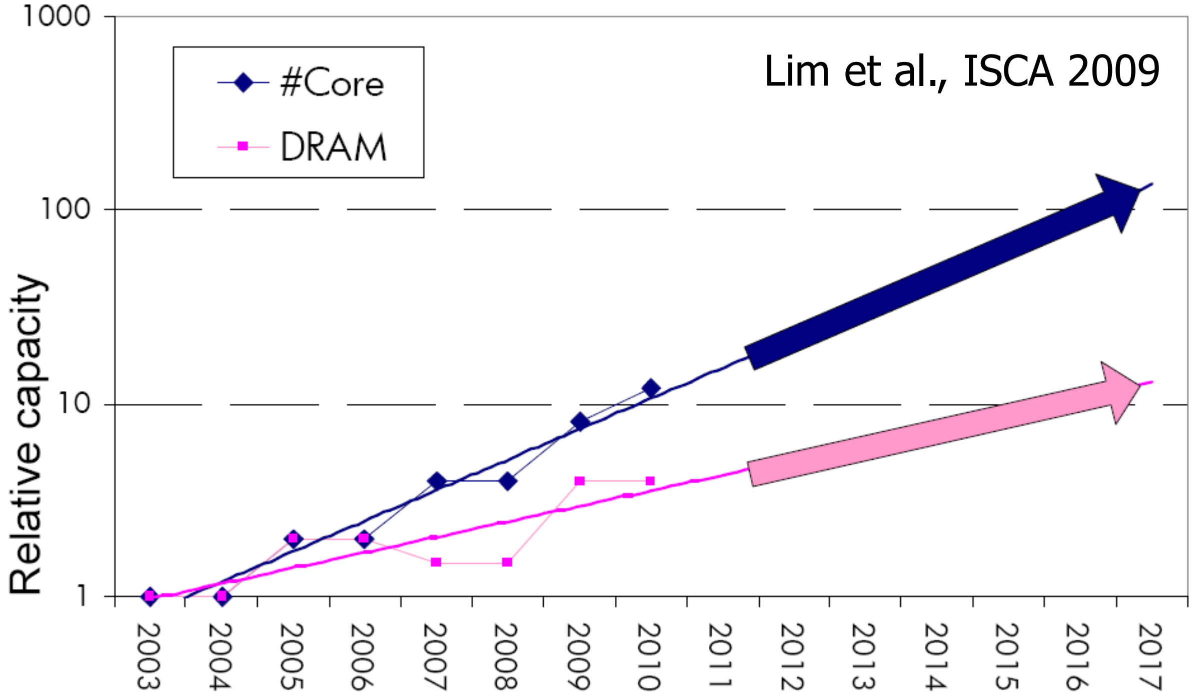
- Need for main memory capacity, bandwidth, QoS increasing
  - Multi-core: increasing number of cores/agents
  - Data-intensive applications: increasing demand/hunger for data
  - Consolidation: cloud computing, GPUs, mobile, heterogeneity

- Main memory energy/power is a key system design concern

- DRAM technology scaling is ending

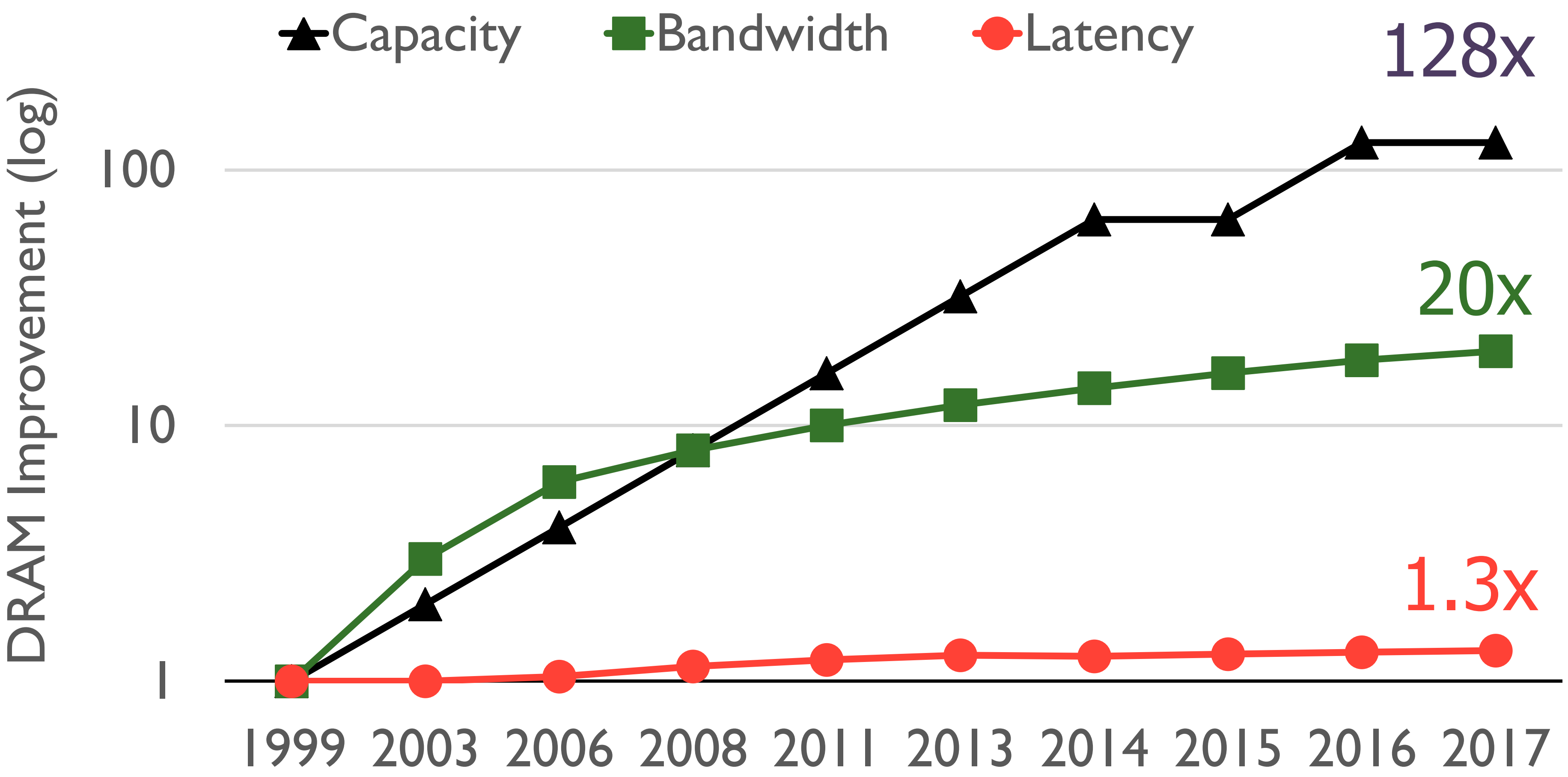
Example: The Memory Capacity Gap

Core count doubling ~ every 2 years
DRAM DIMM capacity doubling ~ every 3 years



- *Memory capacity per core* expected to drop by 30% every two years
- Trends worse for *memory bandwidth per core*!

DRAM Capacity, Bandwidth, Latency Trends



Memory latency remains almost constant

DRAM Latency Is Critical for Performance

In-memory Databases

[Mao+, EuroSys'12;
Clapp+ (**Intel**), IISWC'15]

Graph/Tree Processing

[Xu+, IISWC'12; Umuroglu+, FPL'15]

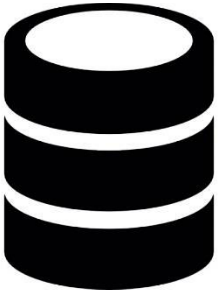
In-Memory Data Analytics

[Clapp+ (**Intel**), IISWC'15;
Awan+, BDCloud'15]

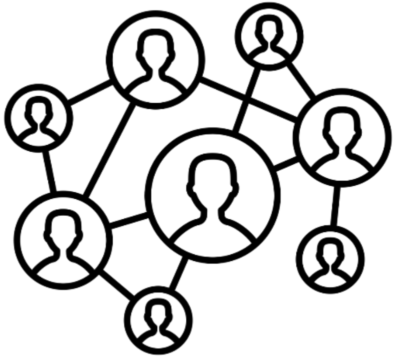
Datacenter Workloads

[Kanev+ (**Google**), ISCA'15]

DRAM Latency Is Critical for Performance



In-memory Databases

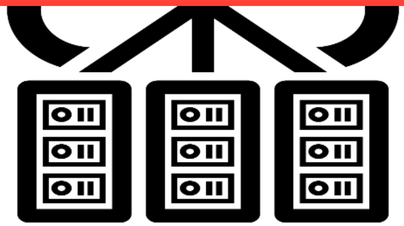


Graph/Tree Processing

Long memory latency → performance bottleneck

In-Memory Data Analytics

[Clapp+ (**Intel**), IISWC'15;
Awan+, BDCloud'15]



Datacenter Workloads

[Kanev+ (**Google**), ISCA'15]

Major Trends Affecting Main Memory (III)

- Need for main memory capacity, bandwidth, QoS increasing

- Main memory energy/power is a key system design concern
  - ~40-50% energy spent in off-chip memory hierarchy [Lefurgy, IEEE Computer'03] >40% power in DRAM [Ware, HPCA'10][Paul,ISCA'15]
  - DRAM consumes power even when not used (periodic refresh)

- DRAM technology scaling is ending

Major Trends Affecting Main Memory (IV)

- Need for main memory capacity, bandwidth, QoS increasing

- Main memory energy/power is a key system design concern

- DRAM technology scaling is ending
  - ITRS projects DRAM will not scale easily below X nm
  - Scaling has provided many benefits:
    - higher capacity (density), lower cost, lower energy

Major Trends Affecting Main Memory (V)

- DRAM scaling has already become increasingly difficult
  - Increasing cell leakage current, reduced cell reliability, increasing manufacturing difficulties [Kim+ ISCA 2014], [Liu+ ISCA 2013], [Mutlu IMW 2013], [Mutlu DATE 2017]
  - **Difficult to significantly improve capacity, energy**

- **Emerging memory technologies** are promising

Major Trends Affecting Main Memory (V)

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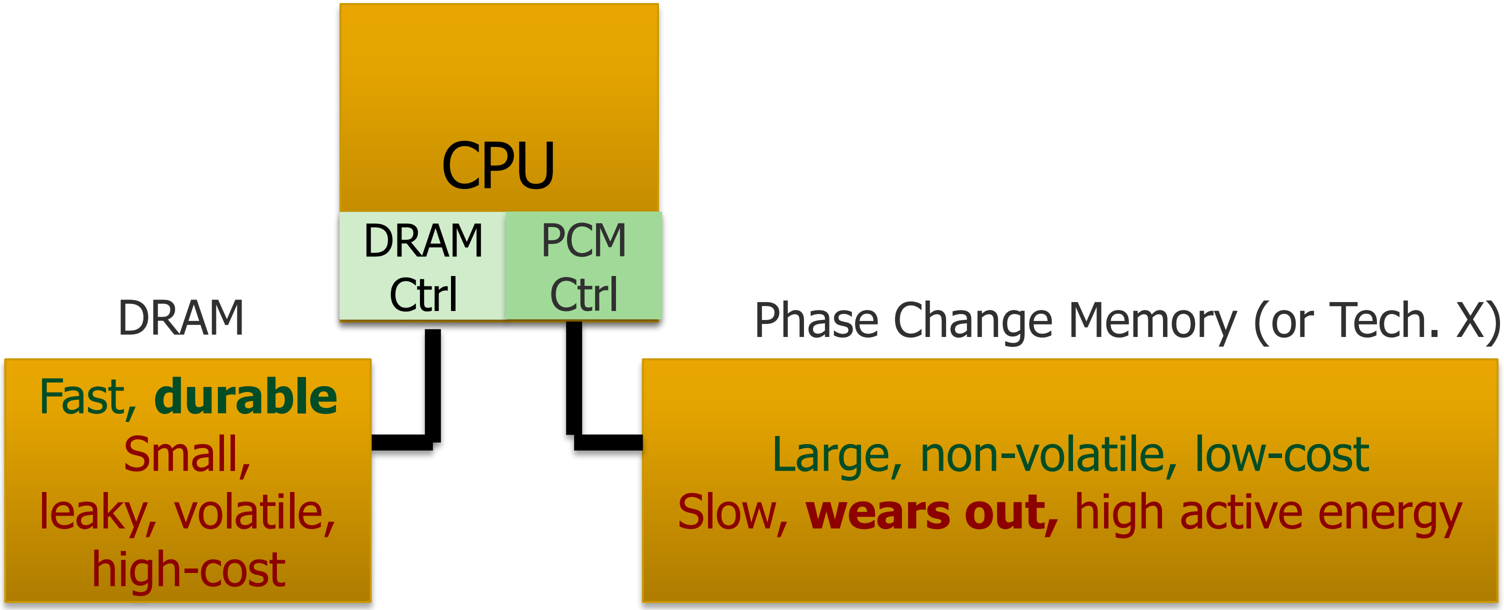
  - **Difficult to significantly improve capacity, energy**

- **Emerging memory technologies** are promising

3D-Stacked DRAM	higher bandwidth	smaller capacity
Reduced-Latency DRAM (e.g., RL/TL-DRAM, FLY-RAM)	lower latency	higher cost
Low-Power DRAM (e.g., LPDDR3, LPDDR4, Voltron)	lower power	higher latency higher cost
Non-Volatile Memory (NVM) (e.g., PCM, STTRAM, ReRAM, 3D Xpoint)	larger capacity	higher latency higher dynamic power lower endurance

Major Trend: Hybrid Main Memory


CPU

DRAM Ctrl

PCM Ctrl

DRAM

Fast, **durable**
Small,
leaky, volatile,
high-cost

Phase Change Memory (or Tech. X)

Large, non-volatile, low-cost
Slow, **wears out,** high active energy

Hardware/software manage data allocation and movement
to achieve the best of multiple technologies

Meza+, "Enabling Efficient and Scalable Hybrid Memories," IEEE Comp. Arch. Letters, 2012.

Yoon+, "Row Buffer Locality Aware Caching Policies for Hybrid Memories," ICCD 2012 Best Paper Award.

One Foreshadowing

Main Memory Needs

Intelligent Controllers

Agenda

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Three Key Issues in Future Platforms

- Fundamentally Secure/Reliable/Safe Architectures

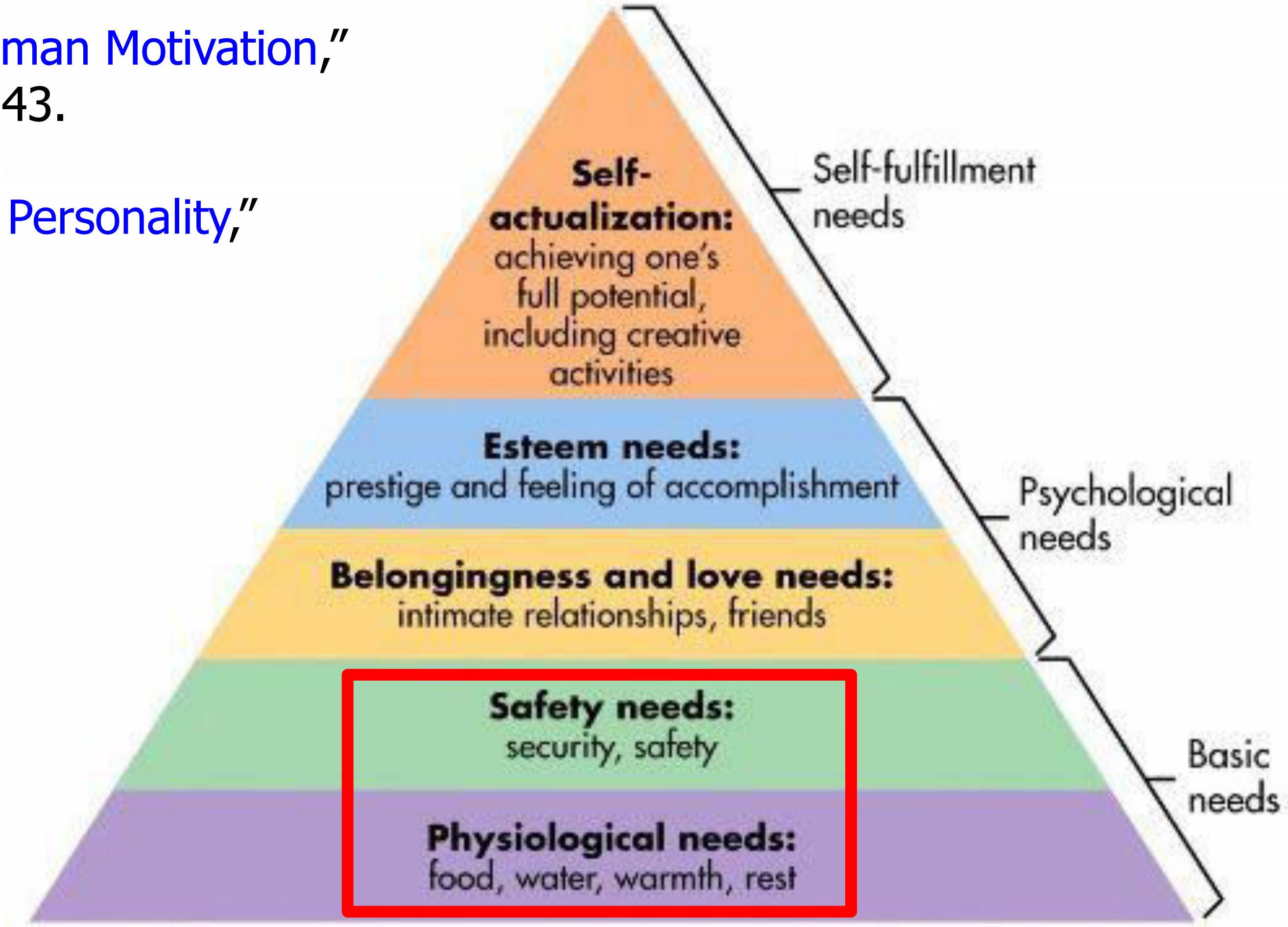
- Fundamentally Energy-Efficient Architectures
  - Memory-centric (Data-centric) Architectures

- Fundamentally Low Latency Architectures

Maslow's (Human) Hierarchy of Needs

Maslow, "A Theory of Human Motivation," Psychological Review, 1943.

Maslow, "Motivation and Personality," Book, 1954-1970.



- We need to start with reliability and security…

Source: https://www.simplypsychology.org/maslow.html

How Reliable/Secure/Safe is This Bridge?

Source: http://www.technologystudent.com/struct1/tacom1.png

Collapse of the "Galloping Gertie"

Source: AP

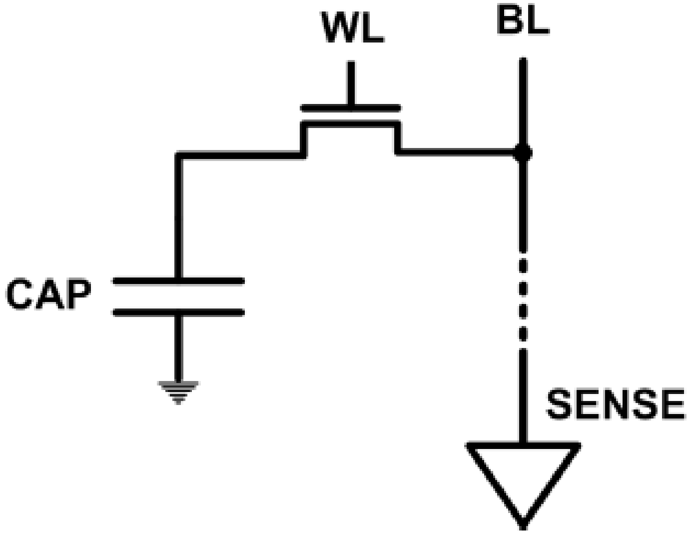
How Secure Are These People?

Security is about preventing unforeseen consequences

Source: https://s-media-cache-ak0.pinimg.com/originals/48/09/54/4809543a9c7700246a0cf8acdae27abf.jpg

The DRAM Scaling Problem

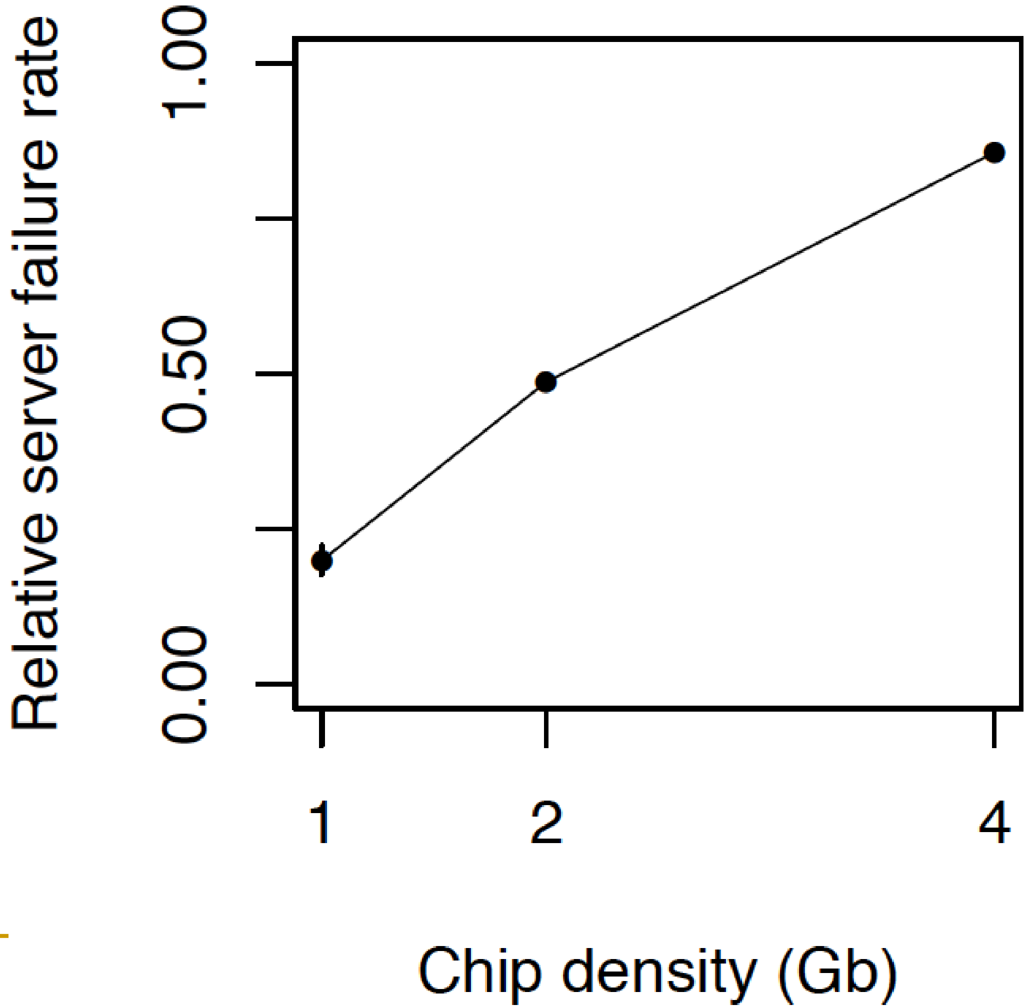
- DRAM stores charge in a capacitor (charge-based memory)
  - Capacitor must be large enough for reliable sensing
  - Access transistor should be large enough for low leakage and high retention time
  - Scaling beyond 40-35nm (2013) is challenging [ITRS, 2009]



- DRAM capacity, cost, and energy/power hard to scale

As Memory Scales, It Becomes Unreliable

- Data from all of Facebook's servers worldwide
- Meza+, "Revisiting Memory Errors in Large-Scale Production Data Centers," DSN'15.

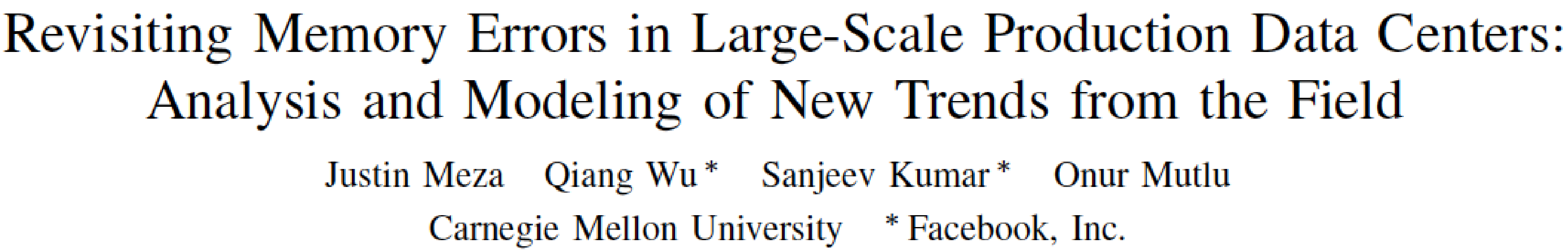


Intuition: *quadratic increase in capacity*

Large-Scale Failure Analysis of DRAM Chips

- Analysis and modeling of memory errors found in all of Facebook’s server fleet

- Justin Meza, Qiang Wu, Sanjeev Kumar, and Onur Mutlu, **"Revisiting Memory Errors in Large-Scale Production Data Centers: Analysis and Modeling of New Trends from the Field"** *Proceedings of the 45th Annual IEEE/IFIP International Conference on Dependable Systems and Networks (**DSN**)*, Rio de Janeiro, Brazil, June 2015.
  [Slides (pptx) (pdf)] [DRAM Error Model]



Revisiting Memory Errors in Large-Scale Production Data Centers: Analysis and Modeling of New Trends from the Field

Justin Meza Qiang Wu* Sanjeev Kumar* Onur Mutlu
Carnegie Mellon University *Facebook, Inc.

Infrastructures to Understand Such Issues

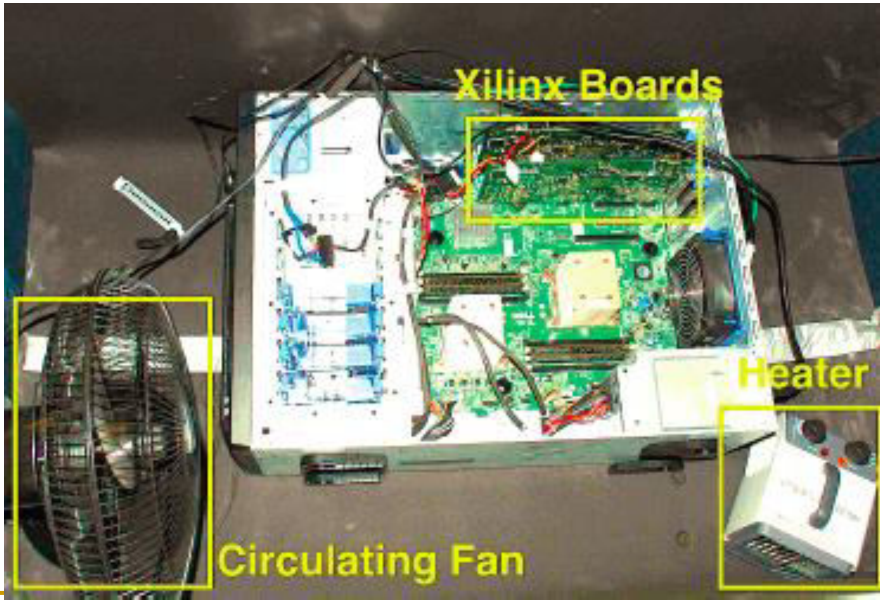
An Experimental Study of Data Retention Behavior in Modern DRAM Devices: Implications for Retention Time Profiling Mechanisms (Liu et al., ISCA 2013)

The Efficacy of Error Mitigation Techniques for DRAM Retention Failures: A Comparative Experimental Study (Khan et al., SIGMETRICS 2014)

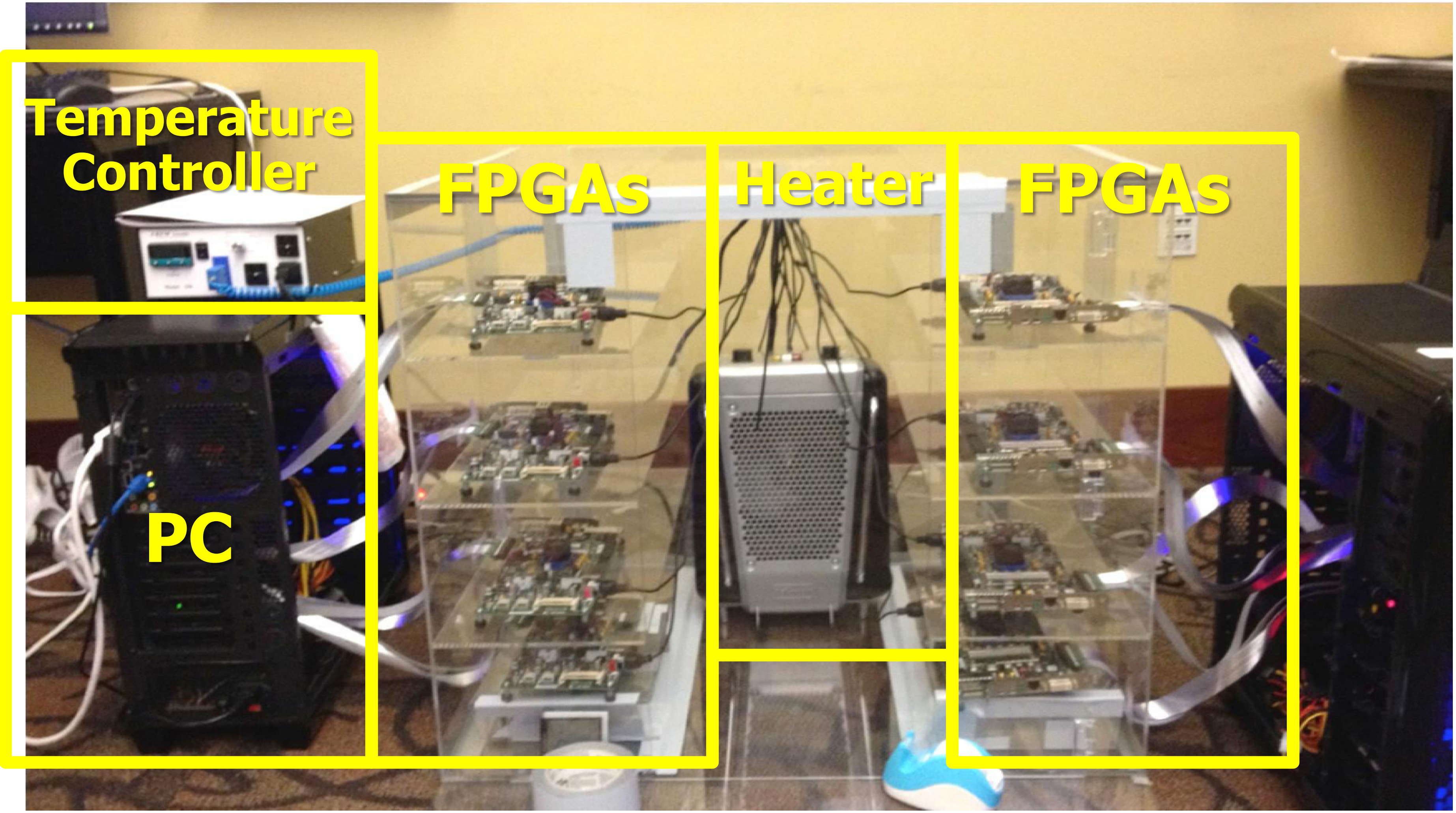
Flipping Bits in Memory Without Accessing Them: An Experimental Study of DRAM Disturbance Errors (Kim et al., ISCA 2014)

Adaptive-Latency DRAM: Optimizing DRAM Timing for the Common-Case (Lee et al., HPCA 2015)

AVATAR: A Variable-Retention-Time (VRT) Aware Refresh for DRAM Systems (Qureshi et al., DSN 2015)



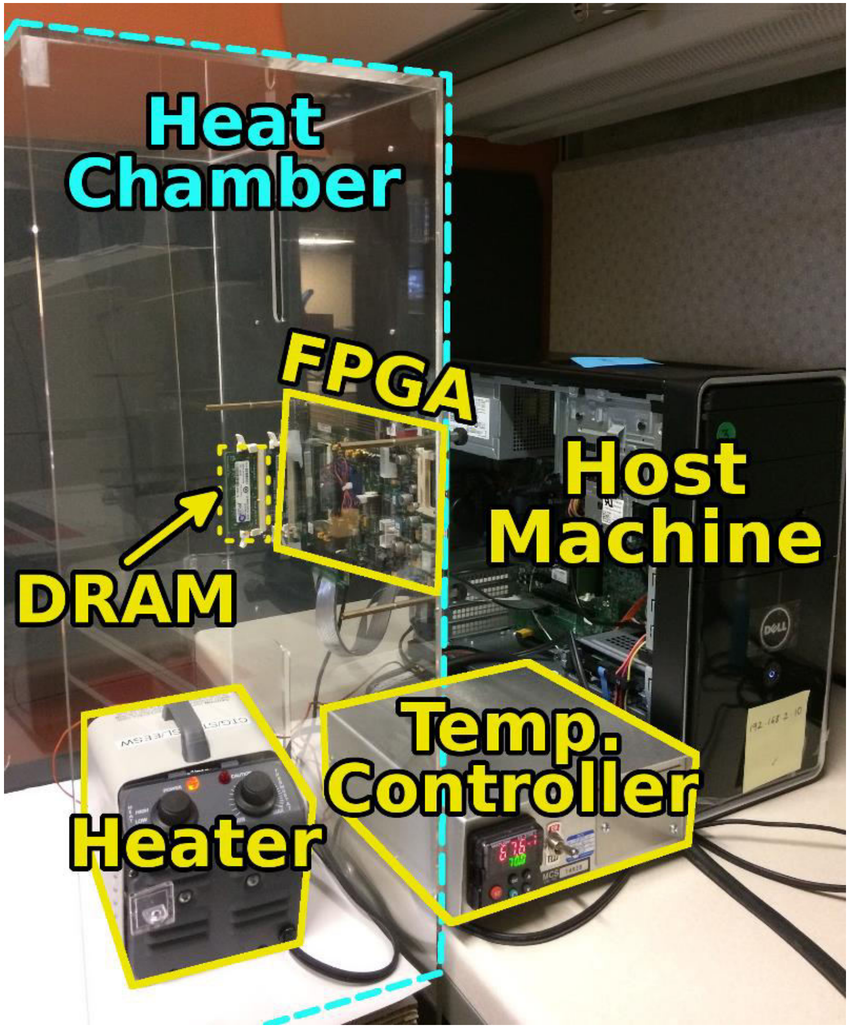
Infrastructures to Understand Such Issues



Kim+, “Flipping Bits in Memory Without Accessing Them: An Experimental Study of DRAM Disturbance Errors,” ISCA 2014.

SoftMC: Open Source DRAM Infrastructure

- Hasan Hassan et al., "**SoftMC: A Flexible and Practical Open-Source Infrastructure for Enabling Experimental DRAM Studies**," HPCA 2017.

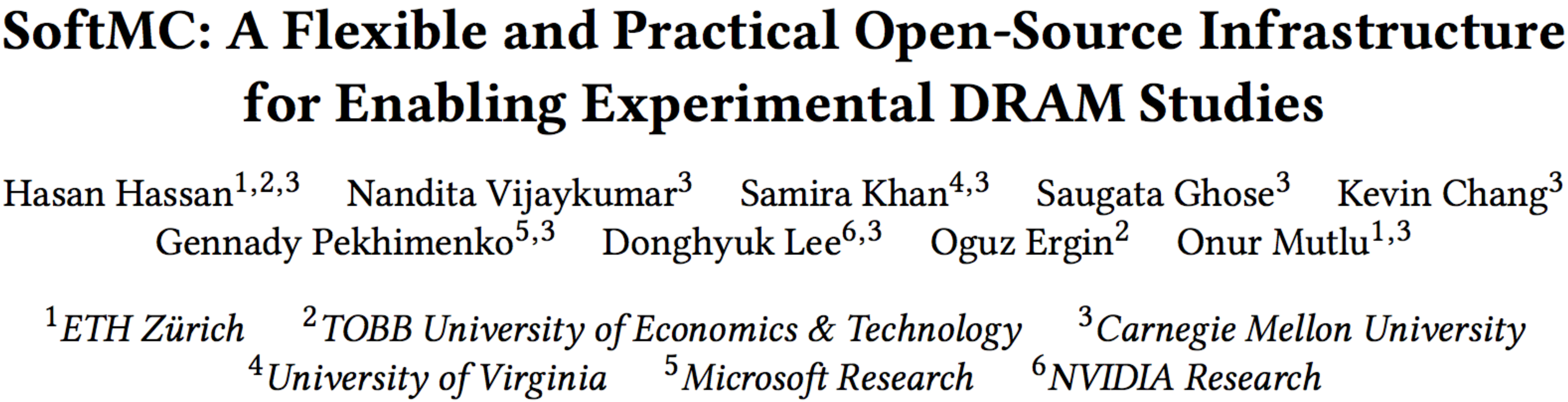


- **Flexible**
- **Easy to Use (C++ API)**
- **Open-source**

github.com/CMU-SAFARI/SoftMC

SoftMC

- https://github.com/CMU-SAFARI/SoftMC



SoftMC: A Flexible and Practical Open-Source Infrastructure for Enabling Experimental DRAM Studies

Hasan Hassan[1,2,3] Nandita Vijaykumar[3] Samira Khan[4,3] Saugata Ghose[3] Kevin Chang[3]
Gennady Pekhimenko[5,3] Donghyuk Lee[6,3] Oguz Ergin[2] Onur Mutlu[1,3]

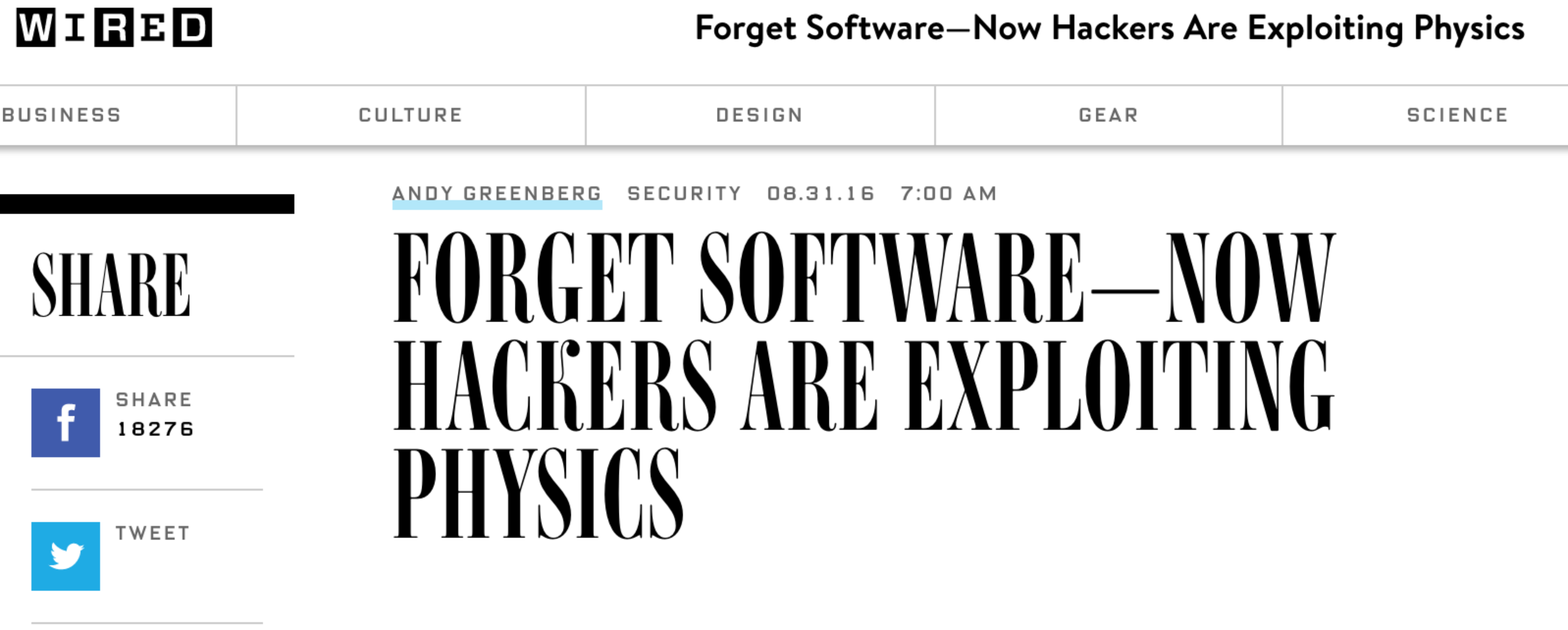
[1]*ETH Zürich* [2]*TOBB University of Economics & Technology* [3]*Carnegie Mellon University*
[4]*University of Virginia* [5]*Microsoft Research* [6]*NVIDIA Research*

A Curious Discovery **[Kim et al., ISCA 2014]**

One can
predictably induce errors
in most DRAM memory chips

DRAM RowHammer

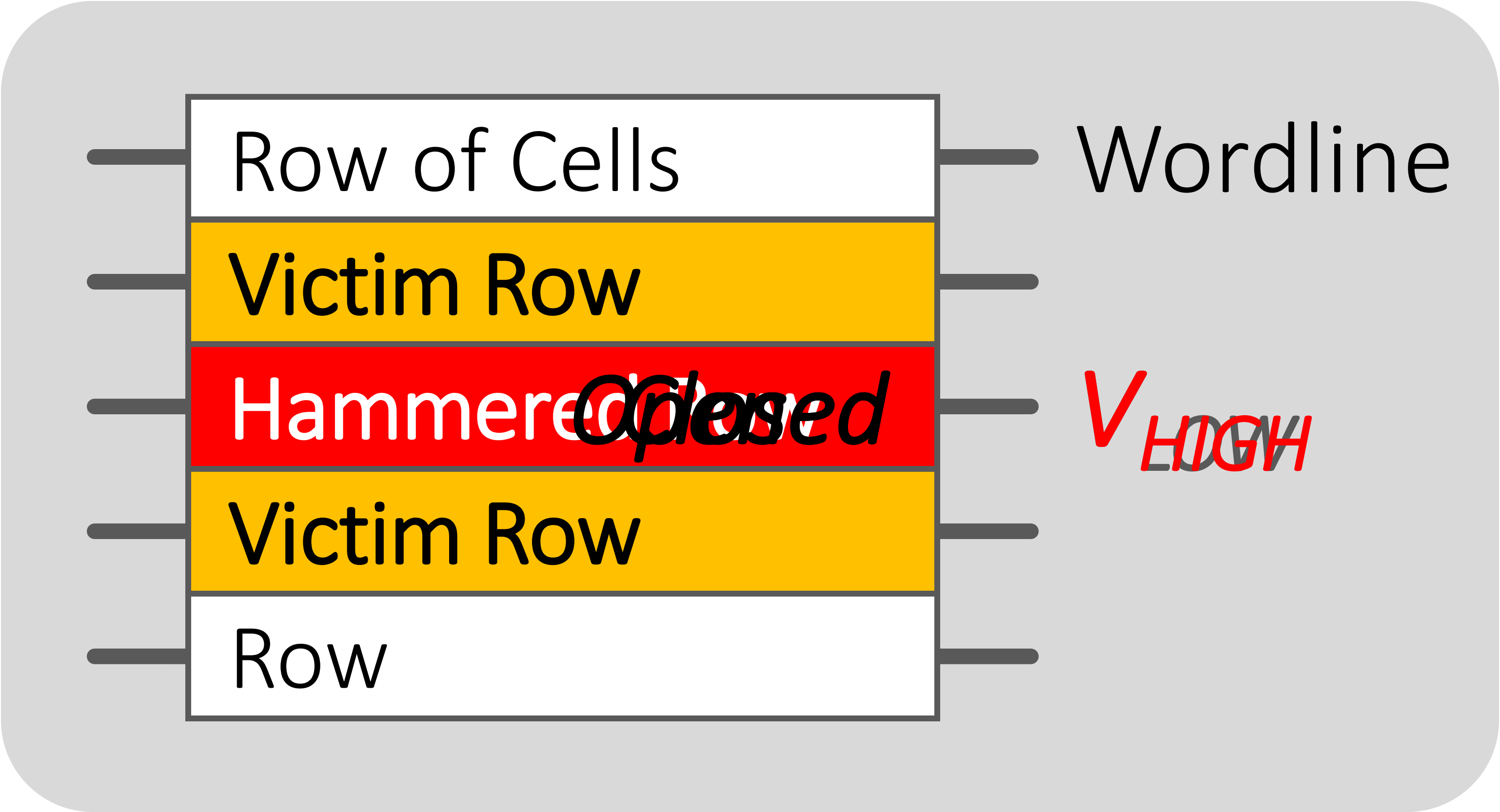
A simple hardware failure mechanism can create a widespread system security vulnerability



ANDY GREENBERG SECURITY 08.31.16 7:00 AM

FORGET SOFTWARE—NOW HACKERS ARE EXPLOITING PHYSICS

Modern DRAM is Prone to Disturbance Errors


Row of Cells

Victim Row

Hammered Row

Opened

Closed

Victim Row

Row

Wordline

V_{LOW}

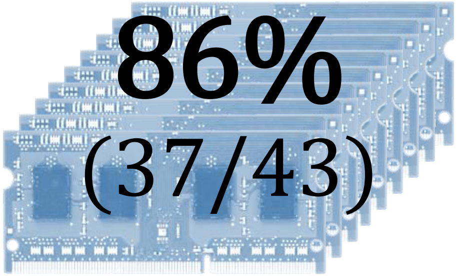
V_{HIGH}

Repeatedly reading a row enough times (before memory gets refreshed) induces disturbance errors in **adjacent rows** in most real DRAM chips you can buy today

Flipping Bits in Memory Without Accessing Them: An Experimental Study of DRAM Disturbance Errors, (Kim et al., ISCA 2014)

Most DRAM Modules Are at Risk

A company



86%

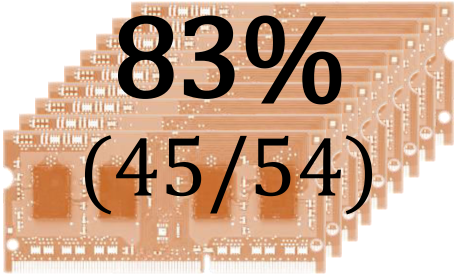
(37/43)

Up to

1.0×10^7

errors

B company



83%

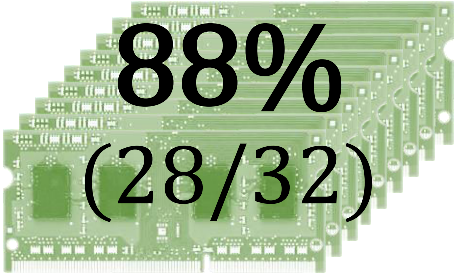
(45/54)

Up to

2.7×10^6

errors

C company



88%

(28/32)

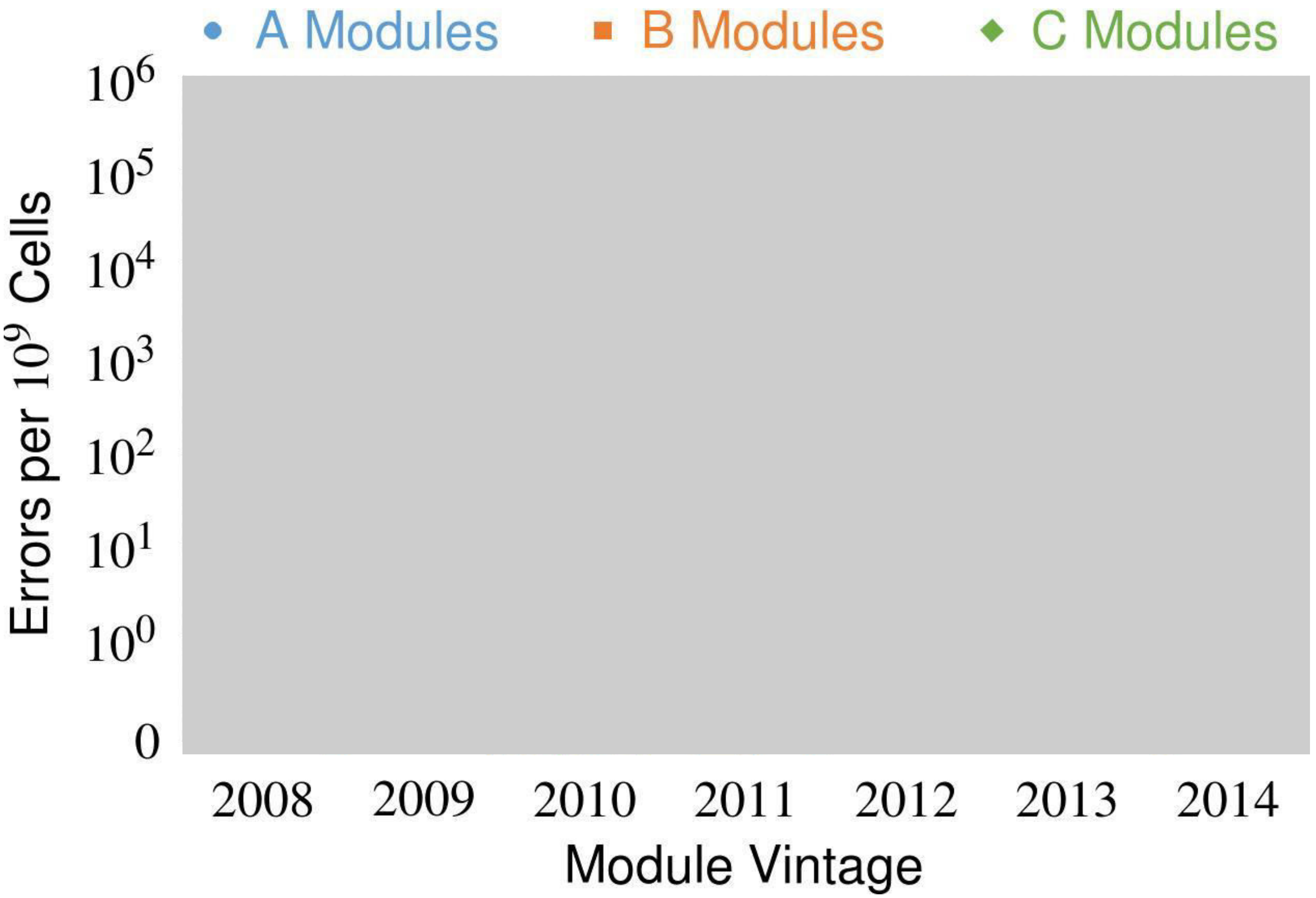
Up to

3.3×10^5

errors

[Flipping Bits in Memory Without Accessing Them: An Experimental Study of DRAM Disturbance Errors](), (Kim et al., ISCA 2014)

Recent DRAM Is More Vulnerable



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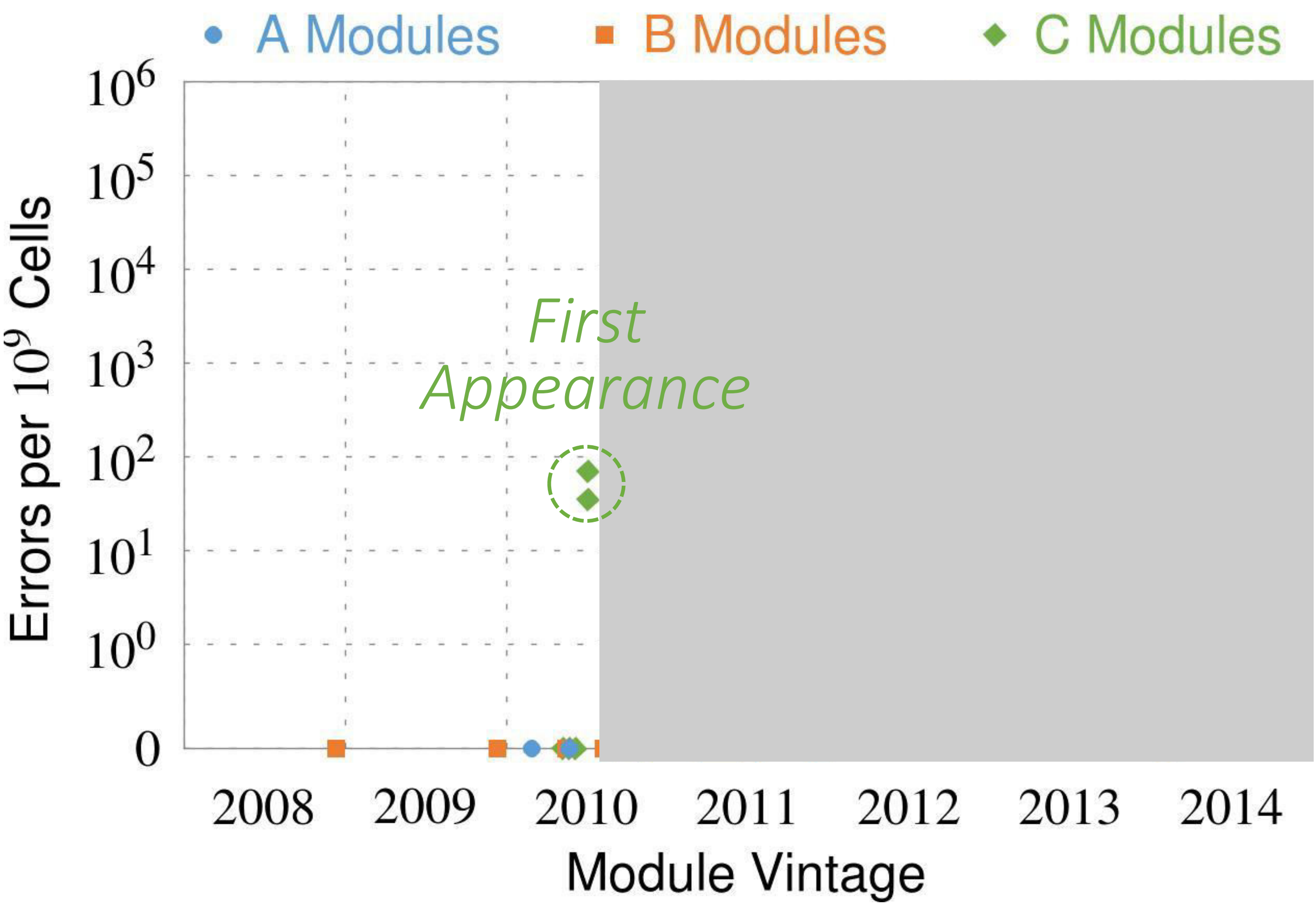

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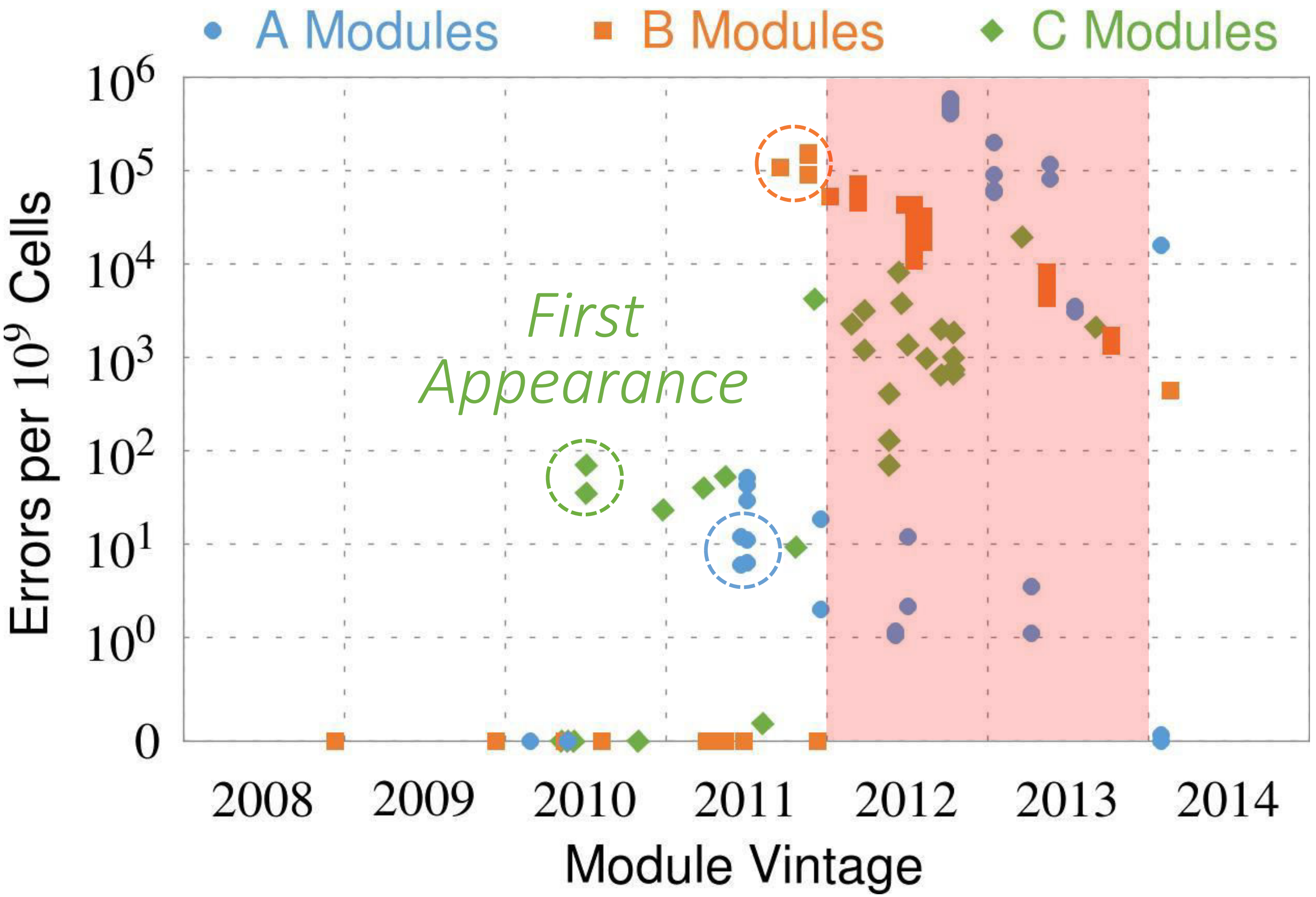
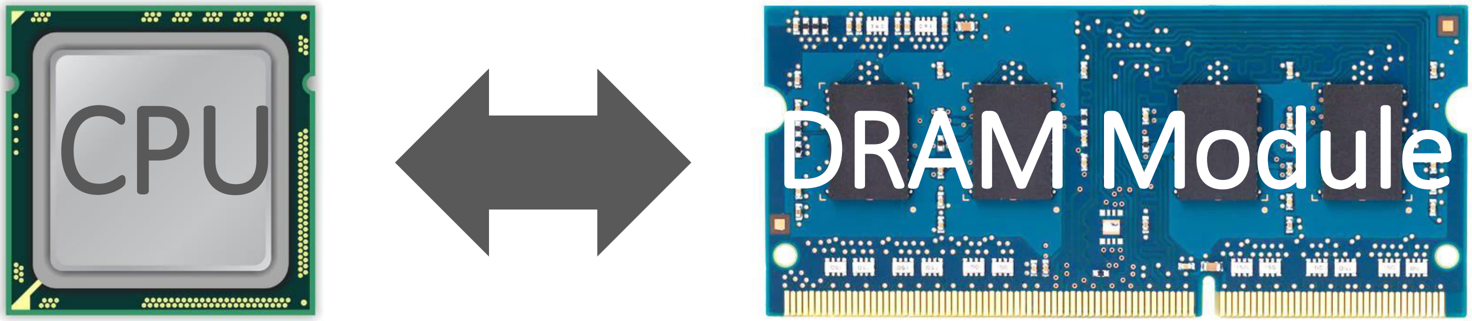


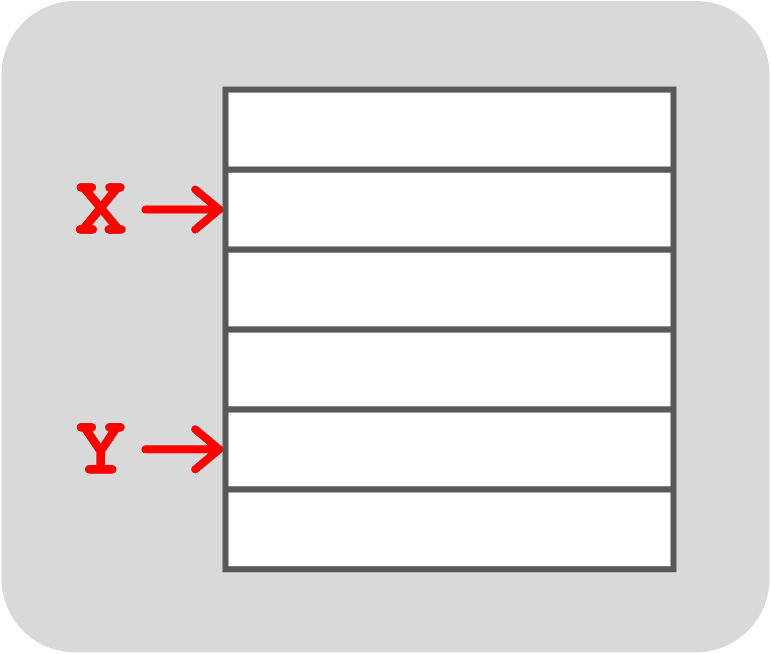
First Appearance

All modules from 2012–2013 are vulnerable

A Simple Program Can Induce Many Errors

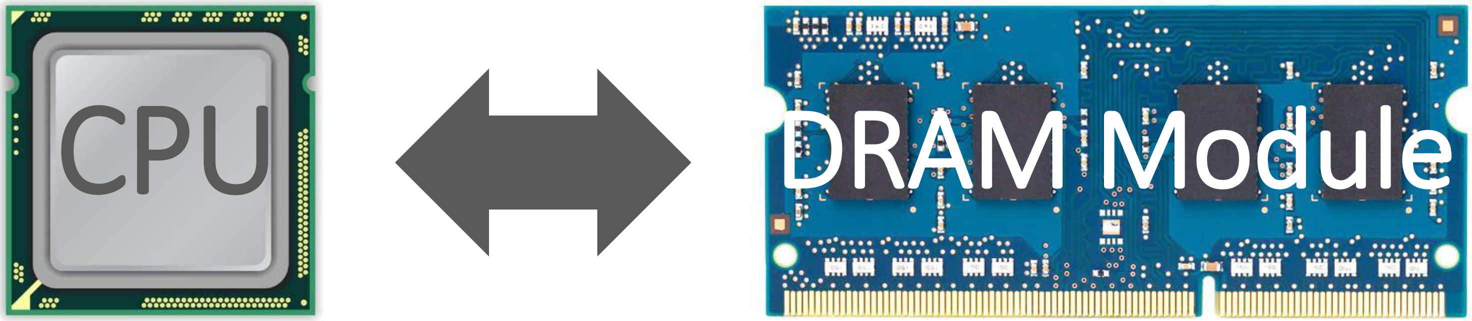


```
loop:
  mov (X), %eax
  mov (Y), %ebx
  clflush (X)
  clflush (Y)
  mfence
  jmp loop
```



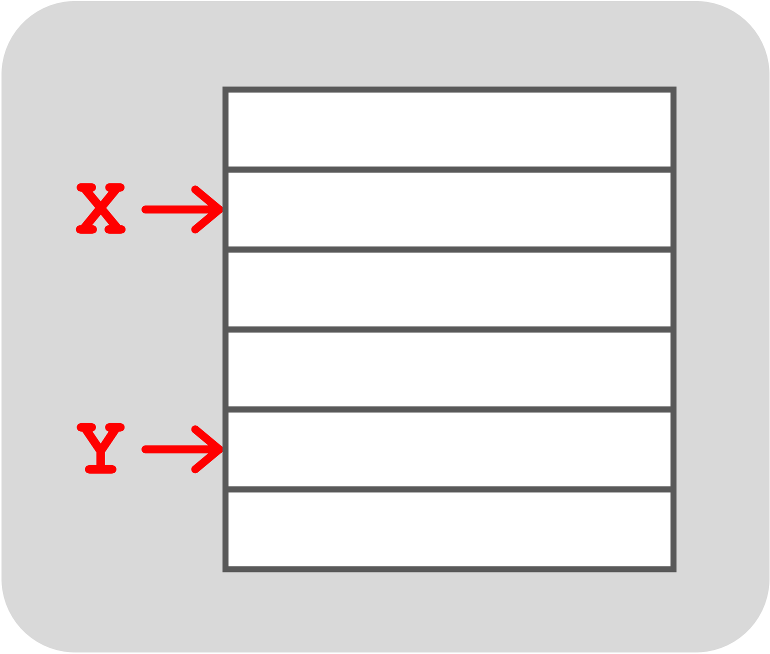
Download from: https://github.com/CMU-SAFARI/rowhammer

A Simple Program Can Induce Many Errors



1. Avoid ***cache hits***
   – Flush **X** from cache

2. Avoid ***row hits*** to **X**
   – Read **Y** in another row



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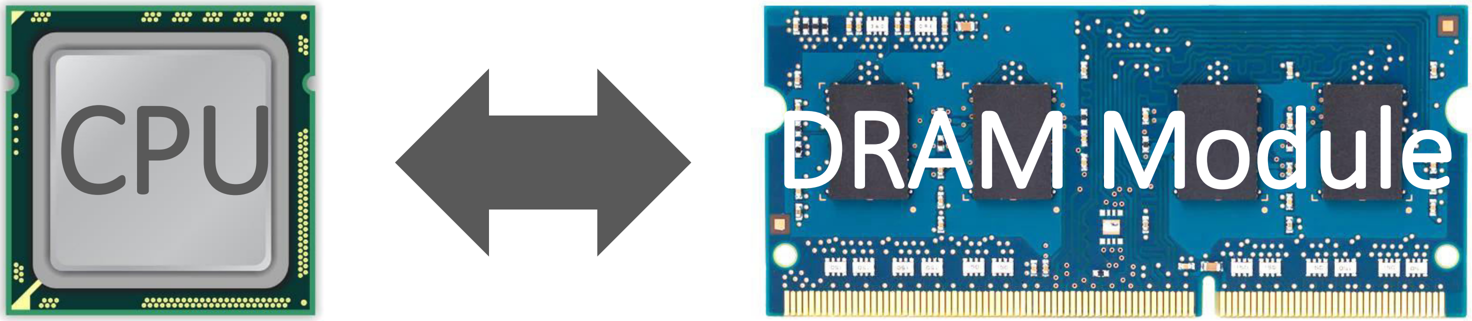

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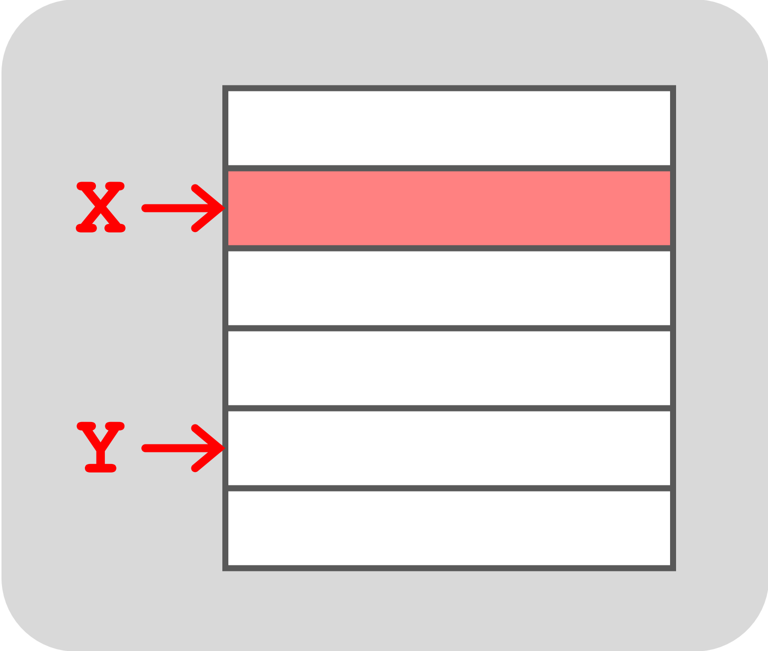

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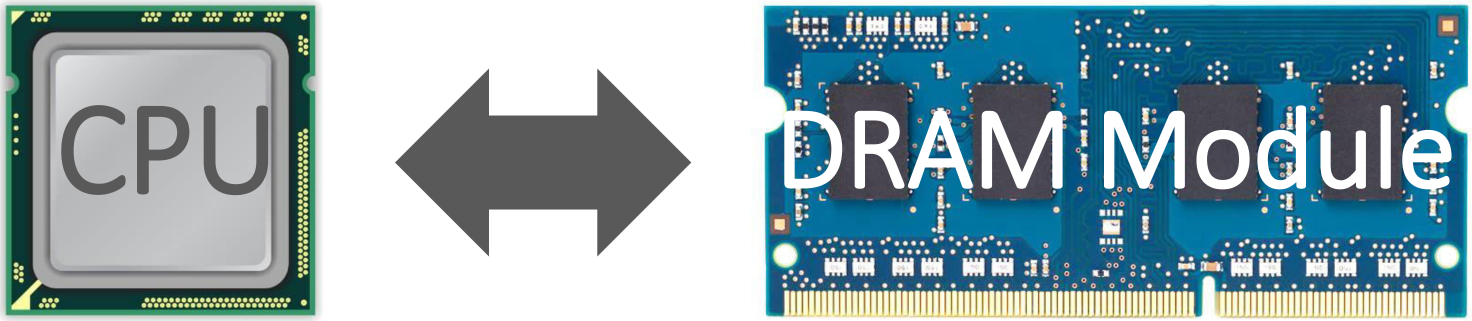

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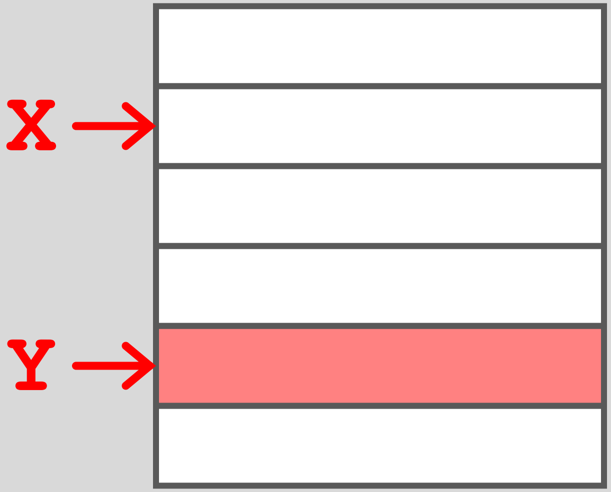

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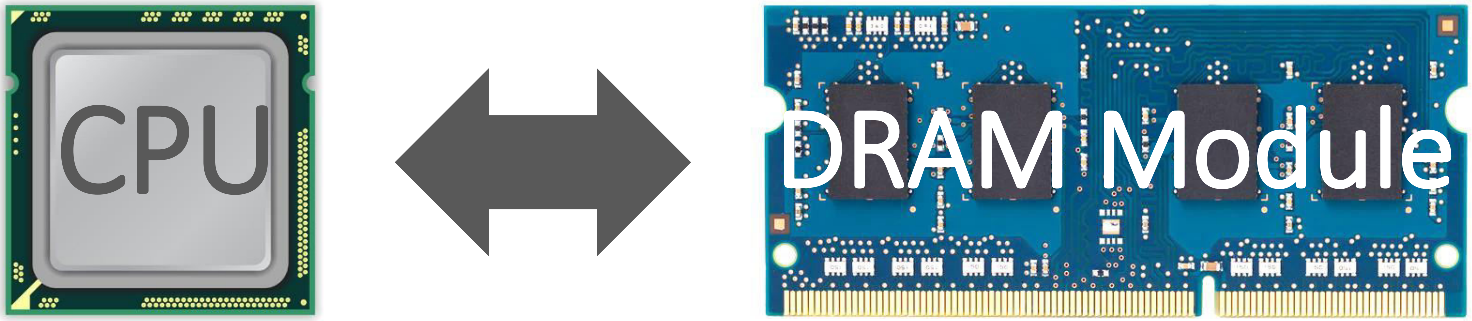

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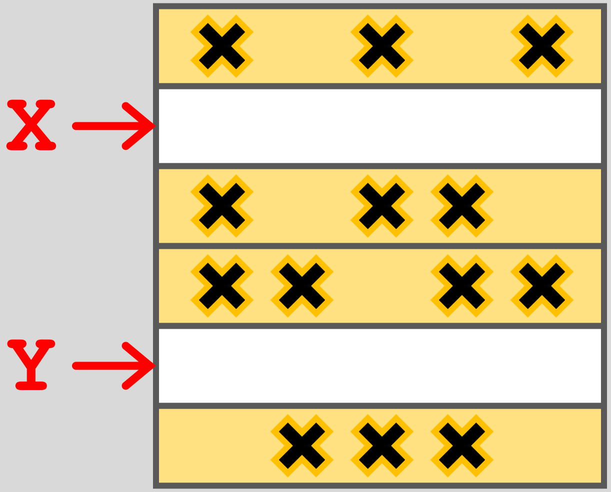


Download from: https://github.com/CMU-SAFARI/rowhammer

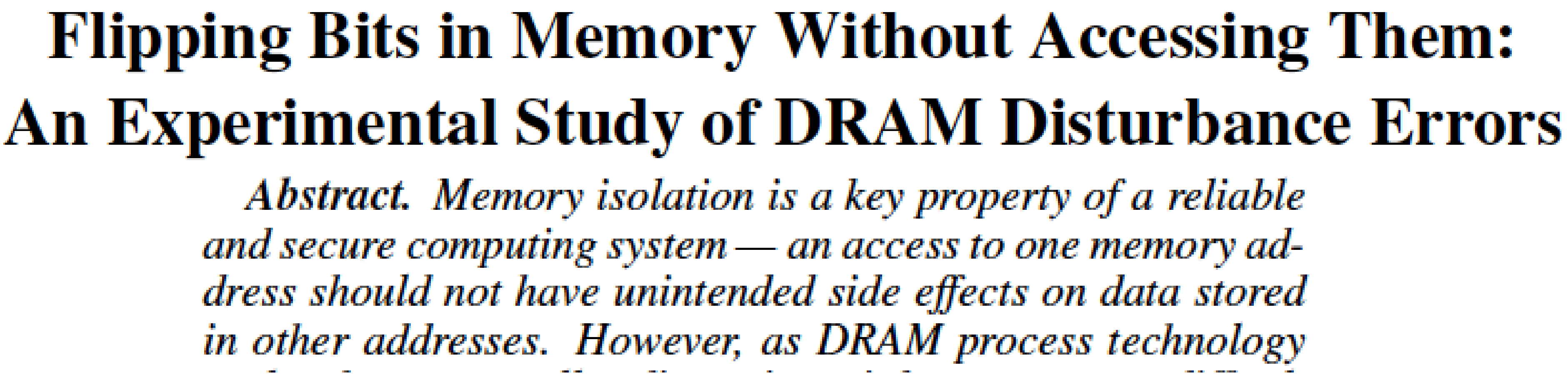
Observed Errors in Real Systems

CPU Architecture	Errors	Access-Rate
Intel Haswell (2013)	22.9K	12.3M/sec
Intel Ivy Bridge (2012)	20.7K	11.7M/sec
Intel Sandy Bridge (2011)	16.1K	11.6M/sec
AMD Piledriver (2012)	59	6.1M/sec

A real reliability & security issue

Kim+, "Flipping Bits in Memory Without Accessing Them: An Experimental Study of DRAM Disturbance Errors," ISCA 2014.

One Can Take Over an Otherwise-Secure System



Flipping Bits in Memory Without Accessing Them:
An Experimental Study of DRAM Disturbance Errors

Abstract. *Memory isolation is a key property of a reliable and secure computing system — an access to one memory address should not have unintended side effects on data stored in other addresses. However, as DRAM process technology*

Project Zero

[Flipping Bits in Memory Without Accessing Them: An Experimental Study of DRAM Disturbance Errors](#) (Kim et al., ISCA 2014)

News and updates from the Project Zero team at Google

[Exploiting the DRAM rowhammer bug to gain kernel privileges](#) (Seaborn+, 2015)

Monday, March 9, 2015

Exploiting the DRAM rowhammer bug to gain kernel privileges

RowHammer Security Attack Example

- "Rowhammer" is a problem with some recent DRAM devices in which repeatedly accessing a row of memory can cause bit flips in adjacent rows (Kim et al., ISCA 2014).
  - Flipping Bits in Memory Without Accessing Them: An Experimental Study of DRAM Disturbance Errors (Kim et al., ISCA 2014)

- We tested a selection of laptops and found that a subset of them exhibited the problem.
- We built two working privilege escalation exploits that use this effect.
  - Exploiting the DRAM rowhammer bug to gain kernel privileges (Seaborn+, 2015)

- One exploit uses rowhammer-induced bit flips to gain kernel privileges on x86-64 Linux when run as an unprivileged userland process.
- When run on a machine vulnerable to the rowhammer problem, the process was able to induce bit flips in page table entries (PTEs).
- It was able to use this to gain write access to its own page table, and hence gain read-write access to all of physical memory.

Exploiting the DRAM rowhammer bug to gain kernel privileges (Seaborn & Dullien, 2015)

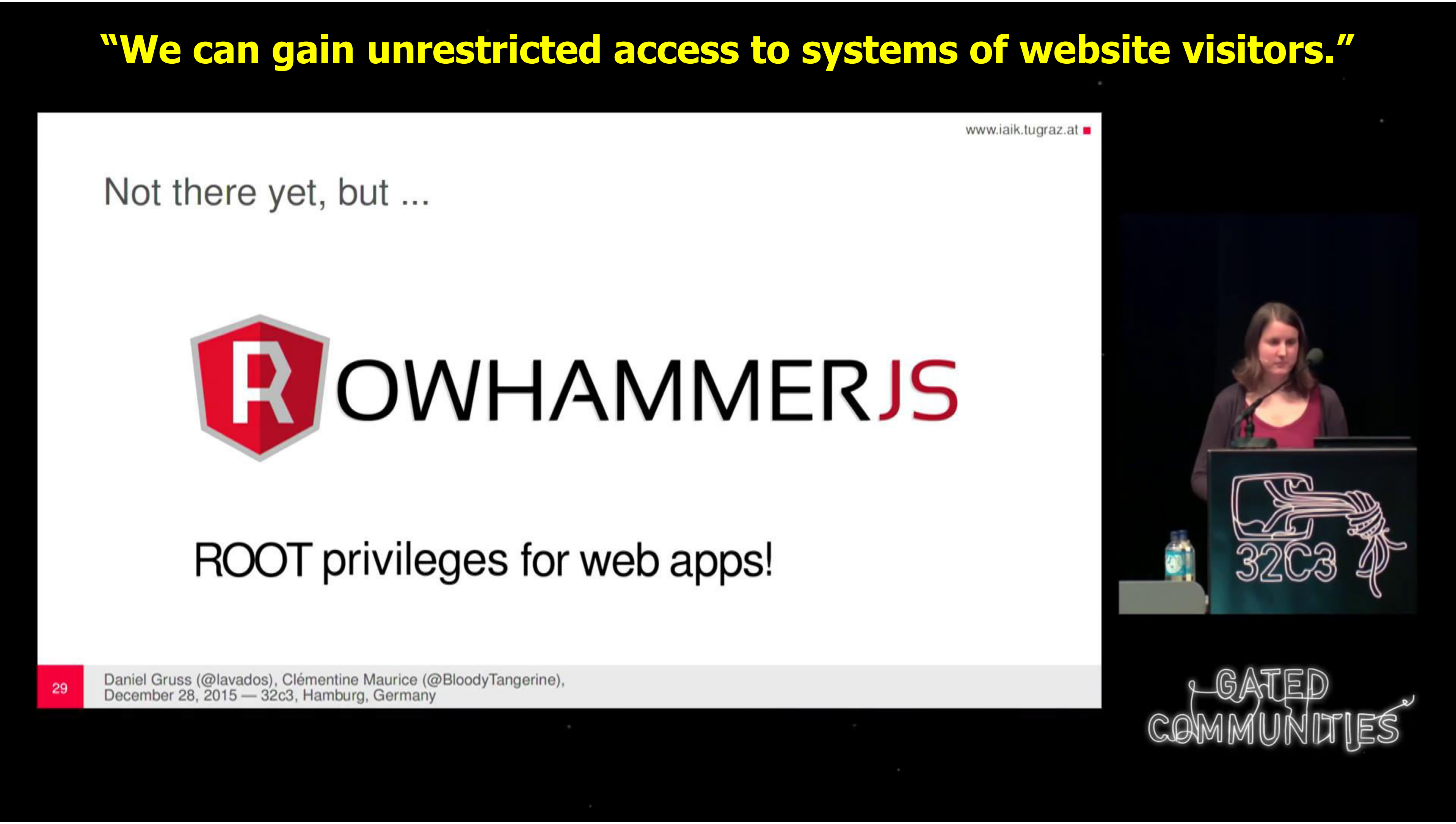
Security Implications

Security Implications

It's like breaking into an apartment by repeatedly slamming a neighbor's door until the vibrations open the door you were after

More Security Implications

"We can gain unrestricted access to systems of website visitors."



www.iaik.tugraz.at

Not there yet, but ...

ROWHAMMERJS

ROOT privileges for web apps!

29 Daniel Gruss (@lavados), Clémentine Maurice (@BloodyTangerine),
December 28, 2015 — 32c3, Hamburg, Germany

Rowhammer.js: A Remote Software-Induced Fault Attack in JavaScript (DIMVA'16)

Source: https://lab.dsst.io/32c3-slides/7197.html

More Security Implications

“Can gain control of a smart phone deterministically”

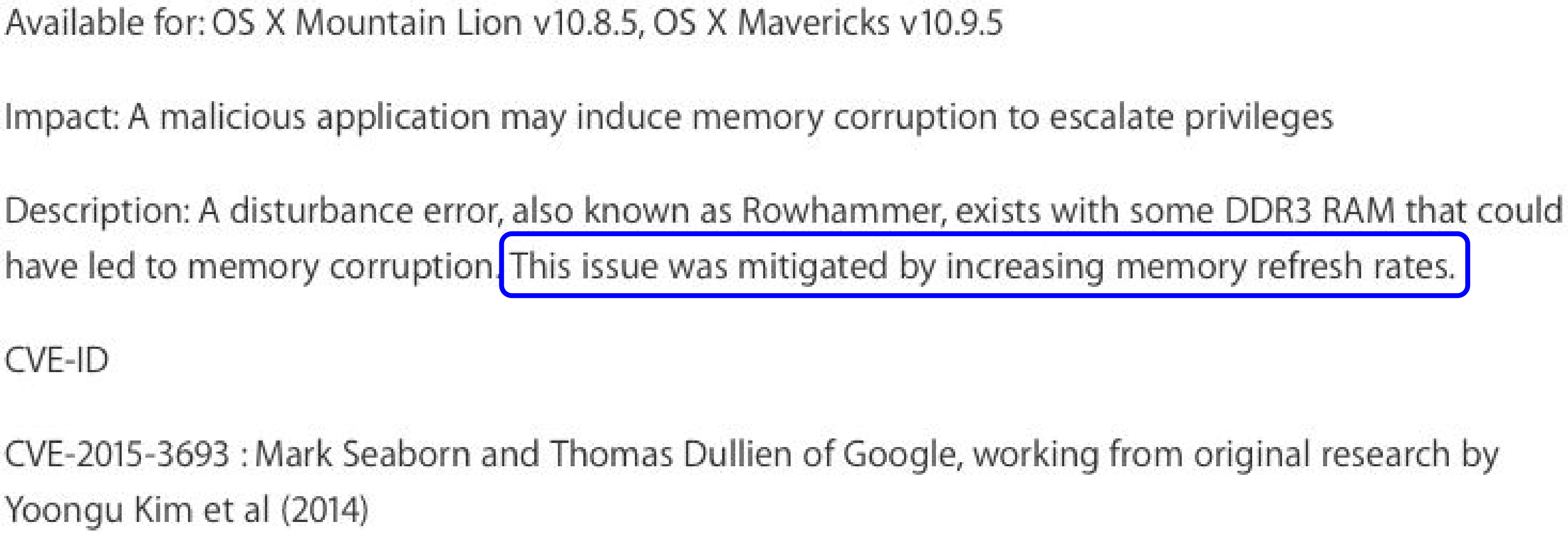
Drammer: Deterministic Rowhammer Attacks on Mobile Platforms, CCS’16

Source: https://fossbytes.com/drammer-rowhammer-attack-android-root-devices/

More Security Implications?

Apple’s Patch for RowHammer

- https://support.apple.com/en-gb/HT204934



Available for: OS X Mountain Lion v10.8.5, OS X Mavericks v10.9.5

Impact: A malicious application may induce memory corruption to escalate privileges

Description: A disturbance error, also known as Rowhammer, exists with some DDR3 RAM that could have led to memory corruption. This issue was mitigated by increasing memory refresh rates.

CVE-ID

CVE-2015-3693 : Mark Seaborn and Thomas Dullien of Google, working from original research by Yoongu Kim et al (2014)

HP, Lenovo, and other vendors released similar patches

Our Solution to RowHammer

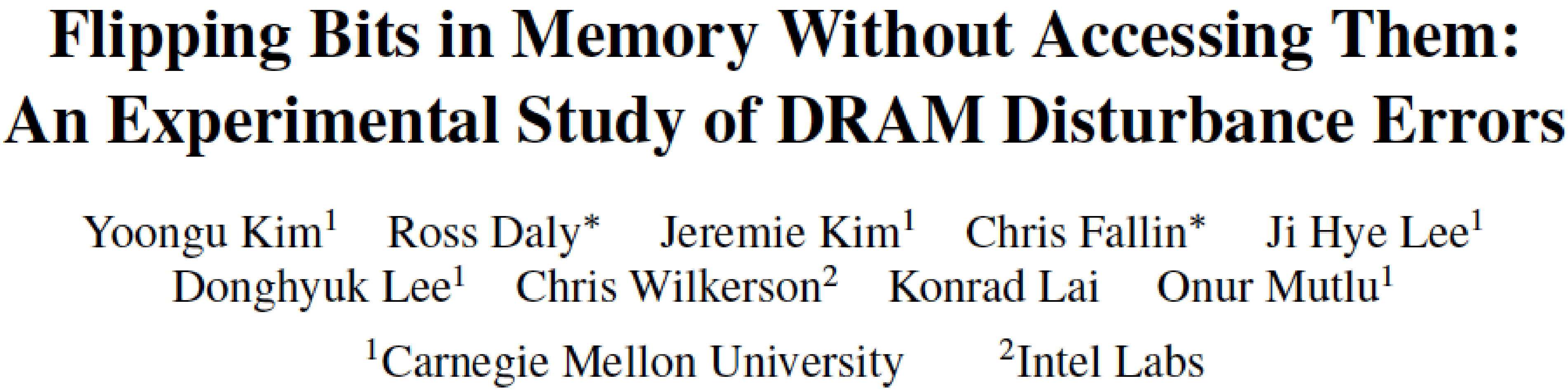
- PARA: *Probabilistic Adjacent Row Activation*

- Key Idea
  - After closing a row, we activate (i.e., refresh) one of its neighbors with a low probability: $p = 0.005$

- Reliability Guarantee
  - When $p=0.005$, errors in one year: 9.4×10^{-14}
  - By adjusting the value of p, we can vary the strength of protection against errors

More on RowHammer Analysis

- Yoongu Kim, Ross Daly, Jeremie Kim, Chris Fallin, Ji Hye Lee, Donghyuk Lee, Chris Wilkerson, Konrad Lai, and Onur Mutlu, **"Flipping Bits in Memory Without Accessing Them: An Experimental Study of DRAM Disturbance Errors"** *Proceedings of the 41st International Symposium on Computer Architecture* (***ISCA***), Minneapolis, MN, June 2014. [Slides (pptx) (pdf)] [Lightning Session Slides (pptx) (pdf)] [Source Code and Data]



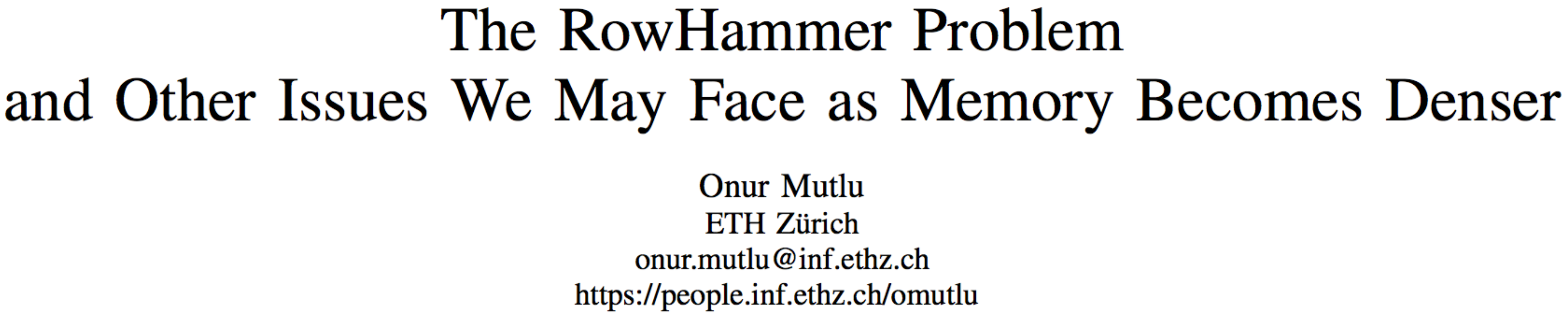
Flipping Bits in Memory Without Accessing Them: An Experimental Study of DRAM Disturbance Errors

Yoongu Kim[1] Ross Daly* Jeremie Kim[1] Chris Fallin* Ji Hye Lee[1]
Donghyuk Lee[1] Chris Wilkerson[2] Konrad Lai Onur Mutlu[1]

[1]Carnegie Mellon University [2]Intel Labs

Future of Memory Reliability

- Onur Mutlu,
  "The RowHammer Problem and Other Issues We May Face as Memory Becomes Denser"
  *Invited Paper in Proceedings of the Design, Automation, and Test in Europe Conference (**DATE**)*, Lausanne, Switzerland, March 2017.
  [Slides (pptx) (pdf)]

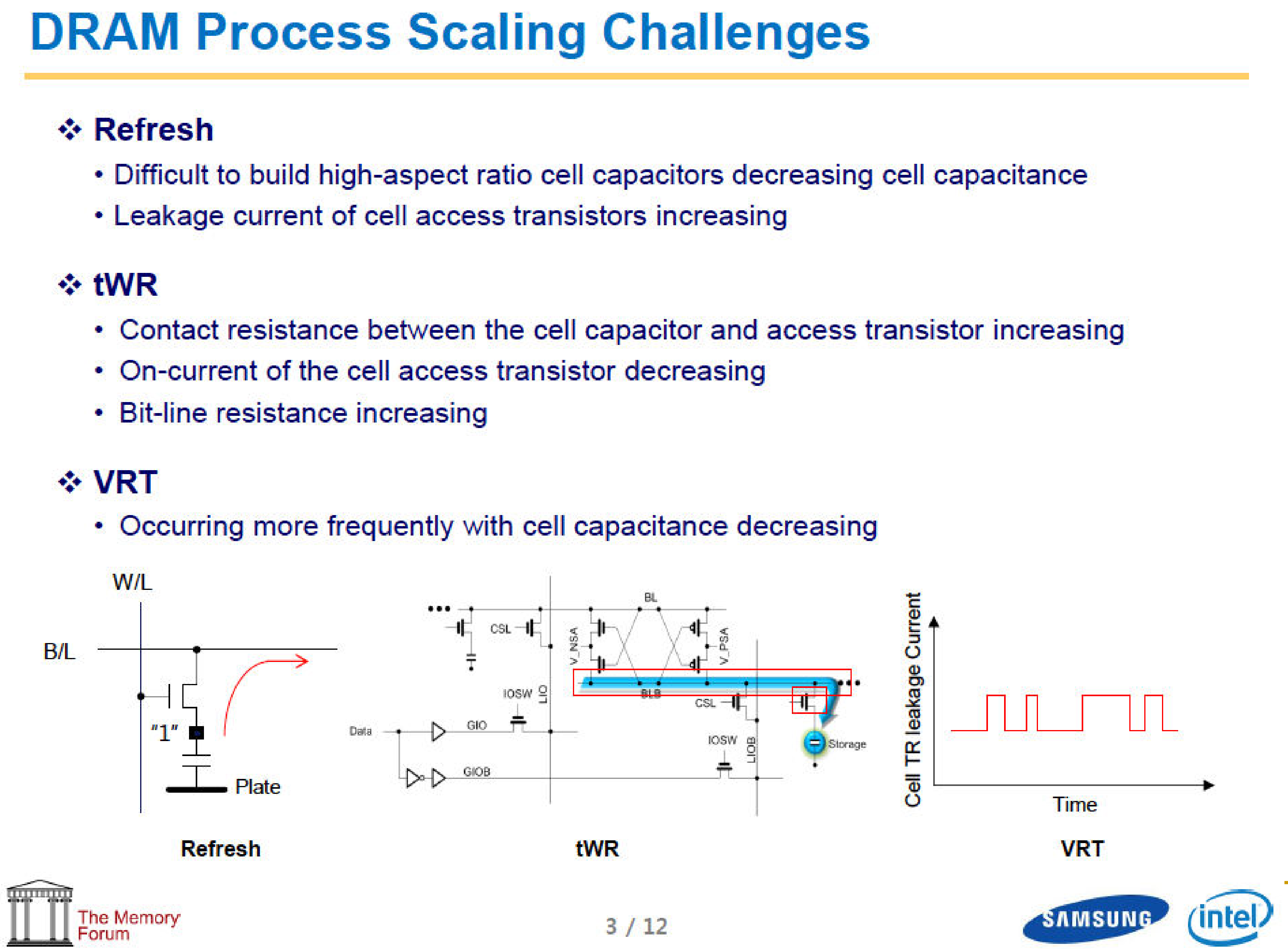


The RowHammer Problem
and Other Issues We May Face as Memory Becomes Denser

Onur Mutlu
ETH Zürich
onur.mutlu@inf.ethz.ch
https://people.inf.ethz.ch/omutlu

https://people.inf.ethz.ch/omutlu/pub/rowhammer-and-other-memory-issues_date17.pdf

Industry Is Writing Papers About It, Too



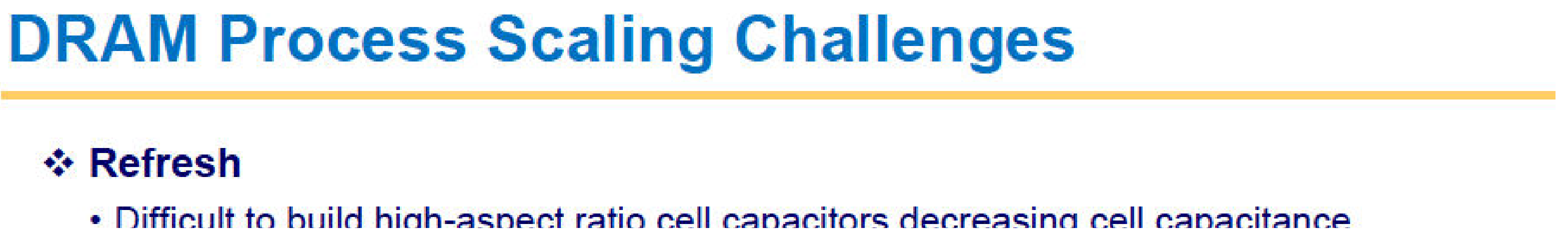
DRAM Process Scaling Challenges

- **Refresh**
  - Difficult to build high-aspect ratio cell capacitors decreasing cell capacitance
  - Leakage current of cell access transistors increasing
- **tWR**
  - Contact resistance between the cell capacitor and access transistor increasing
  - On-current of the cell access transistor decreasing
  - Bit-line resistance increasing
- **VRT**
  - Occurring more frequently with cell capacitance decreasing

Refresh **tWR** **VRT**

The Memory Forum

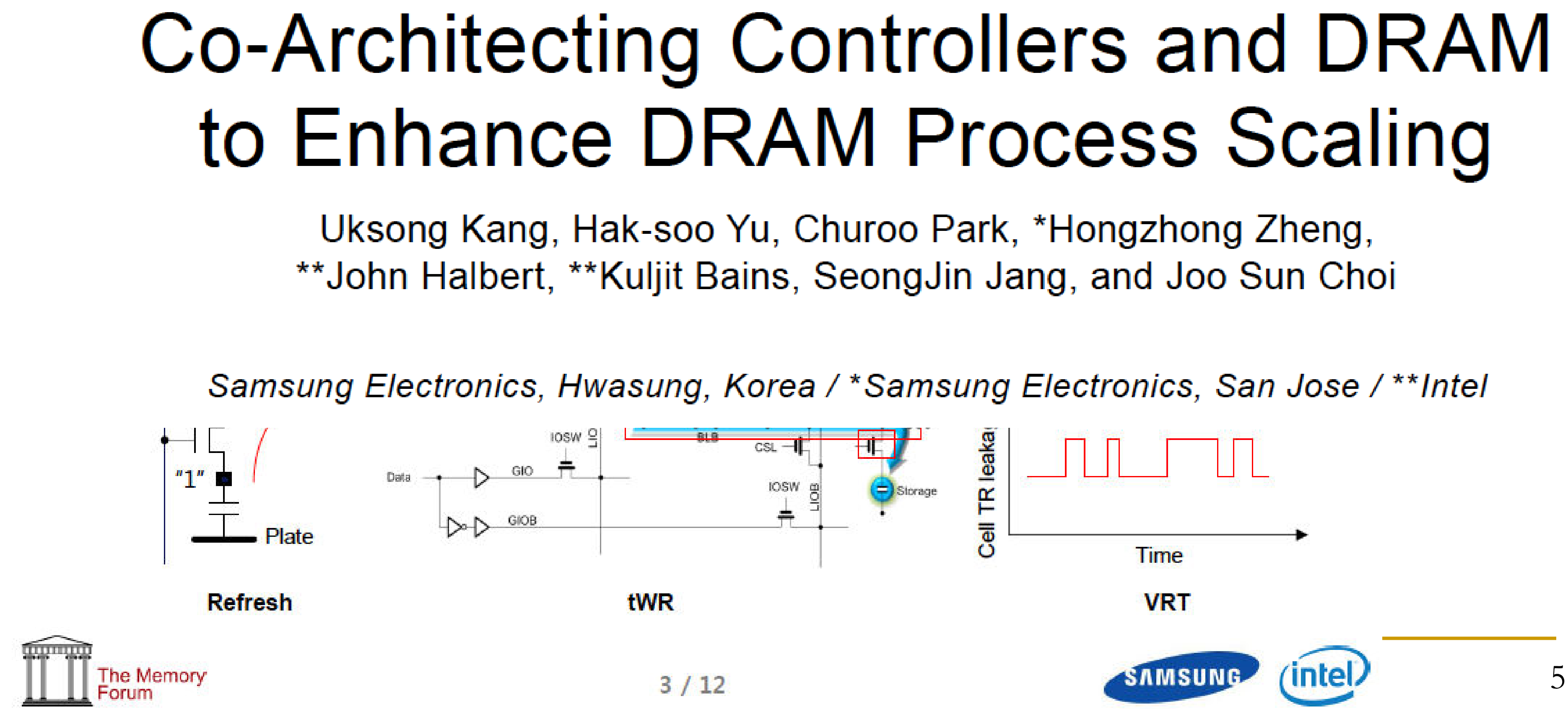
Call for Intelligent Memory Controllers



DRAM Process Scaling Challenges

- **Refresh**
  - Difficult to build high-aspect ratio cell capacitors decreasing cell capacitance

THE MEMORY FORUM 2014



Co-Architecting Controllers and DRAM to Enhance DRAM Process Scaling

Uksong Kang, Hak-soo Yu, Churoo Park, *Hongzhong Zheng,
**John Halbert, **Kuljit Bains, SeongJin Jang, and Joo Sun Choi

*Samsung Electronics, Hwasung, Korea / *Samsung Electronics, San Jose / **Intel*

Refresh **tWR** **VRT**

The Memory Forum

3 / 12

Solution Direction: Principled Designs

Design fundamentally secure computing architectures

Predict and prevent such safety issues

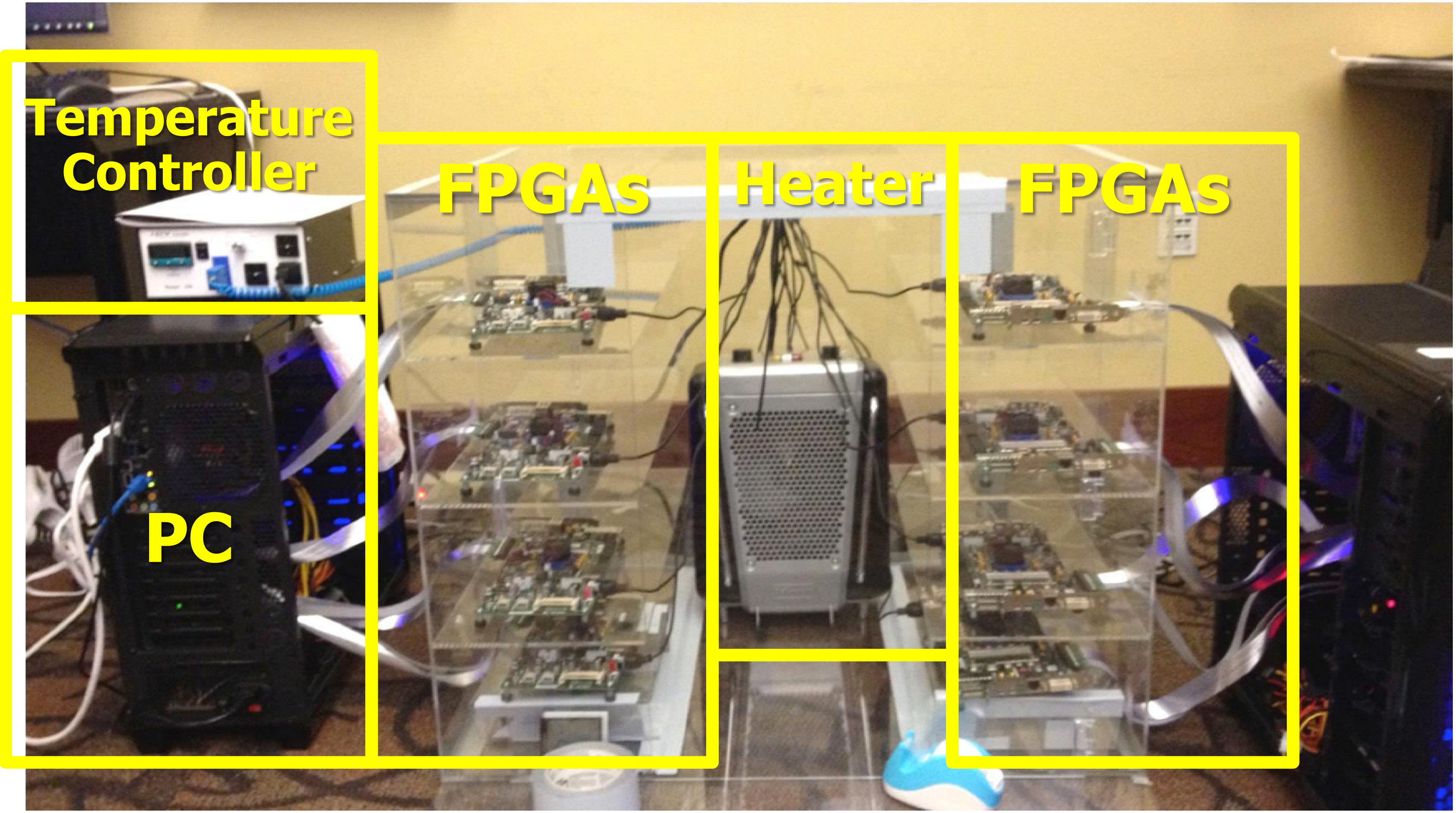
How Do We Keep Memory Secure?

- **Understand**: Methodologies for failure modeling and discovery
  - Modeling and prediction based on real (device) data

- **Architect**: Principled co-architecting of system and memory
  - Good partitioning of duties across the stack

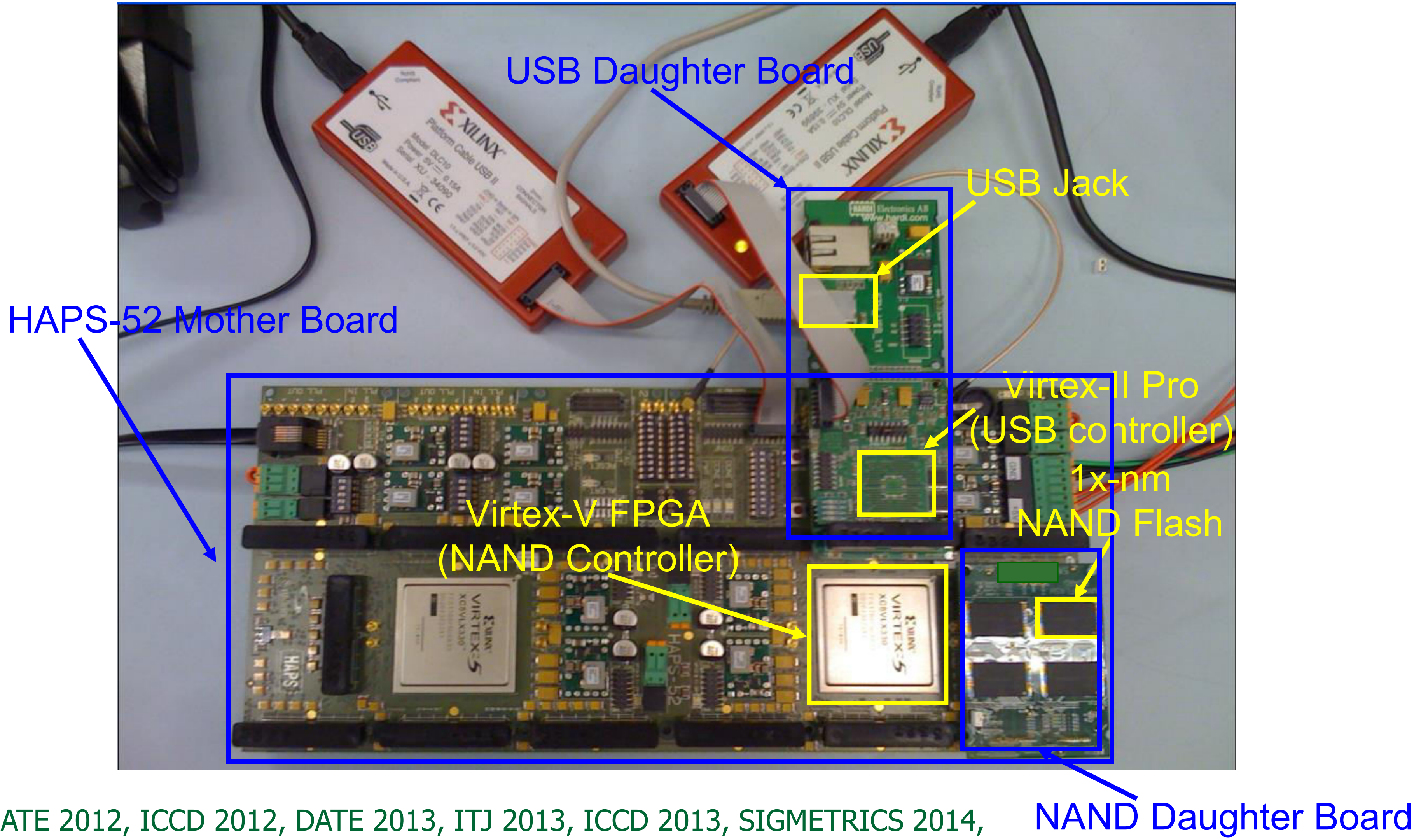
- **Design & Test**: Principled design, automation, testing
  - High coverage and good interaction with system reliability methods

Understand and Model with Experiments (DRAM)



Kim+, "Flipping Bits in Memory Without Accessing Them: An Experimental Study of DRAM Disturbance Errors," ISCA 2014.

Understand and Model with Experiments (Flash)



[DATE 2012, ICCD 2012, DATE 2013, ITJ 2013, ICCD 2013, SIGMETRICS 2014, HPCA 2015, DSN 2015, MSST 2015, JSAC 2016, HPCA 2017, DFRWS 2017, PIEEE'17]

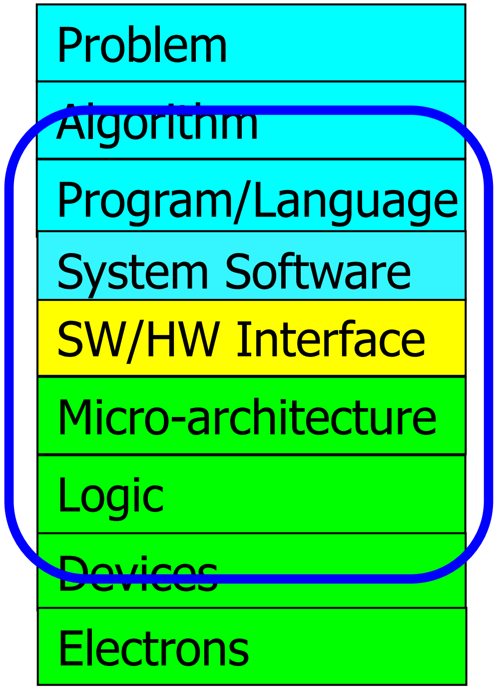
Cai+, "Error Characterization, Mitigation, and Recovery in Flash Memory Based Solid State Drives," Proc. IEEE 2017.

There are Two Other Solution Directions

- **New Technologies:** Replace or (more likely) augment DRAM with a different technology
  - Non-volatile memories

- **Embracing Un-reliability:**
  Design memories with different reliability and store data intelligently across them

- …



Fundamental solutions to security require co-design across the hierarchy

Challenge and Opportunity for Future

Fundamentally

Secure, Reliable, Safe

Computing Architectures

One Important Takeaway

Main Memory Needs
Intelligent Controllers

Three Key Issues in Future Platforms

- Fundamentally Secure/Reliable/Safe Architectures

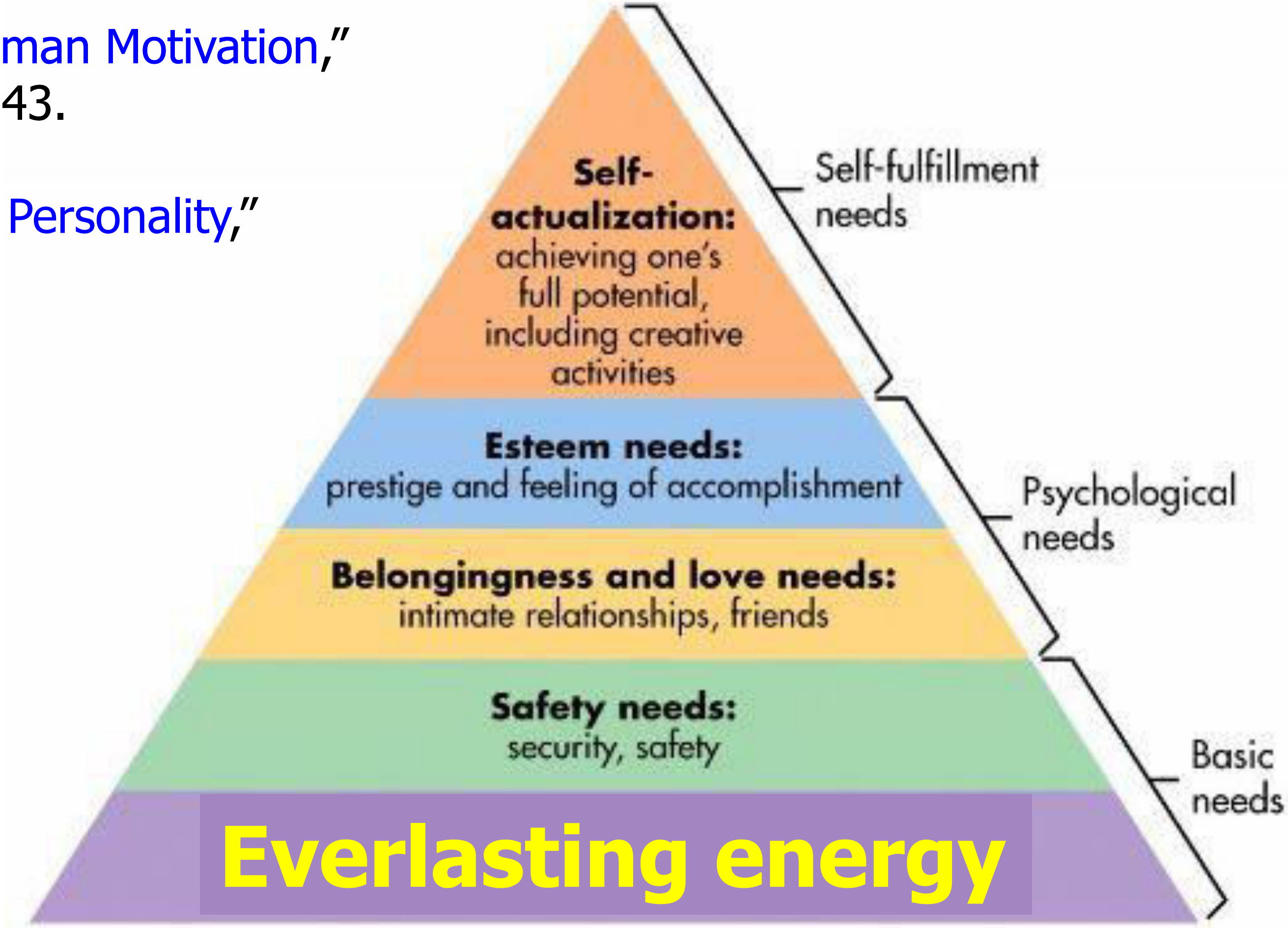
- Fundamentally Energy-Efficient Architectures
  - Memory-centric (Data-centric) Architectures

- Fundamentally Low Latency Architectures

Maslow's (Human) Hierarchy of Needs, Revisited

Maslow, "A Theory of Human Motivation," Psychological Review, 1943.

Maslow, "Motivation and Personality," Book, 1954-1970.



Source: https://www.simplypsychology.org/maslow.html

Challenge and Opportunity for Future

Sustainable

and

Energy Efficient

The Problem

Data access is the major performance and energy bottleneck

Our current

design principles

cause great energy waste

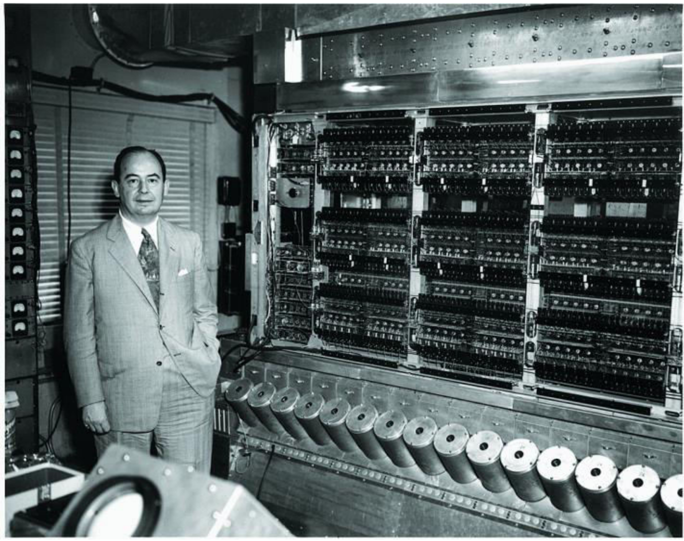
(and great performance loss)

The Problem

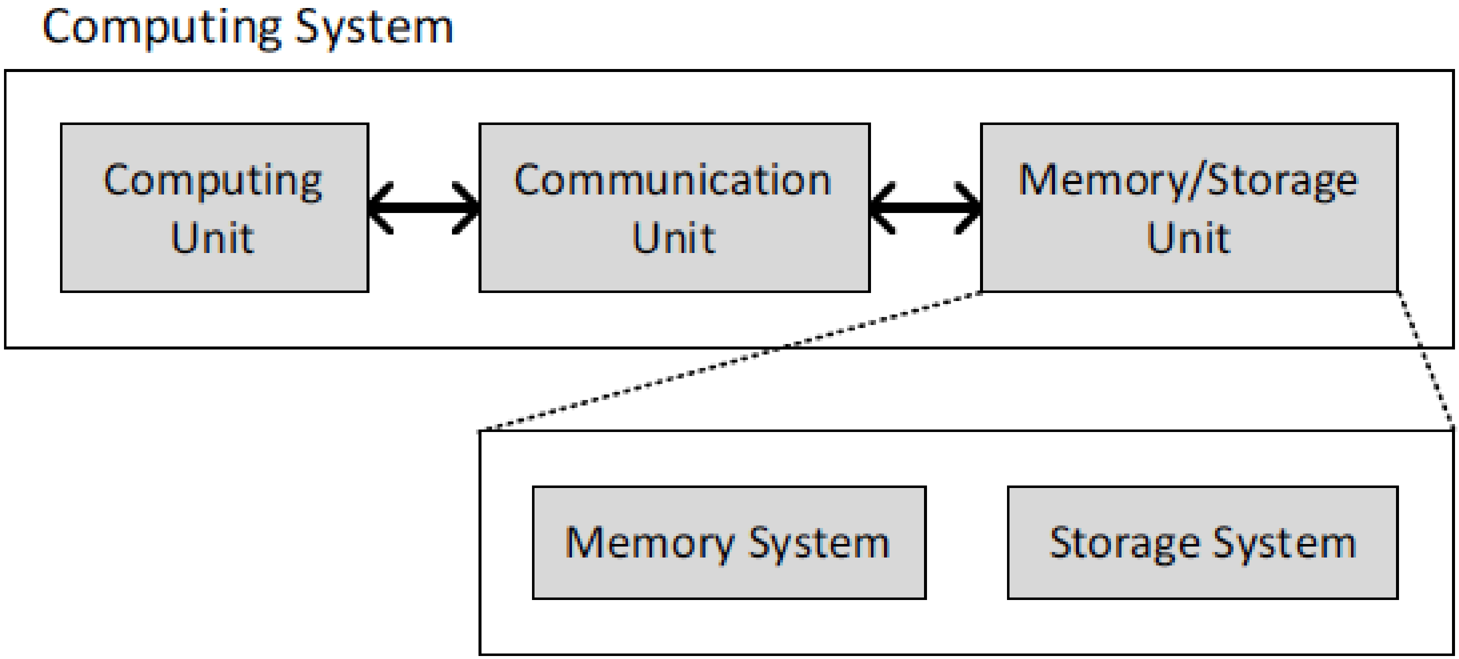
Processing of data
is performed
far away from the data

A Computing System

- Three key components
- Computation
- Communication
- Storage/memory



Burks, Goldstein, von Neumann, "Preliminary discussion of the logical design of an electronic computing instrument," 1946.



Computing System

Computing Unit ↔ Communication Unit ↔ Memory/Storage Unit

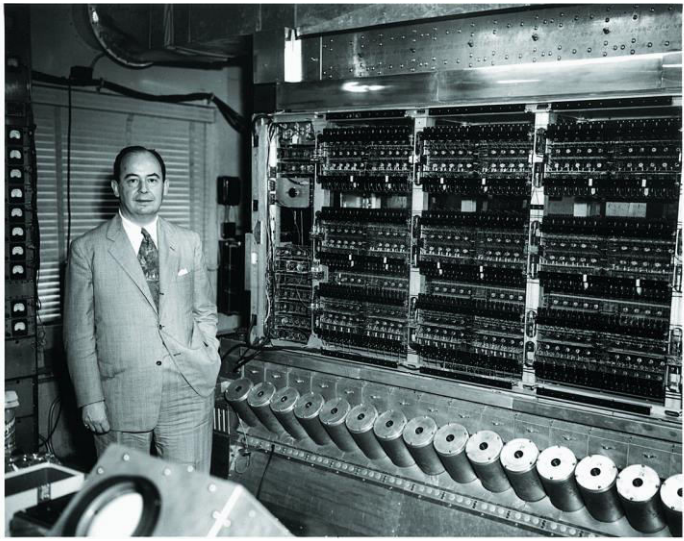
Memory System

Storage System

Image source: https://lbsitbytes2010.wordpress.com/2013/03/29/john-von-neumann-roll-no-15/

A Computing System

- Three key components
- Computation
- Communication
- Storage/memory



Burks, Goldstein, von Neumann, "Preliminary discussion of the logical design of an electronic computing instrument," 1946.

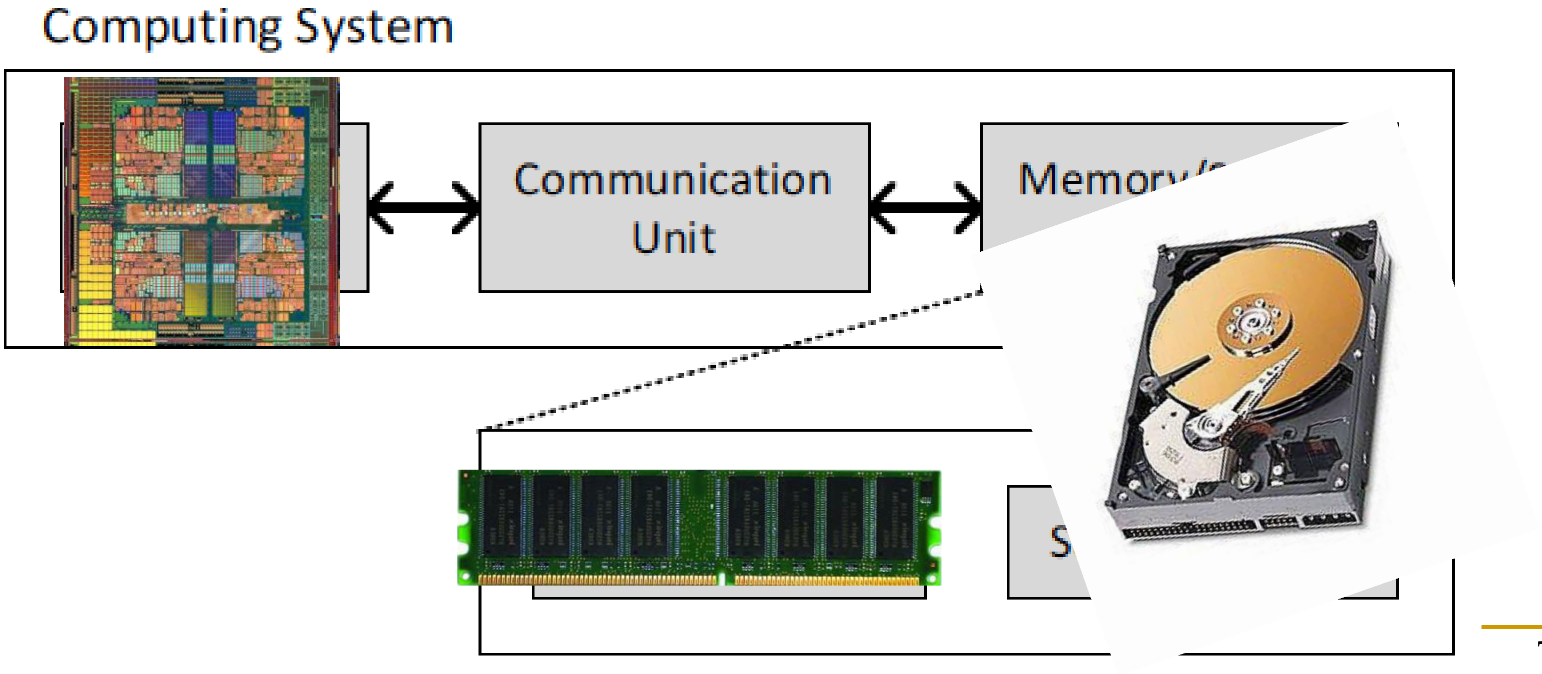
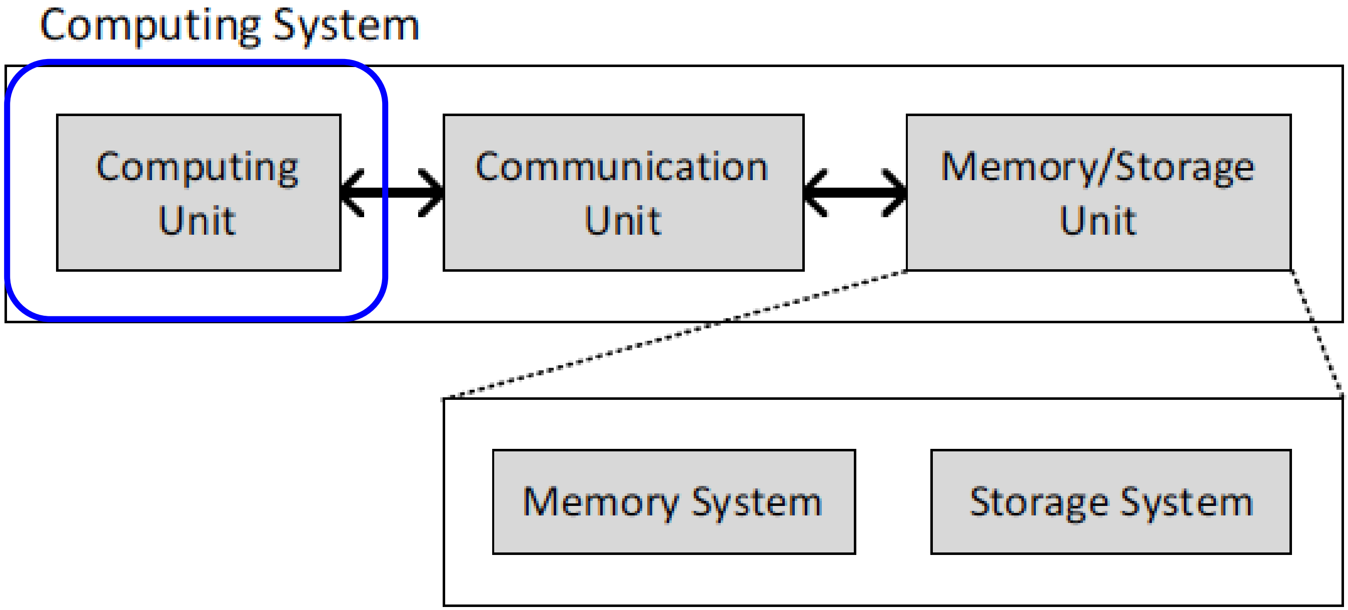


Image source: https://lbsitbytes2010.wordpress.com/2013/03/29/john-von-neumann-roll-no-15/

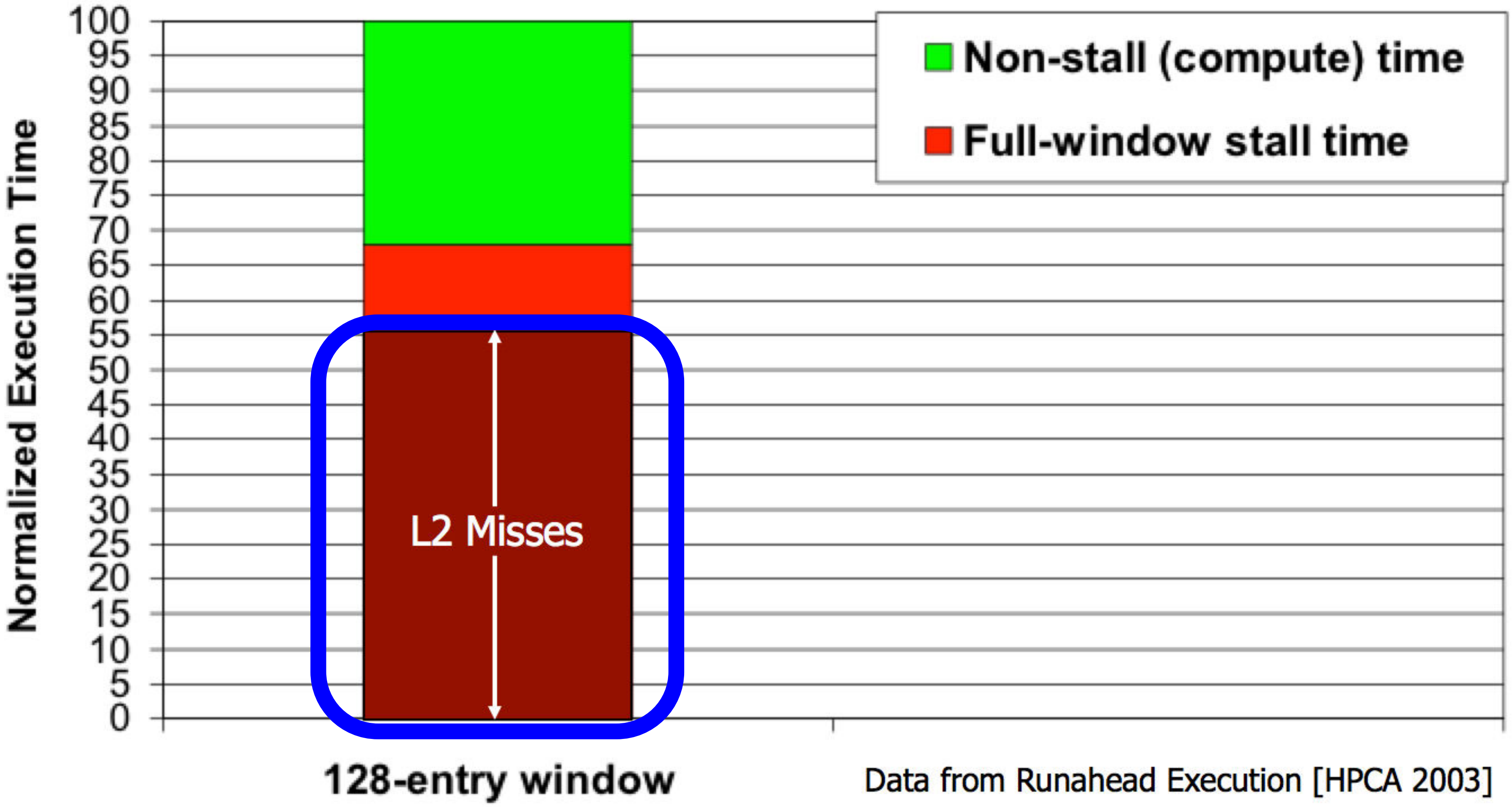
Today's Computing Systems

- Are overwhelmingly processor centric
- All data processed in the processor → at great system cost
- Processor is heavily optimized and is considered the master
- Data storage units are dumb and are largely unoptimized (except for some that are on the processor die)



Yet …

- "**It's the Memory, Stupid!**" (Richard Sites, MPR, 1996)

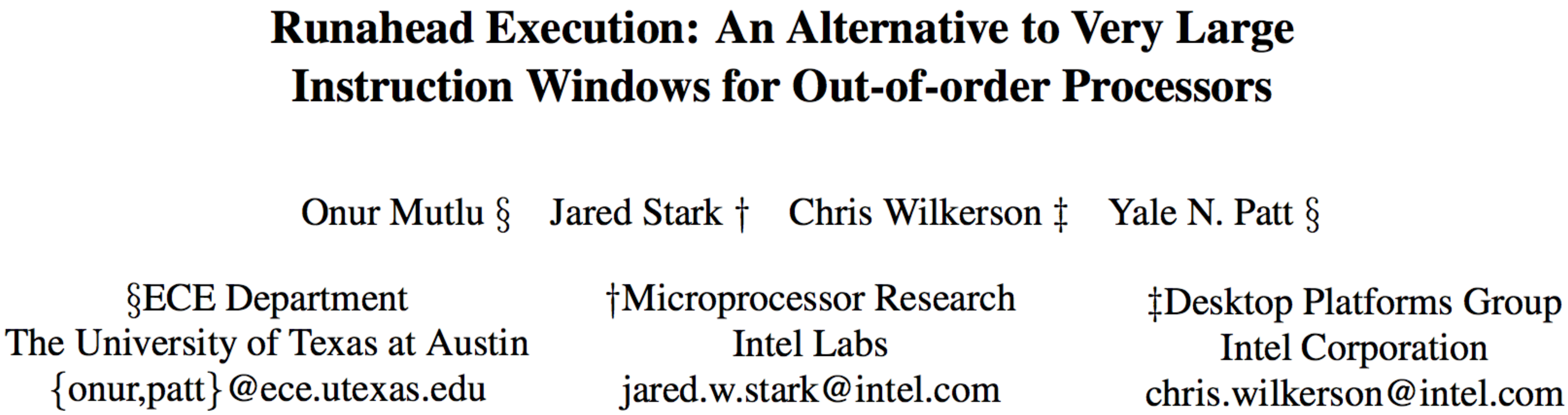


Data from Runahead Execution [HPCA 2003]

Mutlu+, "Runahead Execution: An Alternative to Very Large Instruction Windows for Out-of-Order Processors," HPCA 2003.

The Performance Perspective

- Onur Mutlu, Jared Stark, Chris Wilkerson, and Yale N. Patt, **"Runahead Execution: An Alternative to Very Large Instruction Windows for Out-of-order Processors"** *Proceedings of the 9th International Symposium on High-Performance Computer Architecture* (***HPCA***), pages 129-140, Anaheim, CA, February 2003. Slides (pdf)



Runahead Execution: An Alternative to Very Large Instruction Windows for Out-of-order Processors

Onur Mutlu § Jared Stark † Chris Wilkerson ‡ Yale N. Patt §

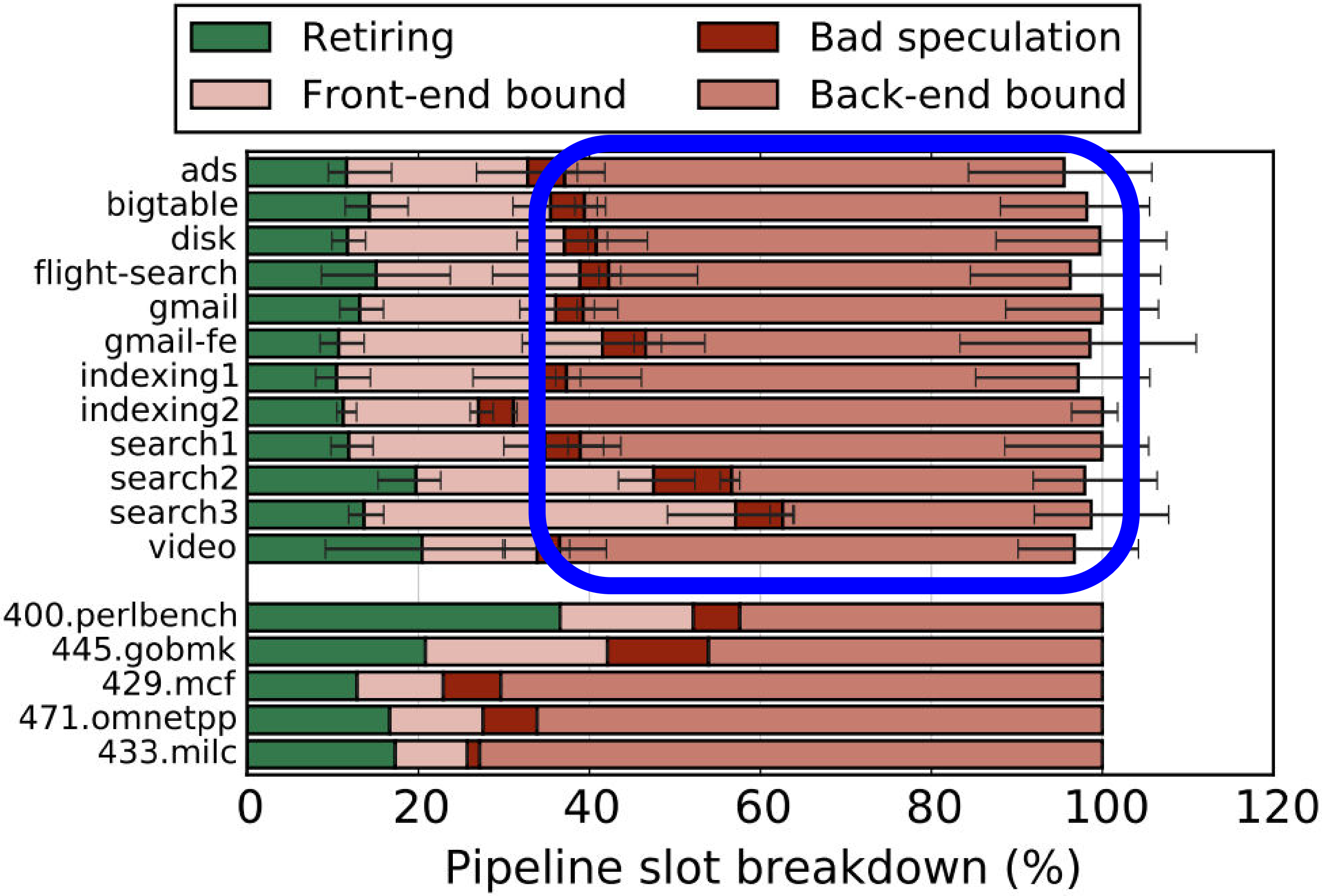
§ECE Department
The University of Texas at Austin
{onur,patt}@ece.utexas.edu

†Microprocessor Research
Intel Labs
jared.w.stark@intel.com

‡Desktop Platforms Group
Intel Corporation
chris.wilkerson@intel.com

The Performance Perspective (Today)

- All of Google's Data Center Workloads (2015):



Kanev+, "Profiling a Warehouse-Scale Computer," ISCA 2015.

The Performance Perspective (Today)

- All of Google's Data Center Workloads (2015):

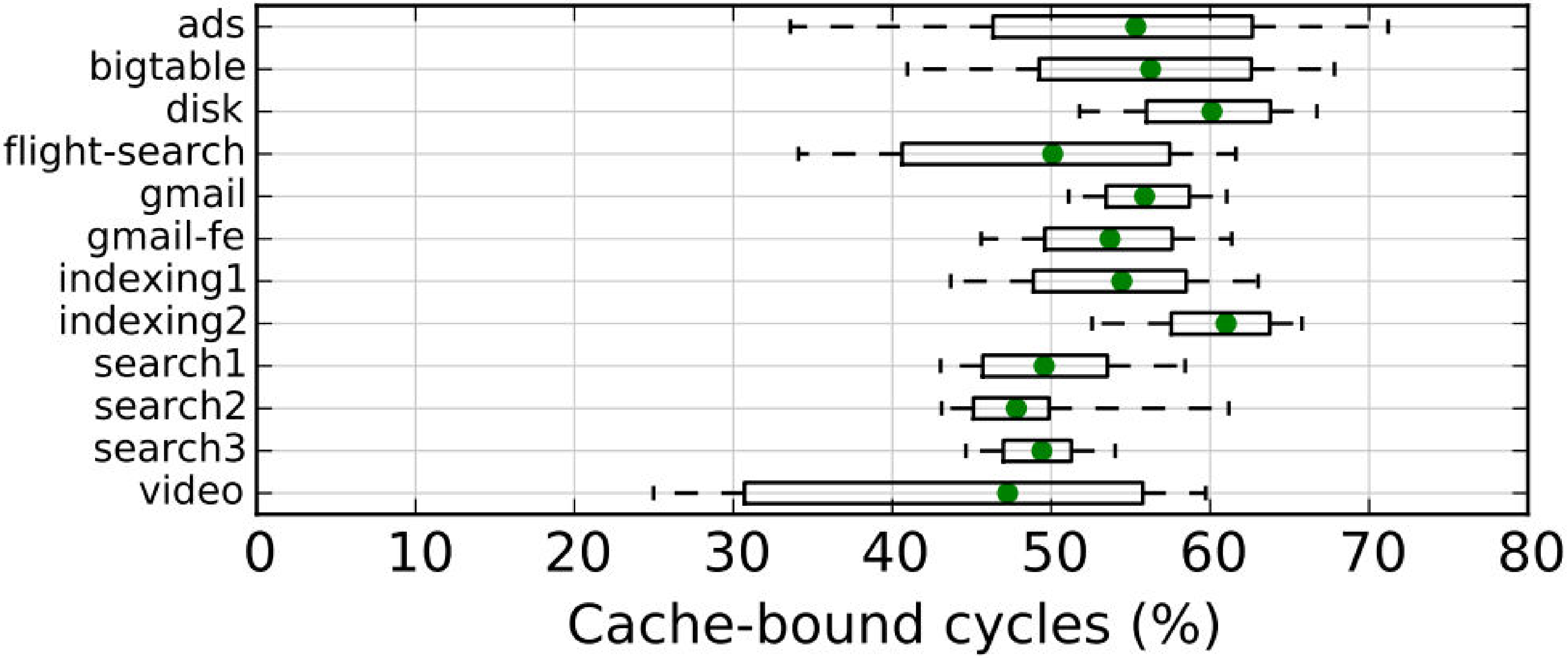


Figure 11: Half of cycles are spent stalled on caches.

Kanev+, "Profiling a Warehouse-Scale Computer," ISCA 2015.

Perils of Processor-Centric Design

- Grossly-imbalanced systems
  - Processing done only in **one place**
  - Everything else just stores and moves data: **data moves a lot**

  → Energy inefficient

  → Low performance

  → Complex

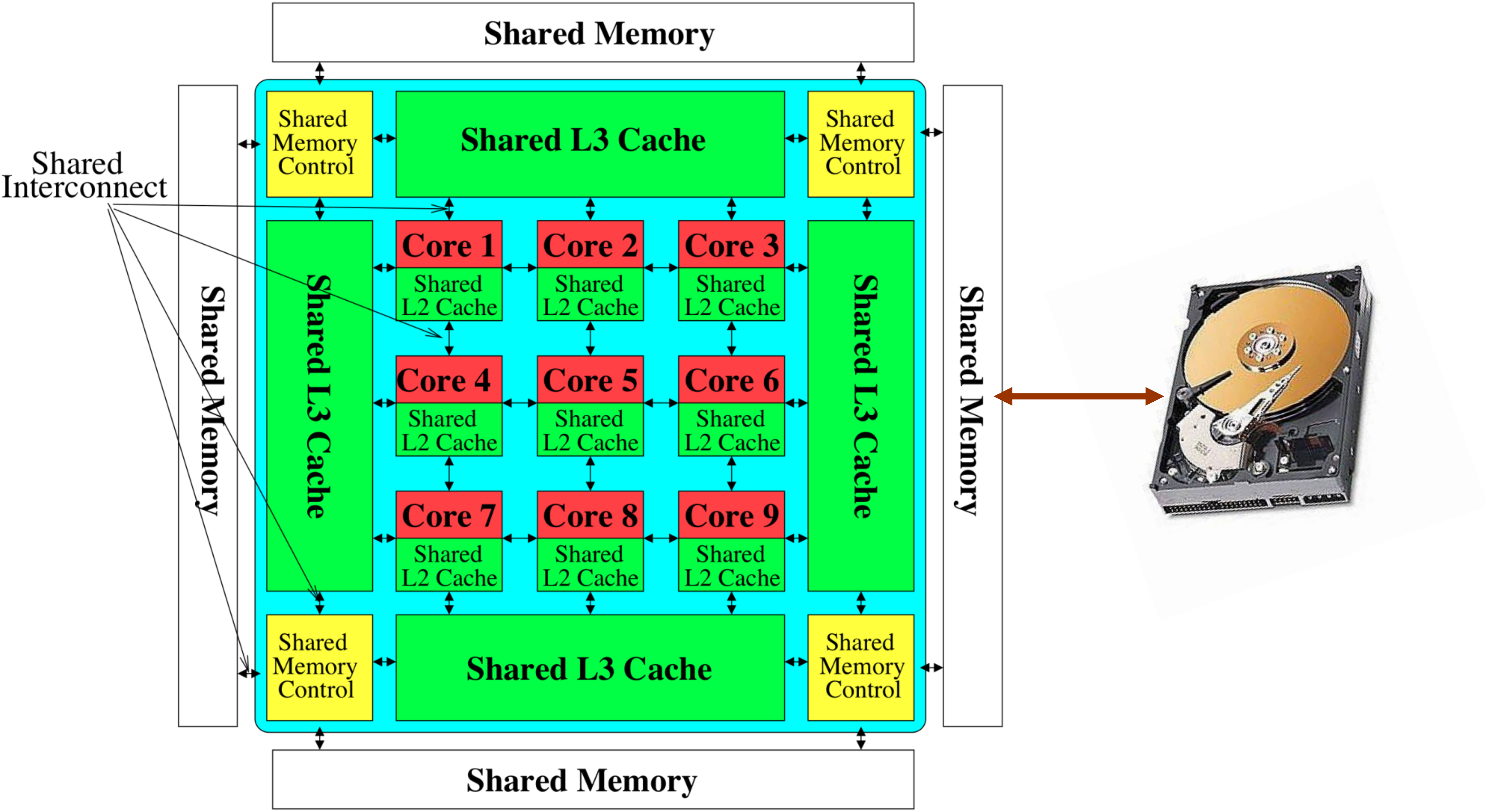
- Overly complex and bloated processor (and accelerators)
  - To tolerate data access from memory
  - Complex hierarchies and mechanisms

  → Energy inefficient

  → Low performance

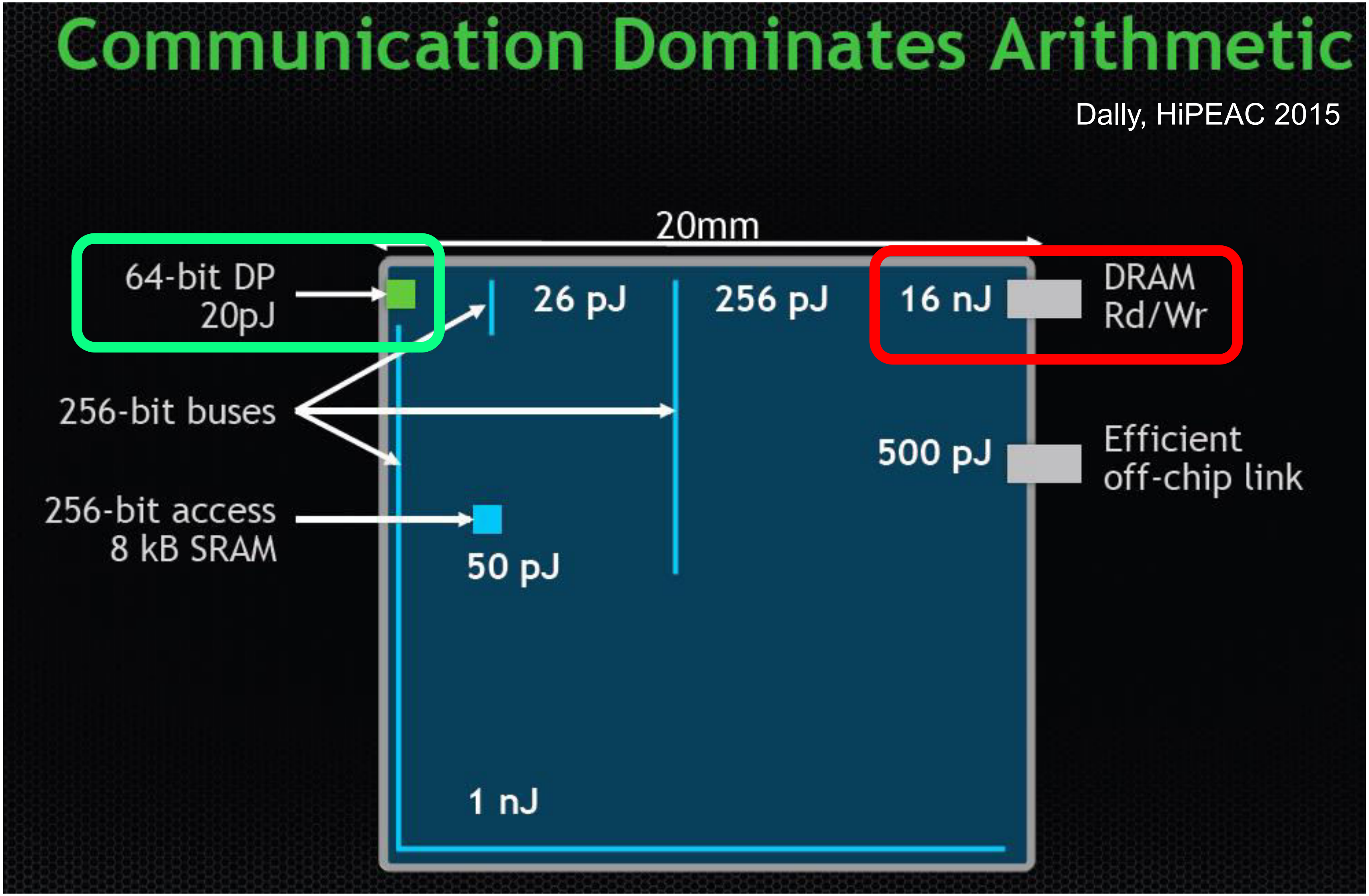
  → Complex

Perils of Processor-Centric Design



Most of the system is dedicated to storing and moving data

The Energy Perspective



Communication Dominates Arithmetic

Dally, HiPEAC 2015

20mm

64-bit DP
20pJ

26 pJ

256 pJ

16 nJ

DRAM
Rd/Wr

256-bit buses

500 pJ

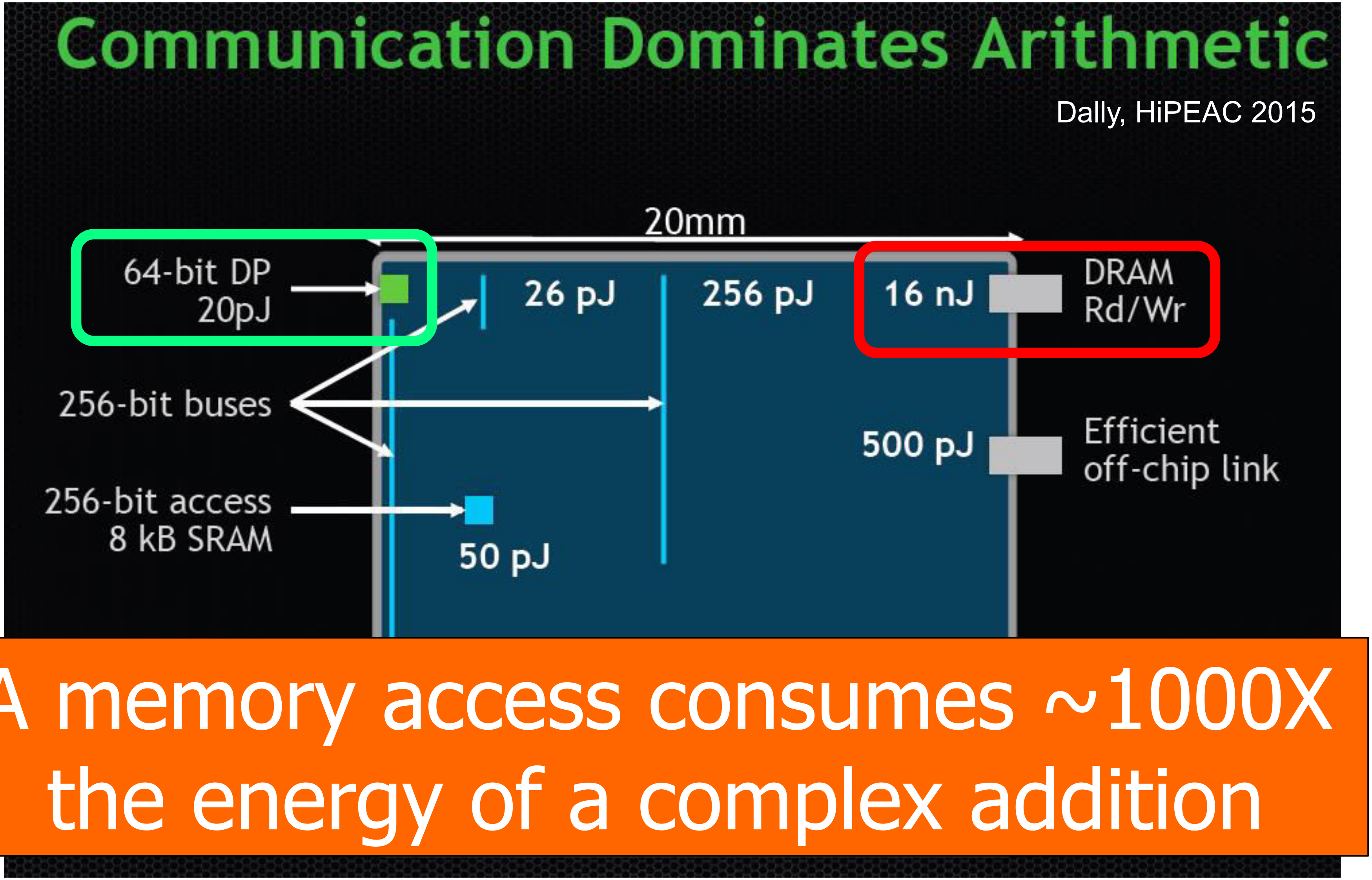
Efficient
off-chip link

256-bit access
8 kB SRAM

50 pJ

1 nJ

Data Movement vs. Computation Energy

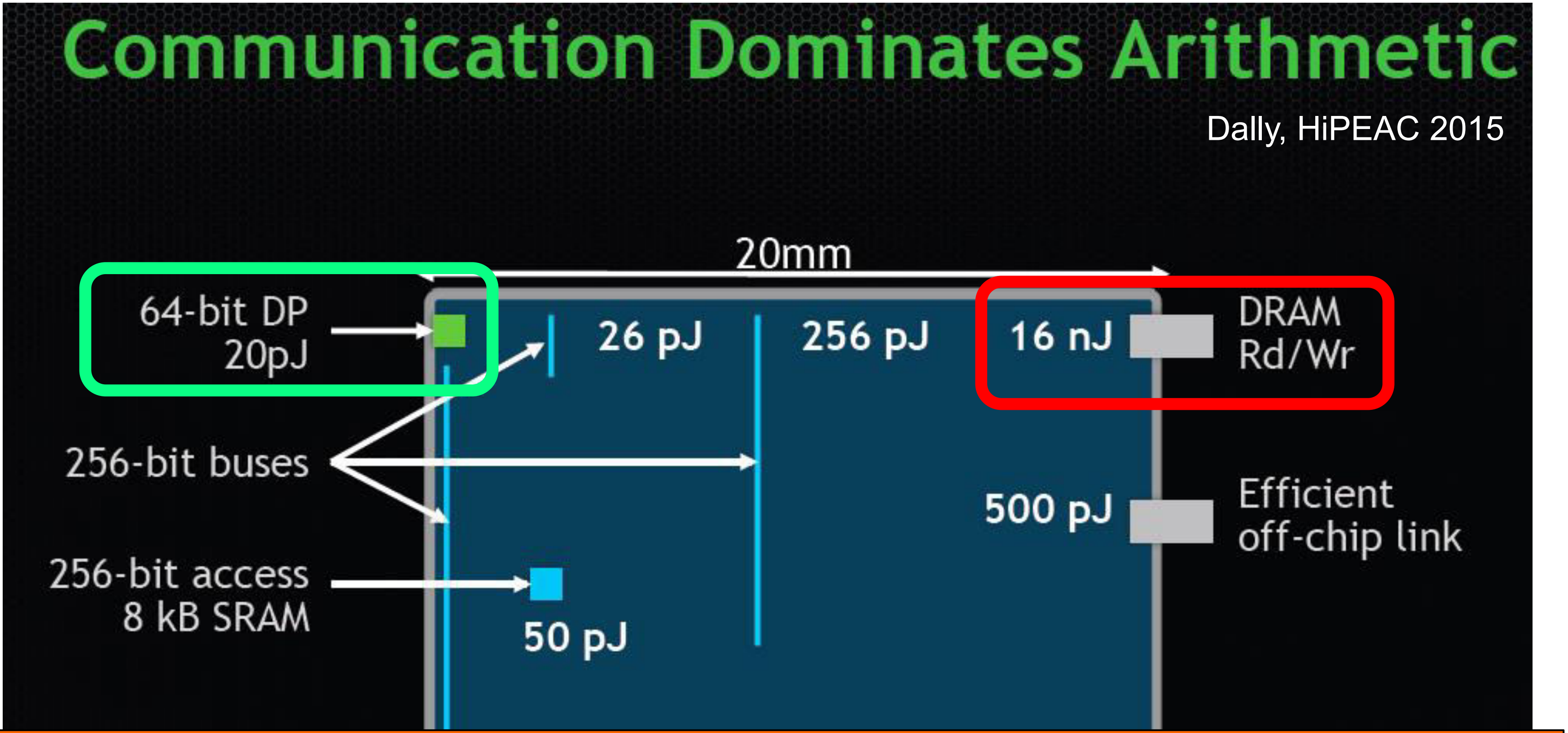


Communication Dominates Arithmetic

Dally, HiPEAC 2015

A memory access consumes ~1000X the energy of a complex addition

We Do Not Want to Move Data!



Communication Dominates Arithmetic

Dally, HiPEAC 2015

A memory access consumes ~1000X the energy of a complex addition

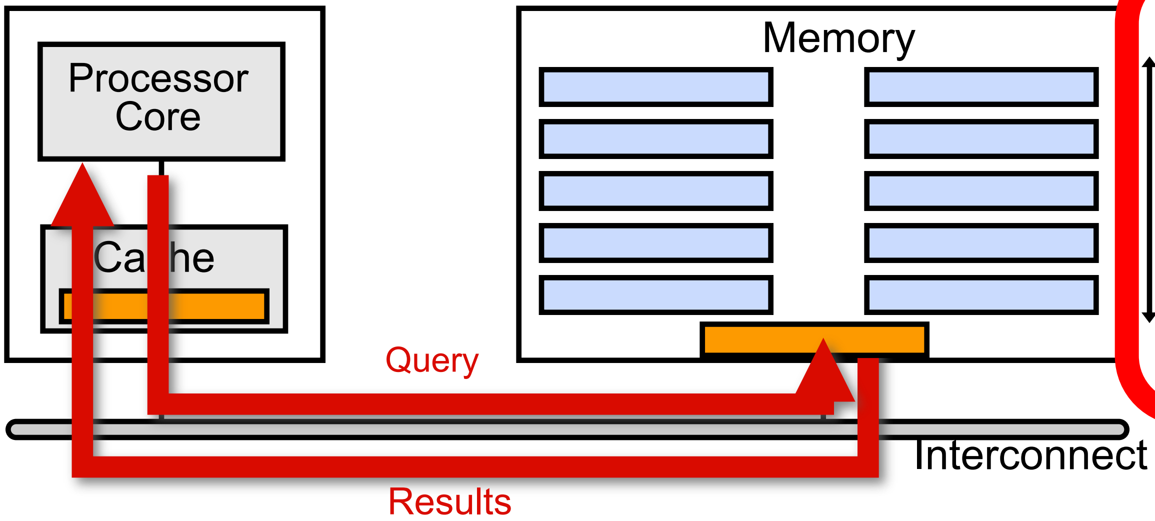
We Need A Paradigm Shift To …

- Enable computation with minimal data movement

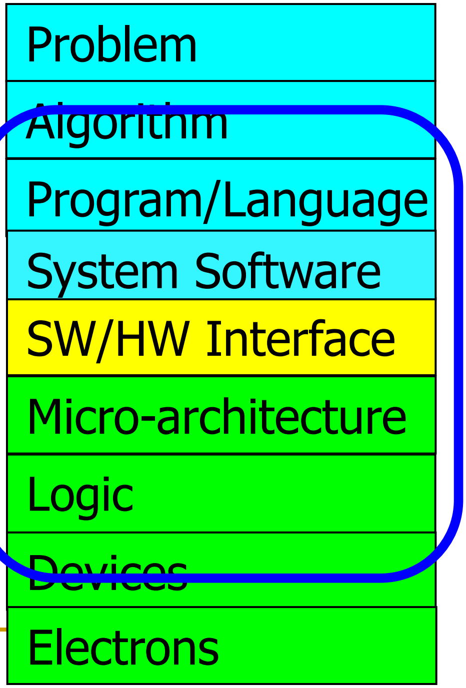
- Compute where it makes sense (where data resides)

- Make computing architectures more data-centric

Goal: Processing Inside Memory



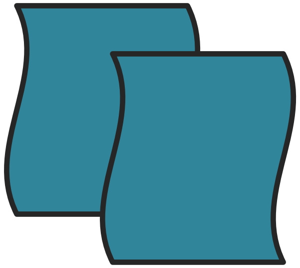
- Database
- Graphs
- Media



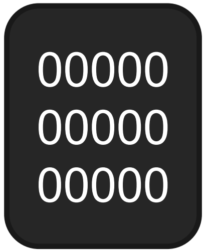
- Many questions … How do we design the:
  - compute-capable memory & controllers?
  - processor chip?
  - software and hardware interfaces?
  - system software and languages?
  - algorithms?

Starting Simple: Data Copy and Initialization

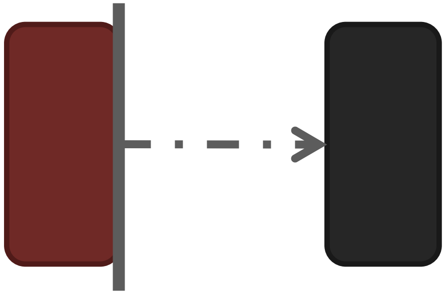
memmove & *memcpy*: 5% cycles in Google's datacenter [Kanev+ ISCA'15]



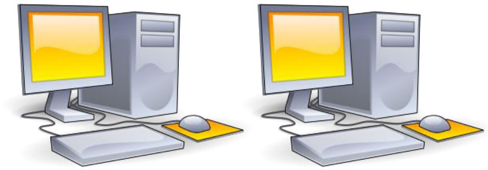
Forking



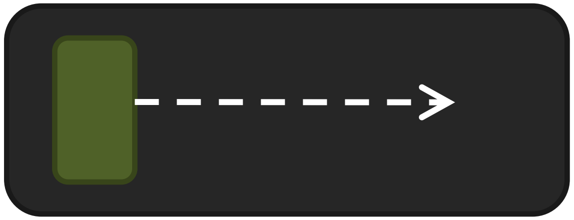
Zero initialization
(e.g., security)



Checkpointing



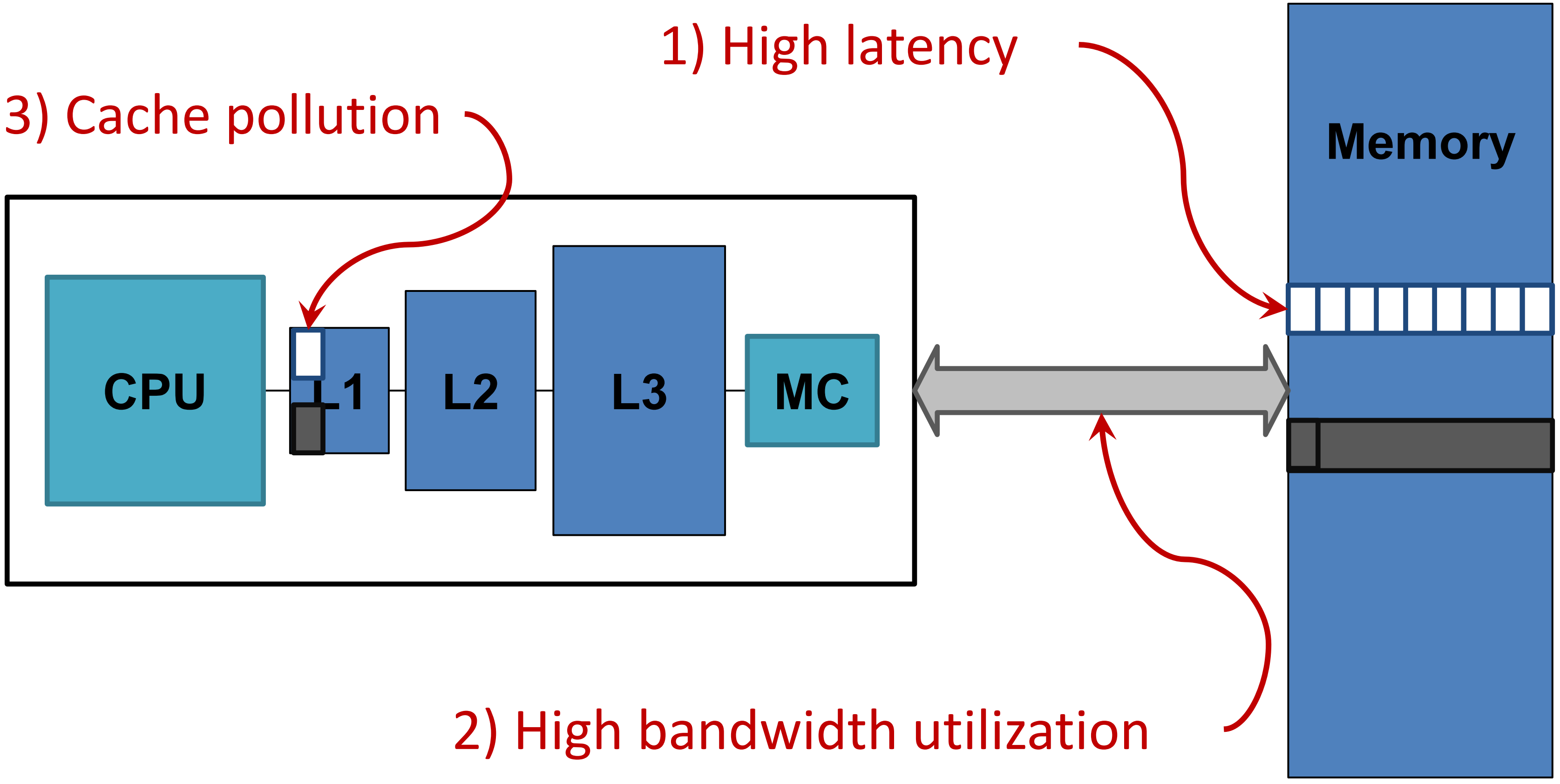
VM Cloning
Deduplication



Page Migration

• • •
Many more

Today's Systems: Bulk Data Copy



1) High latency

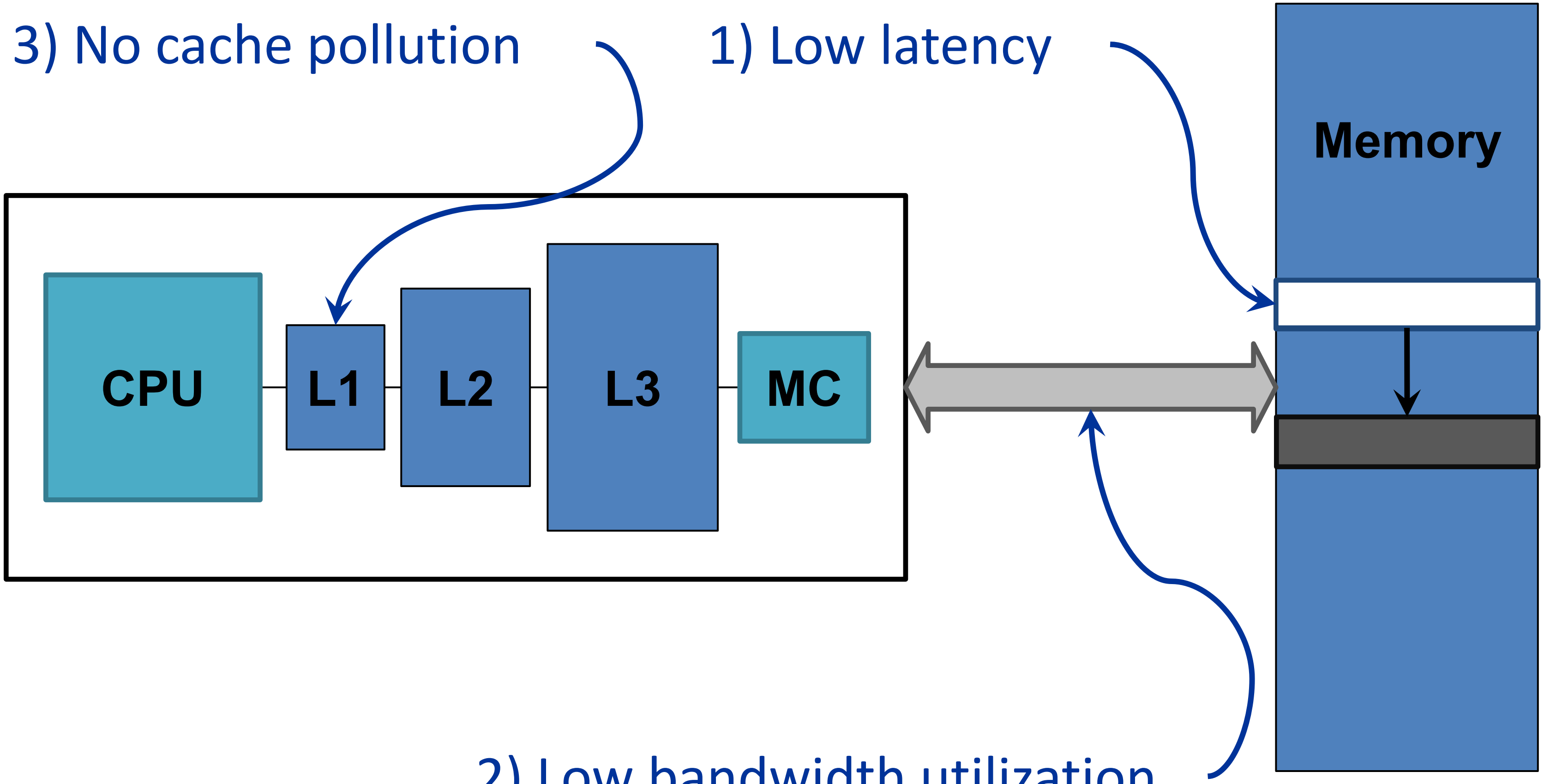
3) Cache pollution

2) High bandwidth utilization

4) Unwanted data movement

1046ns, 3.6uJ (for 4KB page copy via DMA)

Future Systems: In-Memory Copy



3) No cache pollution

1) Low latency

2) Low bandwidth utilization

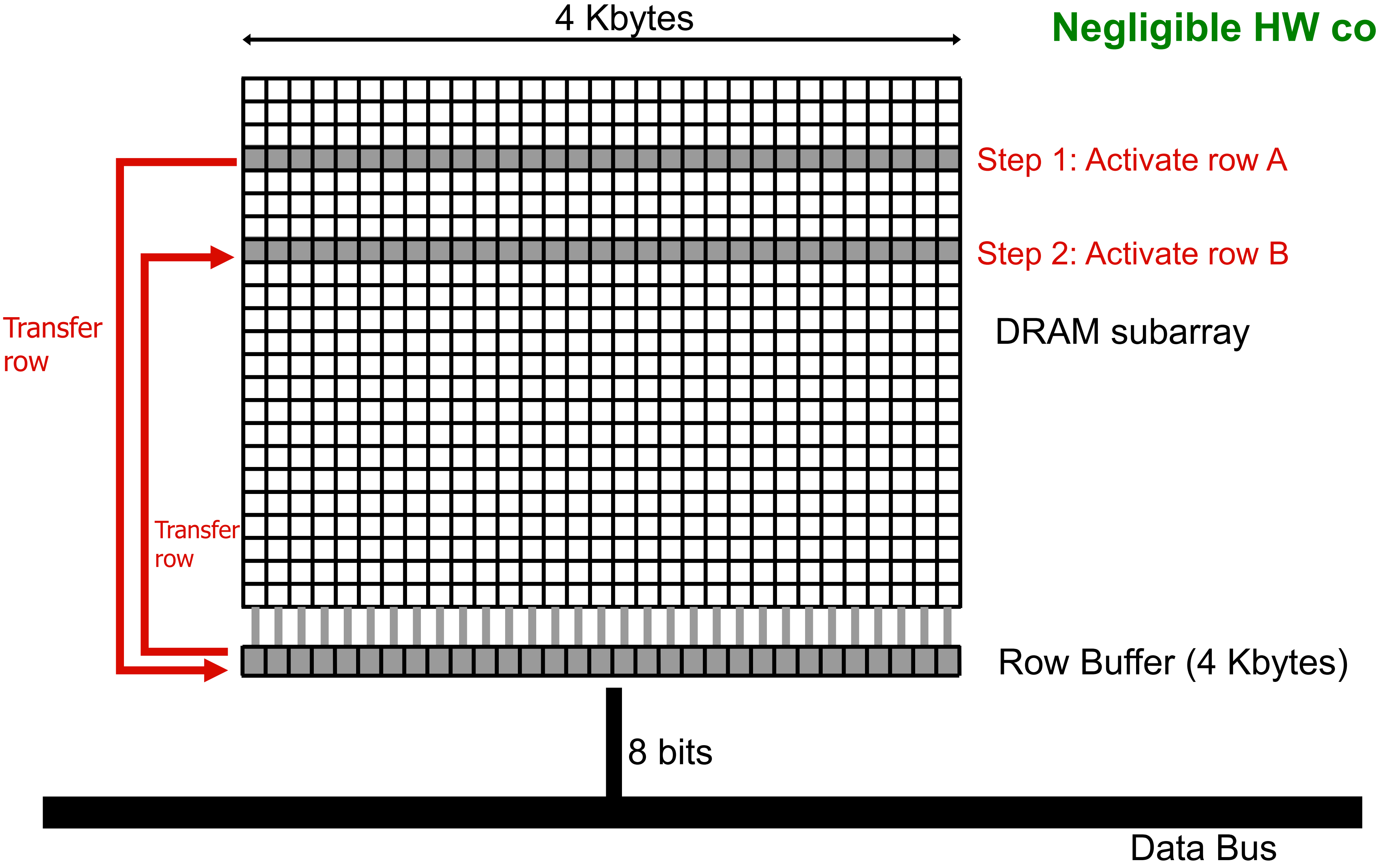
4) No unwanted data movement

1046ns, 3.6uJ → 90ns, 0.04uJ

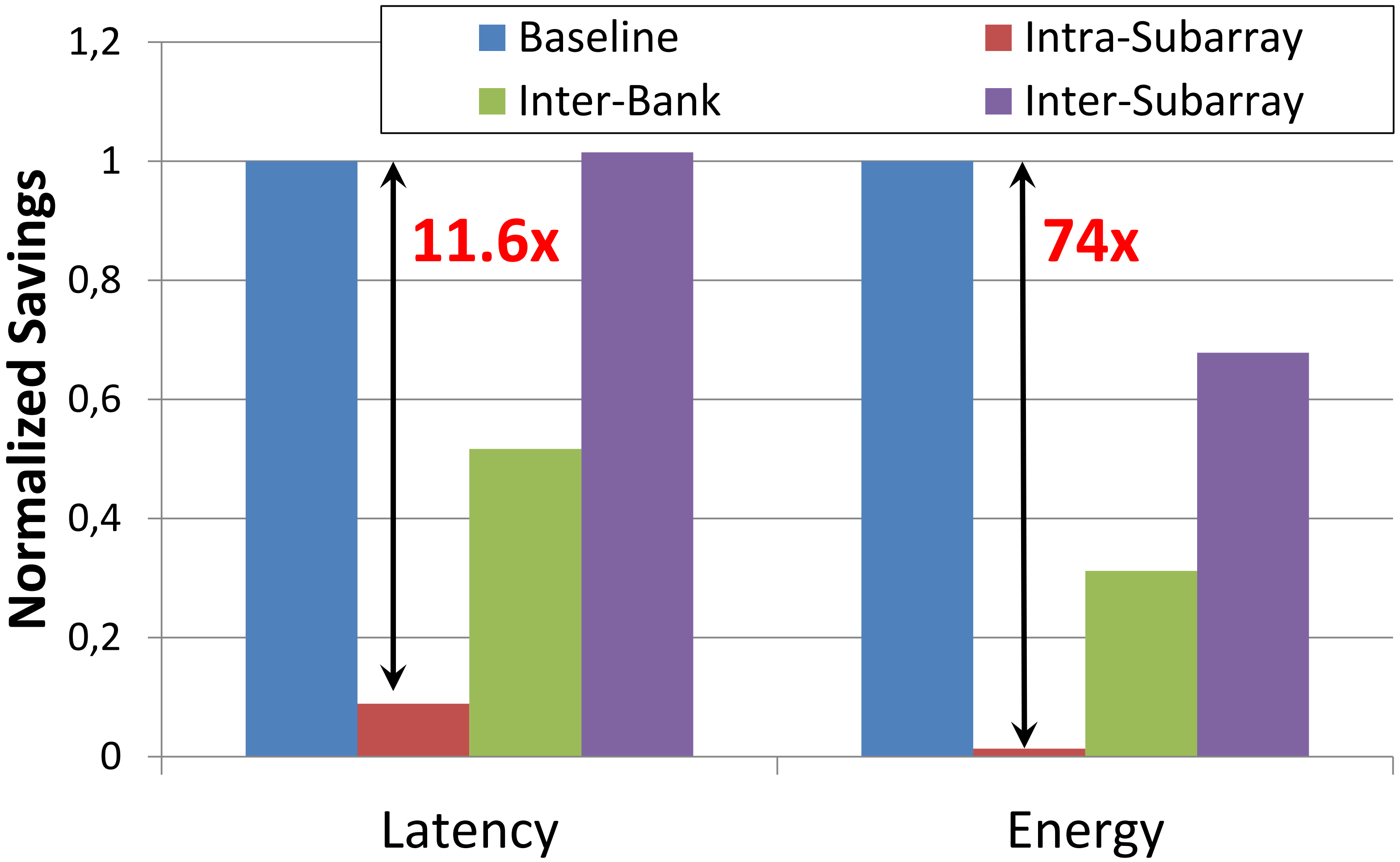
RowClone: In-DRAM Row Copy

Idea: Two consecutive ACTivates

Negligible HW cost



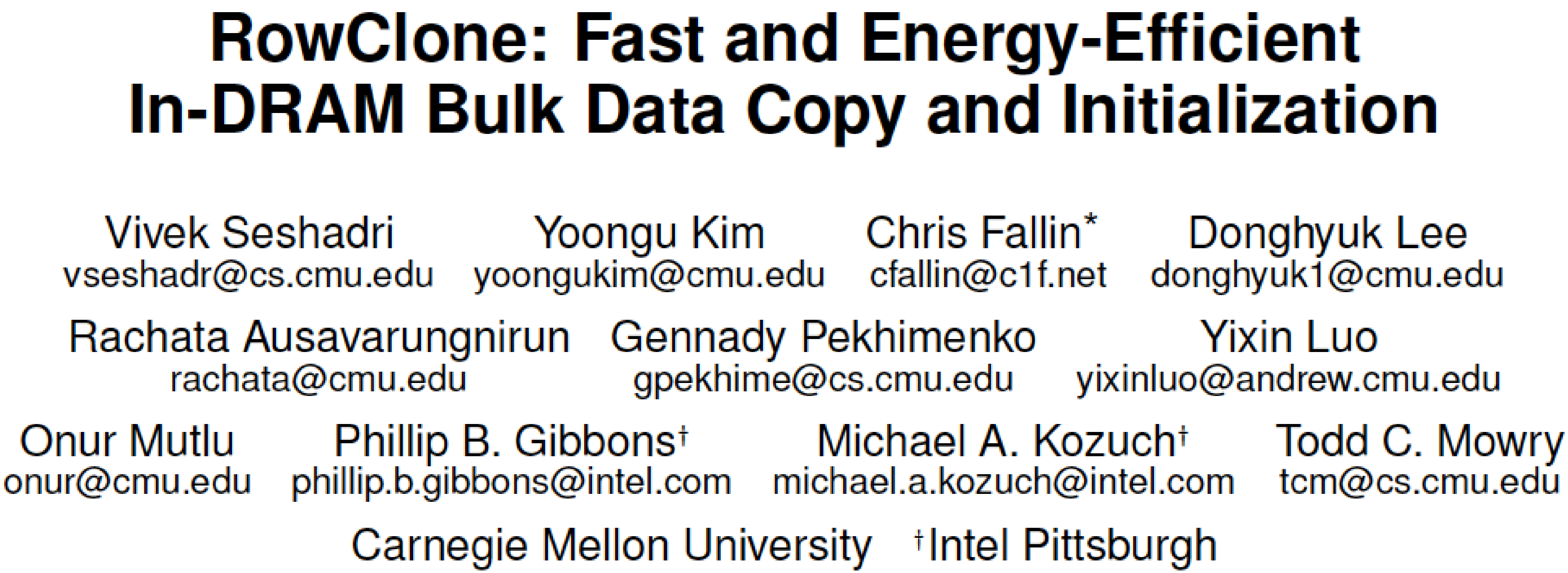
RowClone: Latency and Energy Savings



Seshadri et al., "RowClone: Fast and Efficient In-DRAM Copy and Initialization of Bulk Data," MICRO 2013.

More on RowClone

- Vivek Seshadri, Yoongu Kim, Chris Fallin, Donghyuk Lee, Rachata Ausavarungnirun, Gennady Pekhimenko, Yixin Luo, Onur Mutlu, Michael A. Kozuch, Phillip B. Gibbons, and Todd C. Mowry, **"RowClone: Fast and Energy-Efficient In-DRAM Bulk Data Copy and Initialization"** *Proceedings of the 46th International Symposium on Microarchitecture (**MICRO**)*, Davis, CA, December 2013. [Slides (pptx) (pdf)] [Lightning Session Slides (pptx) (pdf)] [Poster (pptx) (pdf)]



RowClone: Fast and Energy-Efficient
In-DRAM Bulk Data Copy and Initialization

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Yoongu Kim yoongukim@cmu.edu
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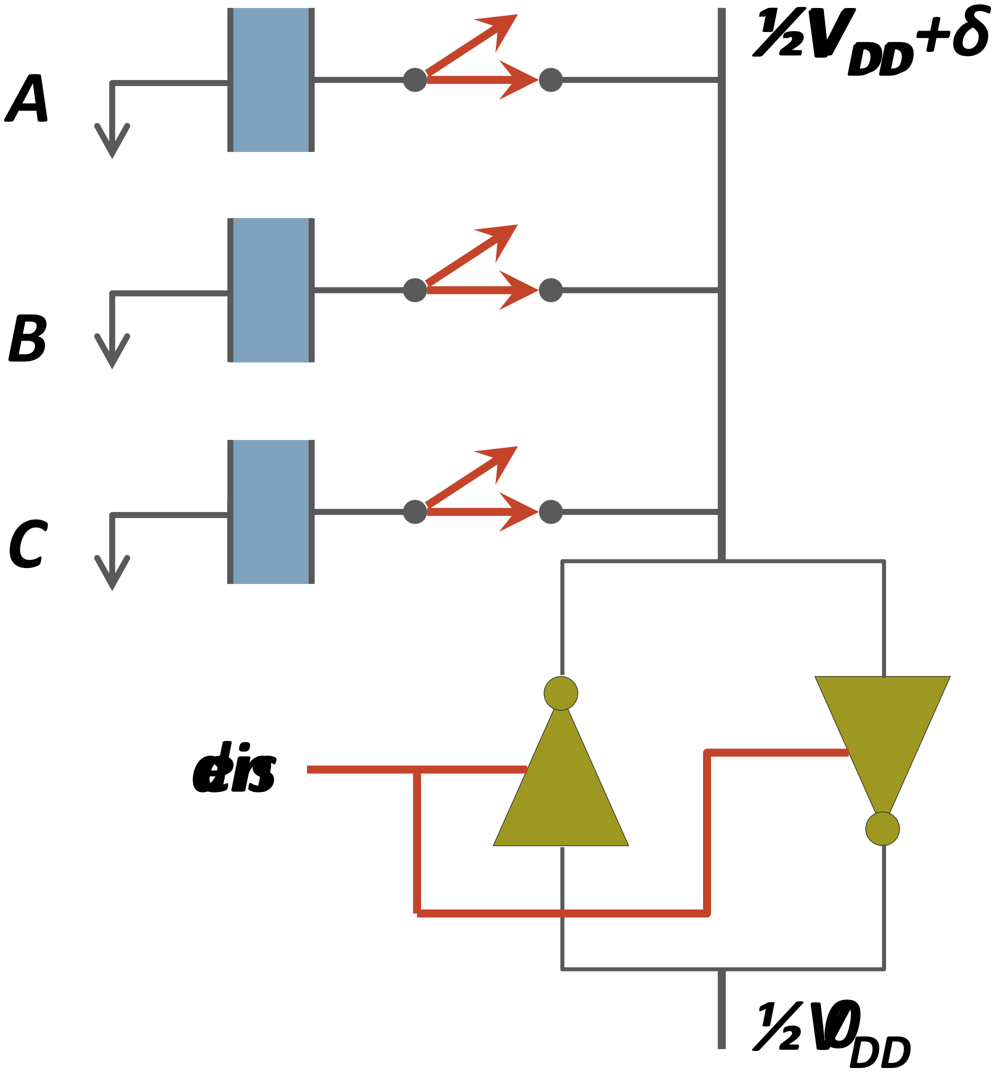
Donghyuk Lee donghyuk1@cmu.edu
Rachata Ausavarungnirun rachata@cmu.edu
Gennady Pekhimenko gpekhime@cs.cmu.edu
Yixin Luo yixinluo@andrew.cmu.edu
Onur Mutlu onur@cmu.edu
Phillip B. Gibbons† phillip.b.gibbons@intel.com
Michael A. Kozuch† michael.a.kozuch@intel.com
Todd C. Mowry tcm@cs.cmu.edu
Carnegie Mellon University †Intel Pittsburgh

In-Memory Bulk Bitwise Operations

- We can support in-DRAM COPY, ZERO, AND, OR, NOT, MAJ
- At low cost
- Using analog computation capability of DRAM
  - Idea: activating multiple rows performs computation
- 30-60X performance and energy improvement
  - Seshadri+, "Ambit: In-Memory Accelerator for Bulk Bitwise Operations Using Commodity DRAM Technology," MICRO 2017.

- New memory technologies enable even more opportunities
  - Memristors, resistive RAM, phase change mem, STT-MRAM, …
  - Can operate on data with minimal movement

In-DRAM AND/OR: Triple Row Activation



Final State

AB + BC + AC

C(A + B) + ~C(AB)

Seshadri+, "Fast Bulk Bitwise AND and OR in DRAM", IEEE CAL 2015.

In-DRAM NOT: Dual Contact Cell

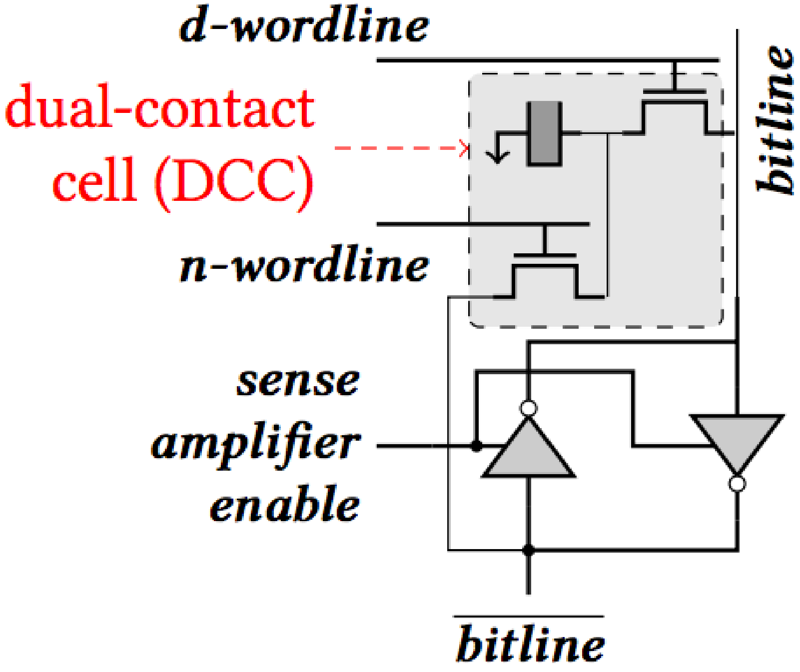
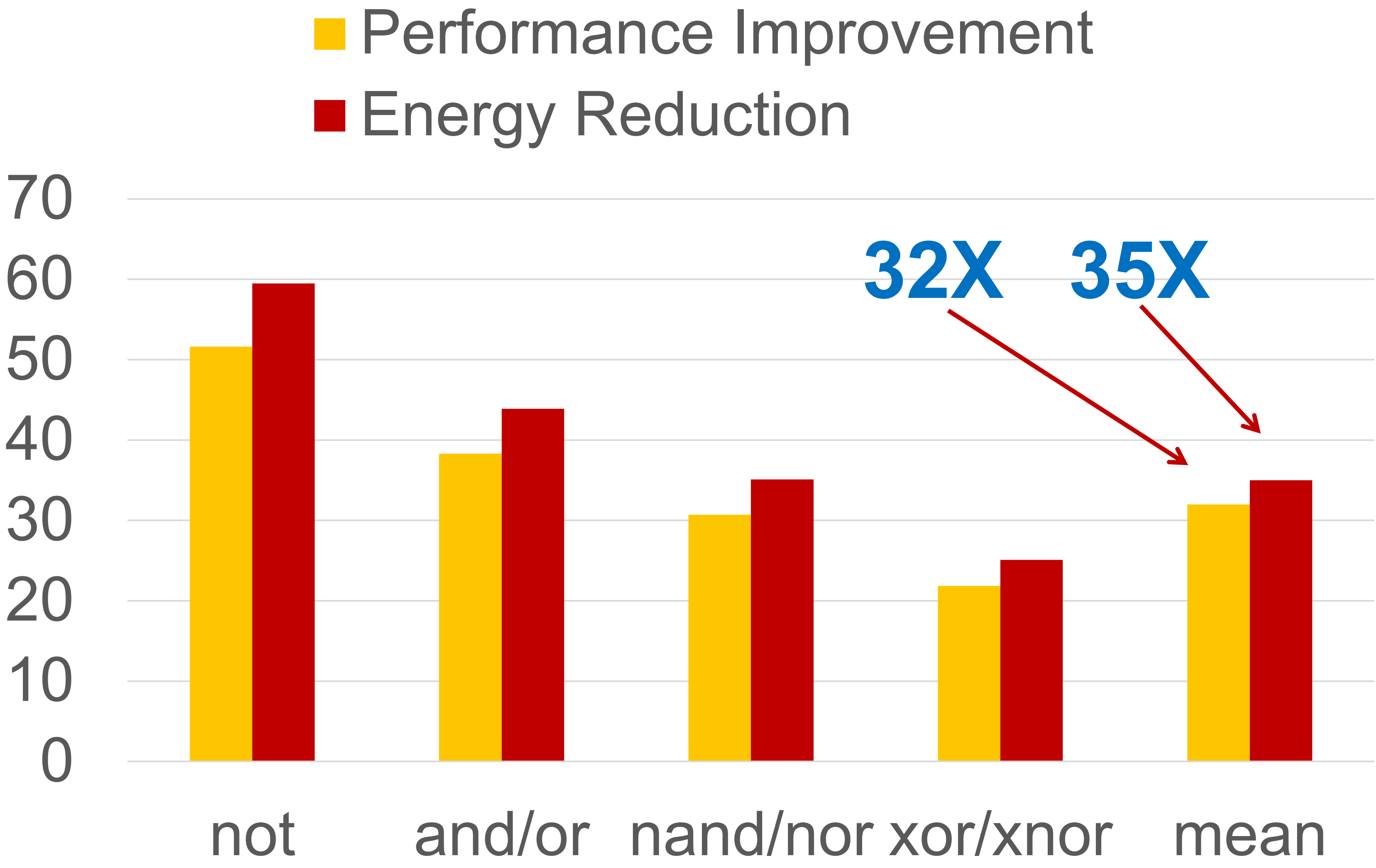


Figure 5: A dual-contact cell connected to both ends of a sense amplifier

Idea:
Feed the negated value in the sense amplifier into a special row

Seshadri+, "Ambit: In-Memory Accelerator for Bulk Bitwise Operations using Commodity DRAM Technology," MICRO 2017.

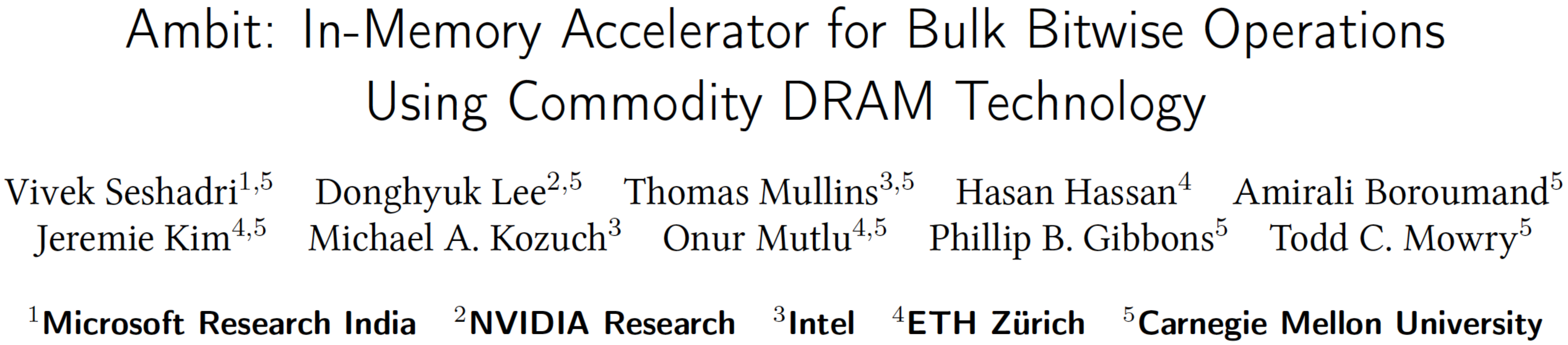
Ambit vs. DDR3: Performance and Energy



Seshadri+, "Ambit: In-Memory Accelerator for Bulk Bitwise Operations using Commodity DRAM Technology," MICRO 2017

More on In-DRAM Bitwise Operations

- Vivek Seshadri et al., "**Ambit: In-Memory Accelerator for Bulk Bitwise Operations Using Commodity DRAM Technology**," MICRO 2017.



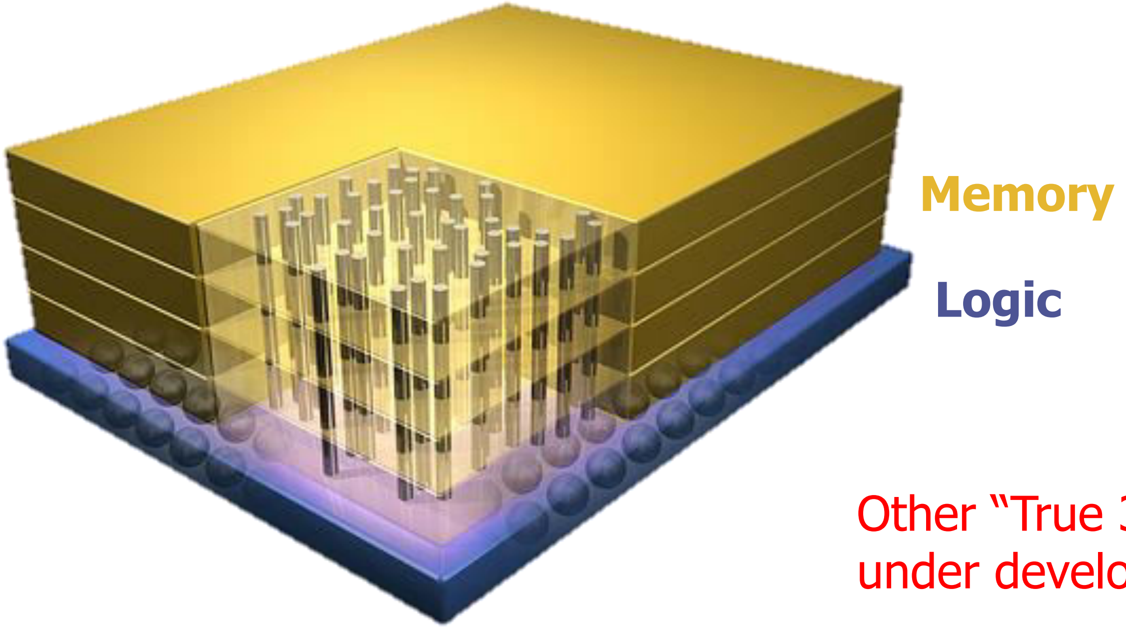
Ambit: In-Memory Accelerator for Bulk Bitwise Operations Using Commodity DRAM Technology

Vivek Seshadri[1,5] Donghyuk Lee[2,5] Thomas Mullins[3,5] Hasan Hassan[4] Amirali Boroumand[5]
Jeremie Kim[4,5] Michael A. Kozuch[3] Onur Mutlu[4,5] Phillip B. Gibbons[5] Todd C. Mowry[5]

[1]**Microsoft Research India** [2]**NVIDIA Research** [3]**Intel** [4]**ETH Zürich** [5]**Carnegie Mellon University**

Opportunity: 3D-Stacked Logic+Memory

Hybrid Memory Cube
CONSORTIUM



Other "True 3D" technologies
under development

Another Example: In-Memory Graph Processing

- Large graphs are everywhere (circa 2015)

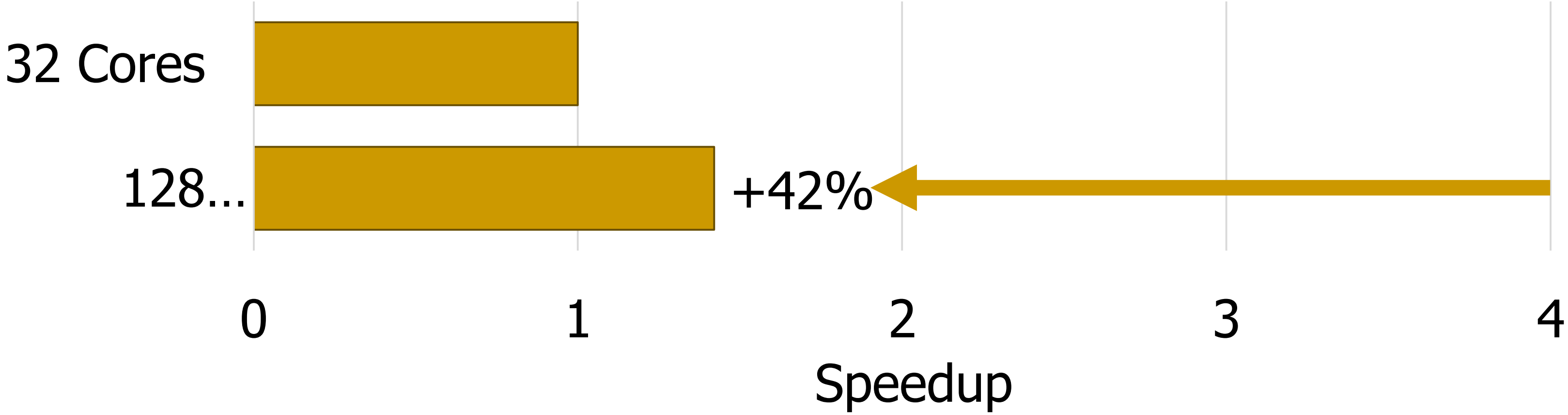
36 Million
Wikipedia Pages

1.4 Billion
Facebook Users

300 Million
Twitter Users

30 Billion
Instagram Photos

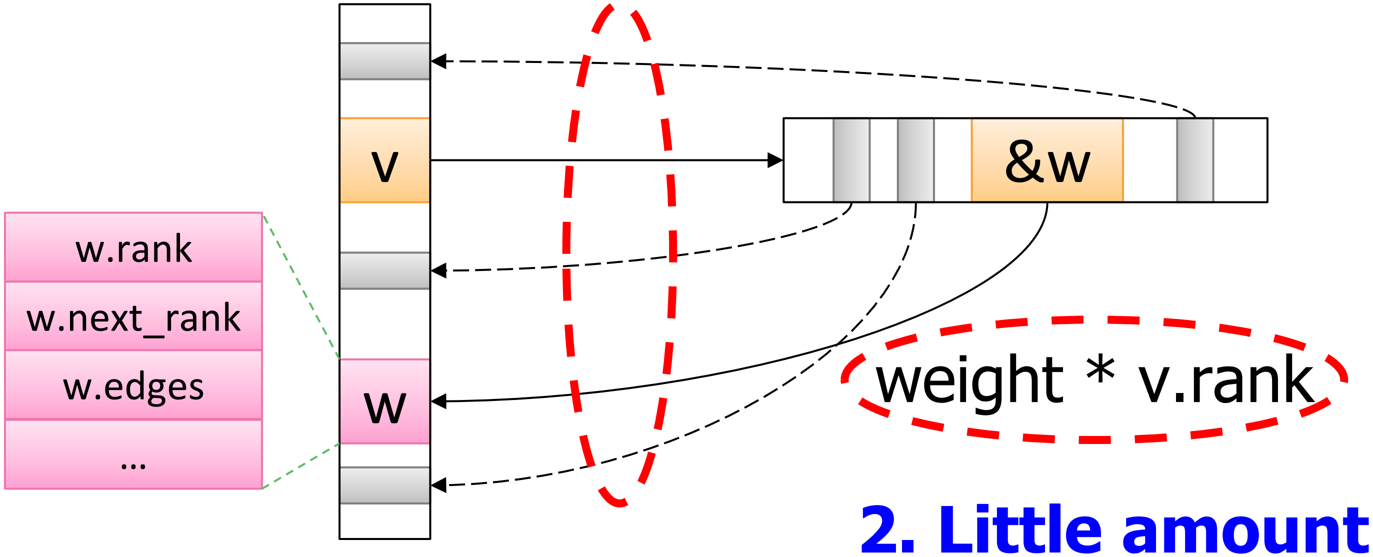
- Scalable large-scale graph processing is challenging



Key Bottlenecks in Graph Processing

```
for (v: graph.vertices) {
    for (w: v.successors) {
        w.next_rank += weight * v.rank;
    }
}
```

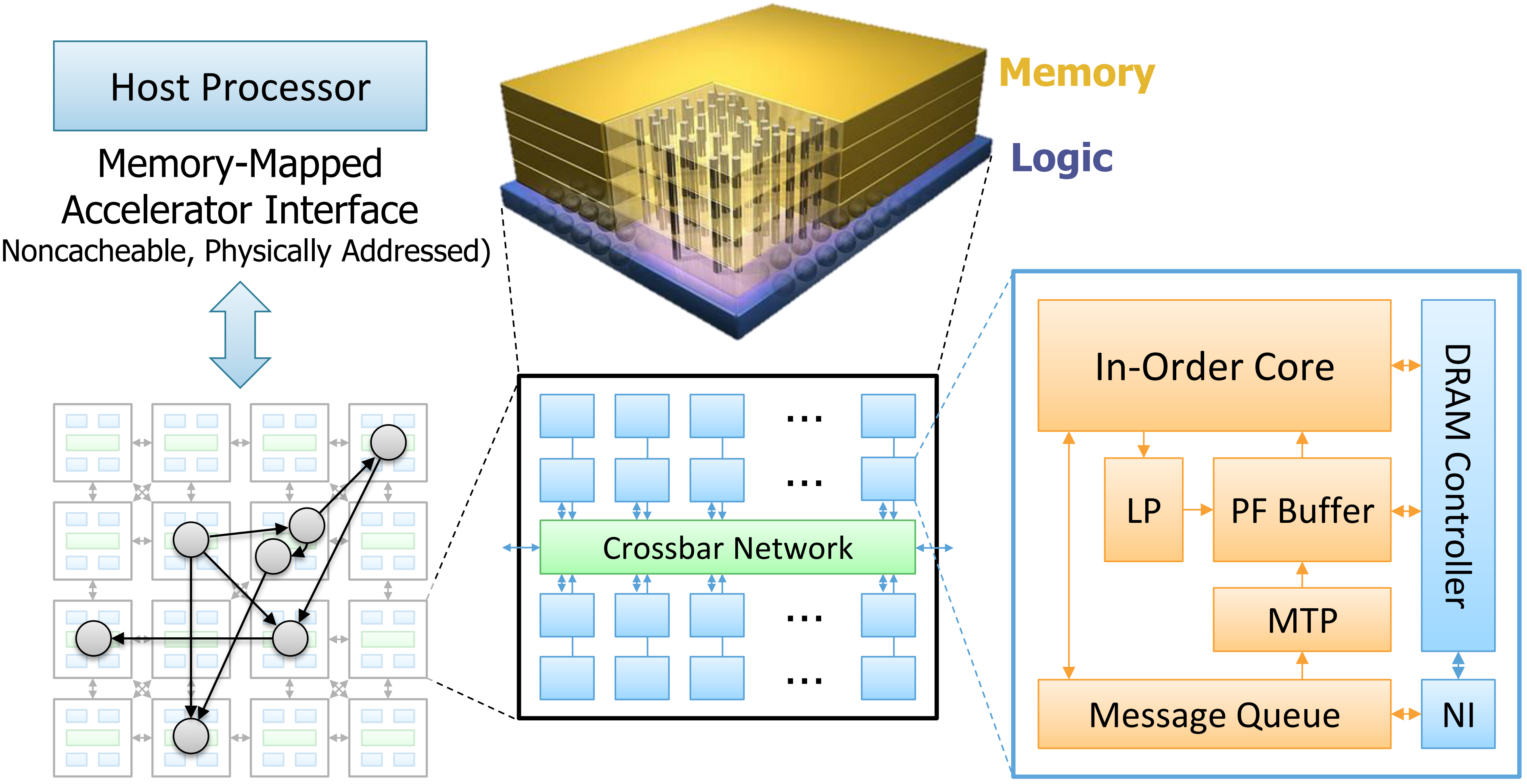
1. Frequent random memory accesses



2. Little amount of computation

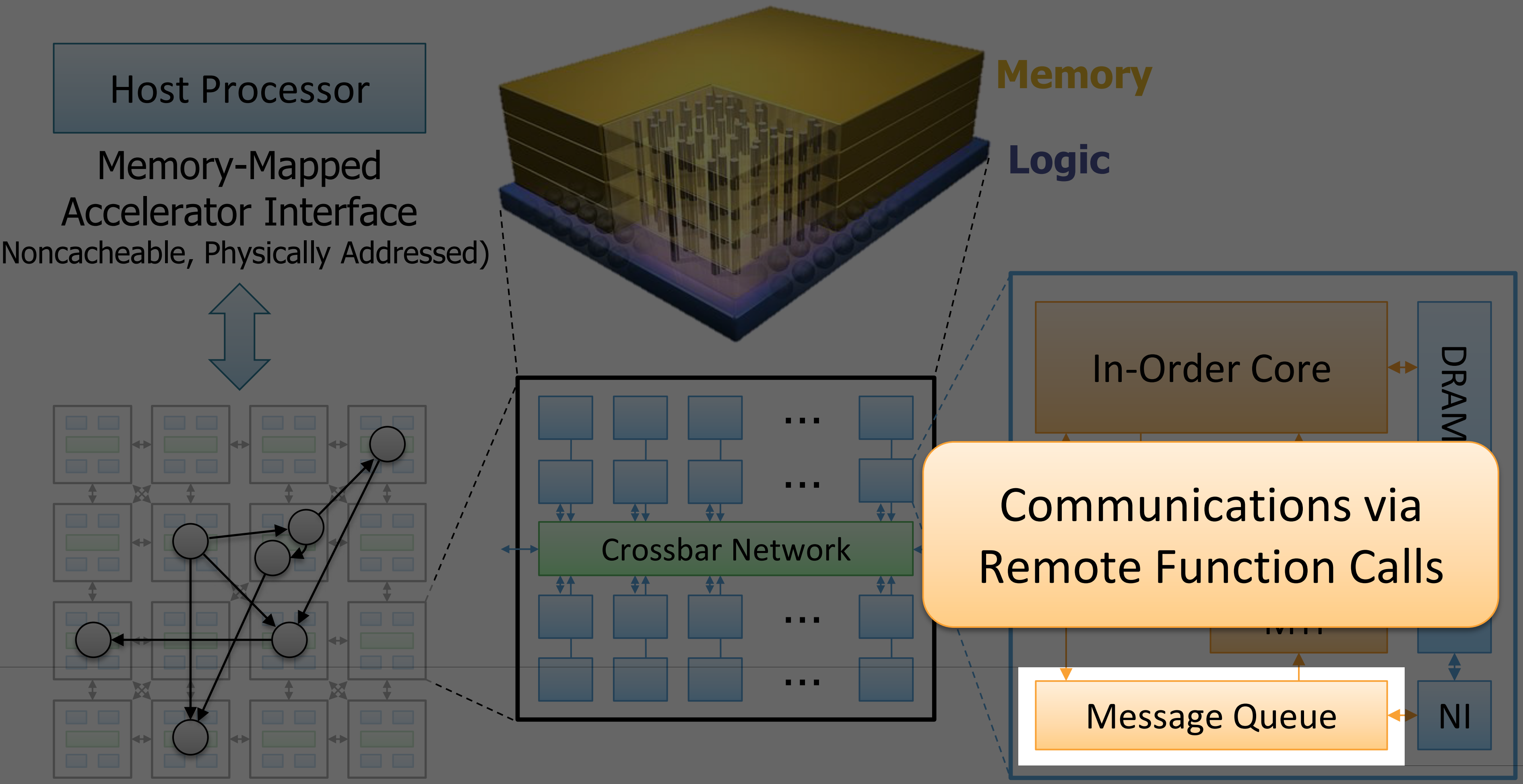
Tesseract System for Graph Processing

Interconnected set of 3D-stacked memory+logic chips with simple cores



SAFARI Ahn+, "A Scalable Processing-in-Memory Accelerator for Parallel Graph Processing" ISCA 2015.

Tesseract System for Graph Processing



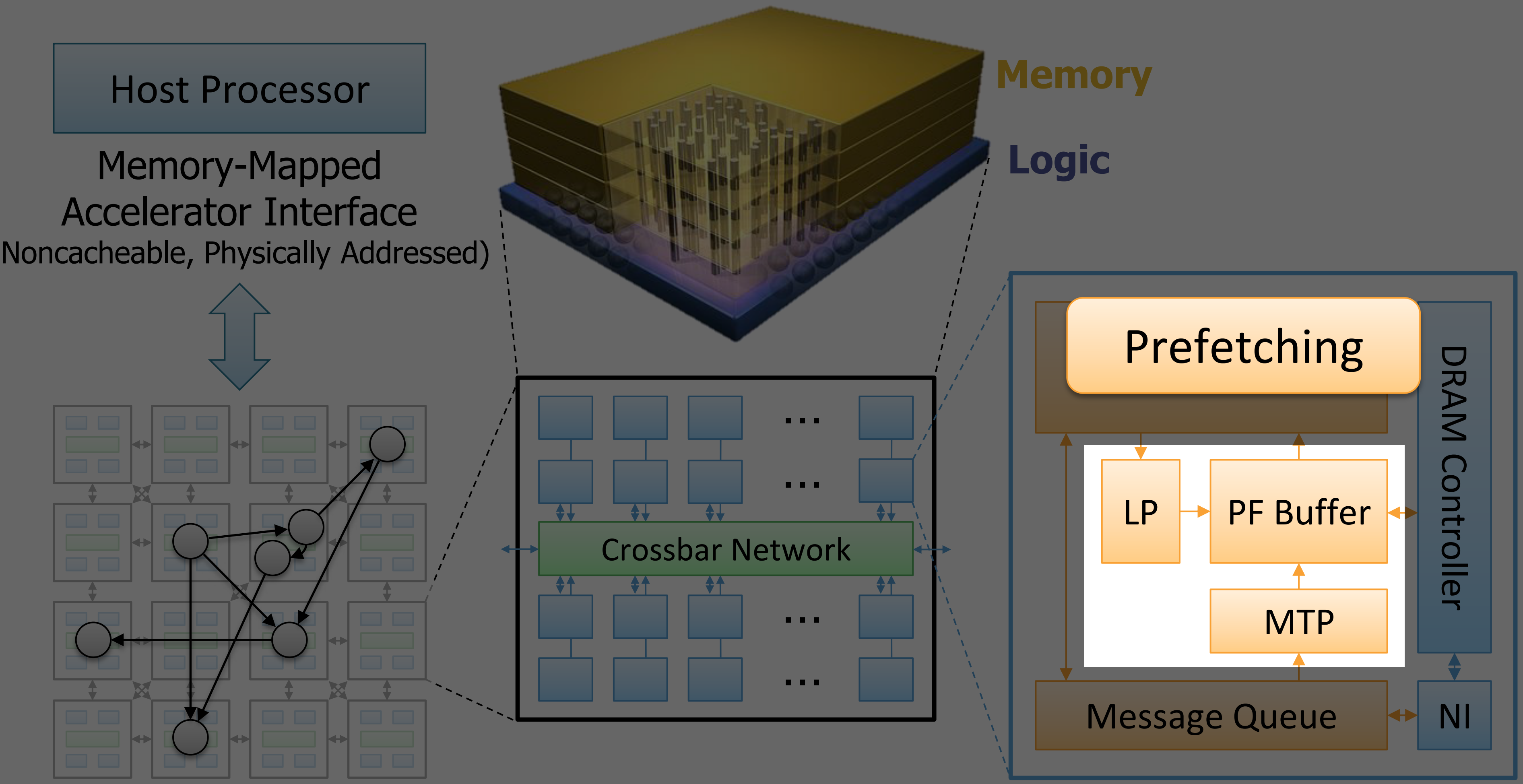
Host Processor

Memory-Mapped Accelerator Interface

(Noncacheable, Physically Addressed)

Communications via Remote Function Calls

Tesseract System for Graph Processing

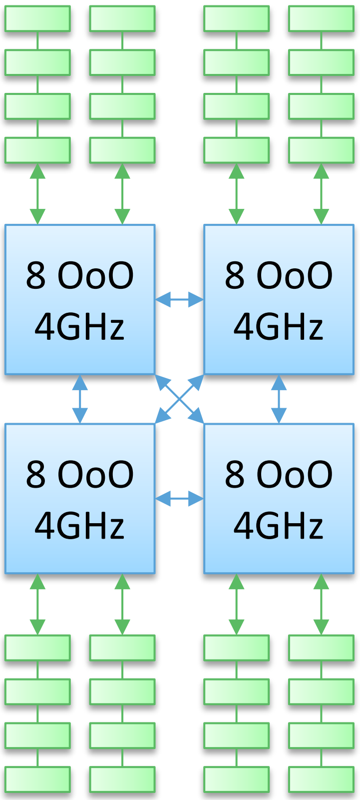


Host Processor

Memory-Mapped
Accelerator Interface
Noncacheable, Physically Addressed)

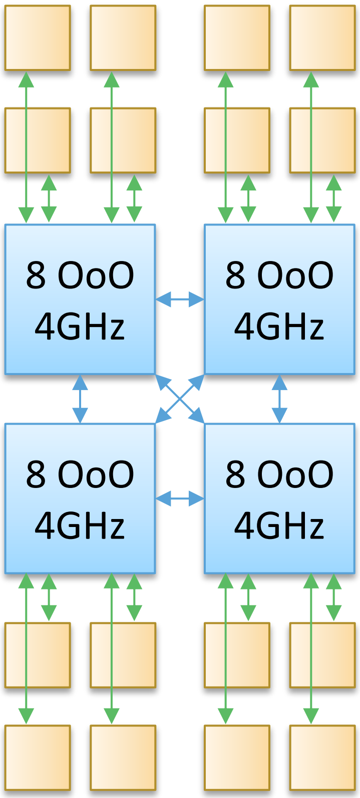
Evaluated Systems

DDR3-OoO



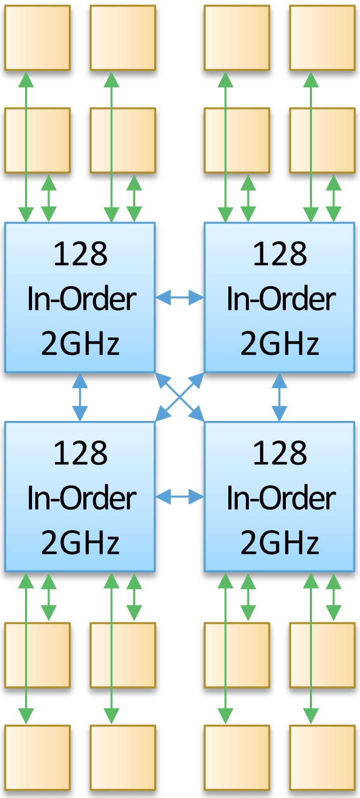
102.4GB/s

HMC-OoO



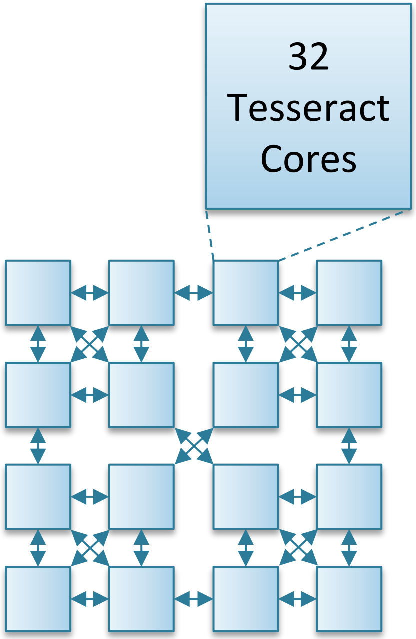
640GB/s

HMC-MC



640GB/s

Tesseract

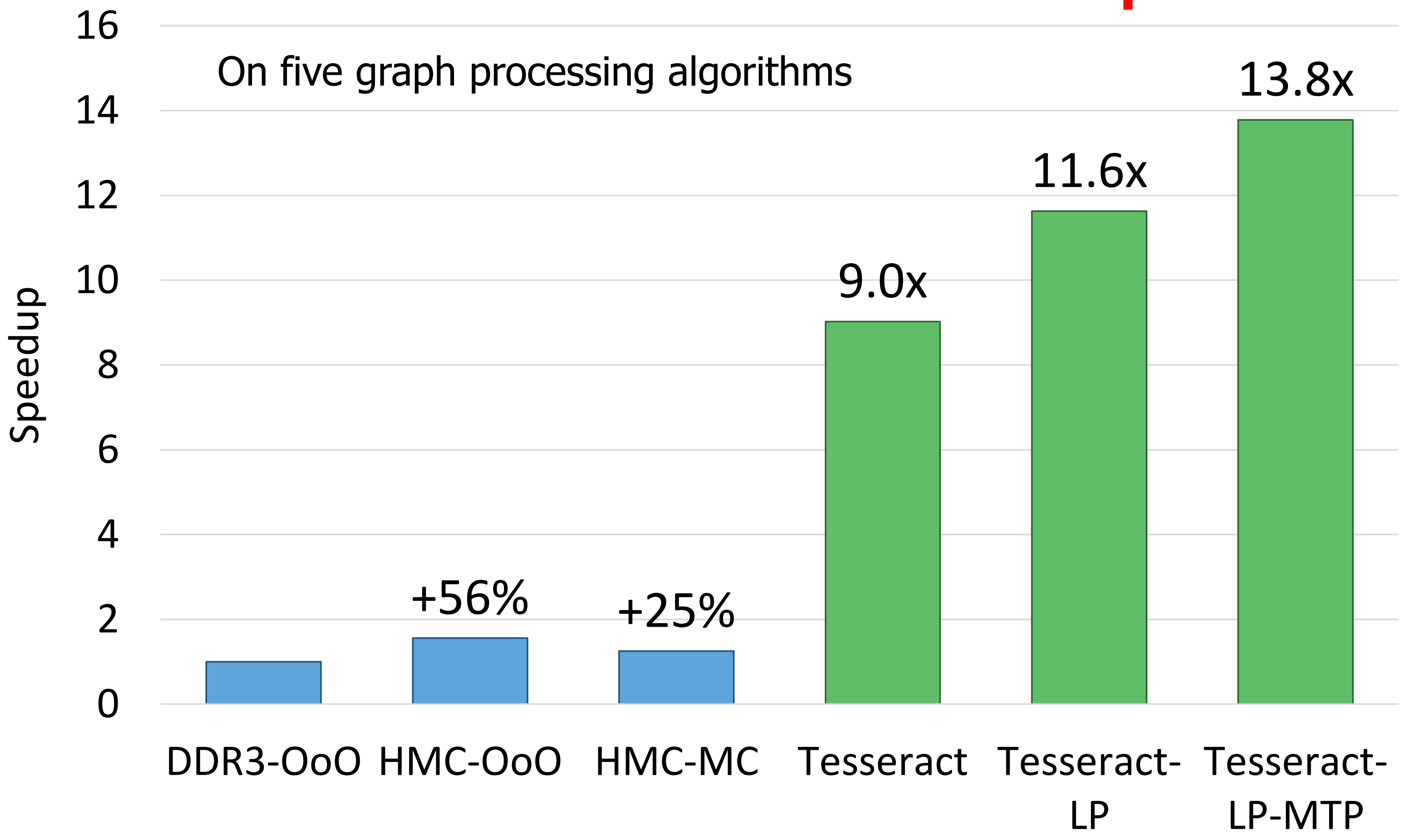


8TB/s

Ahn+, "A Scalable Processing-in-Memory Accelerator for Parallel Graph Processing" ISCA 2015.

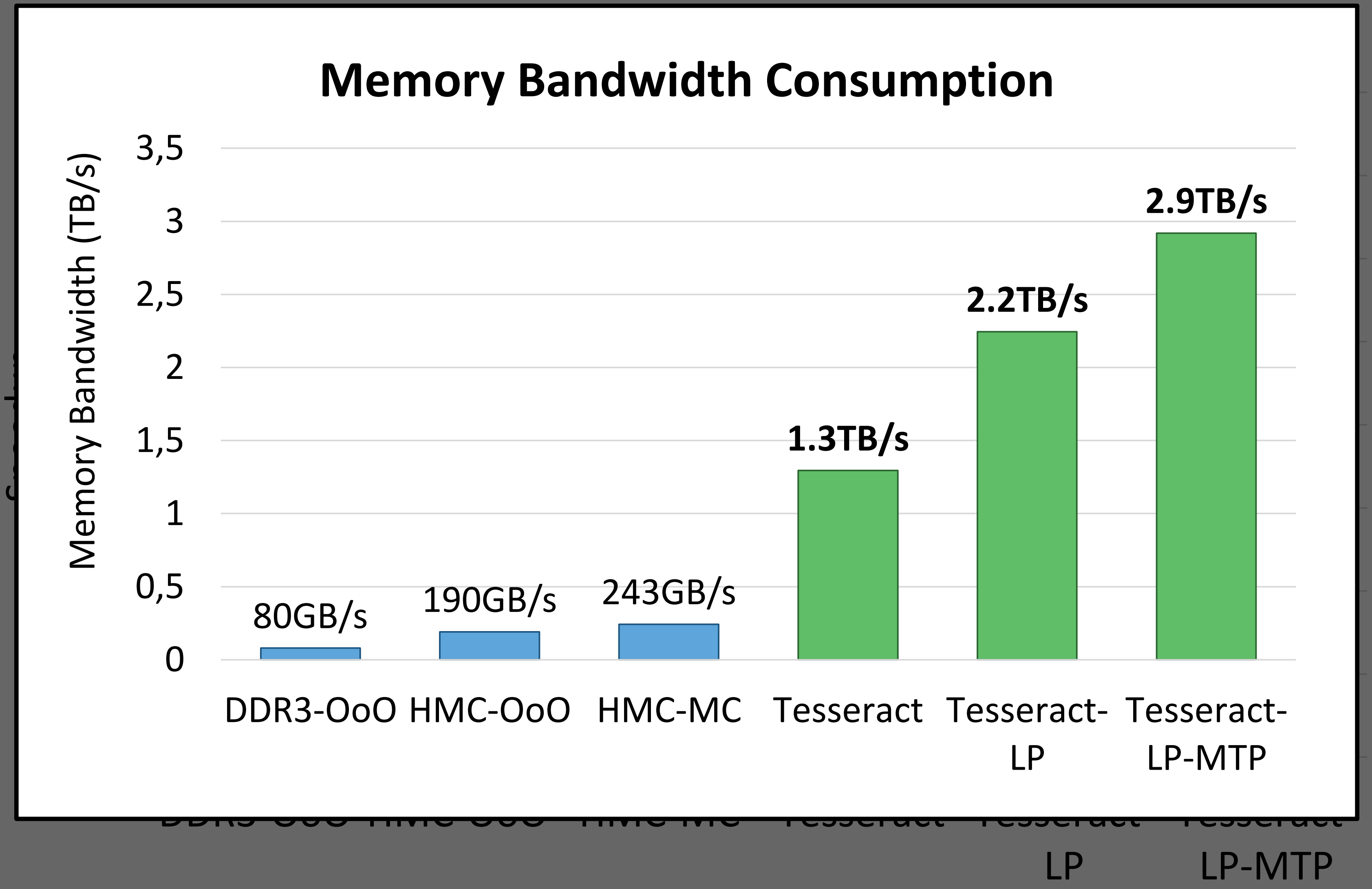
Tesseract Graph Processing Performance

>13X Performance Improvement

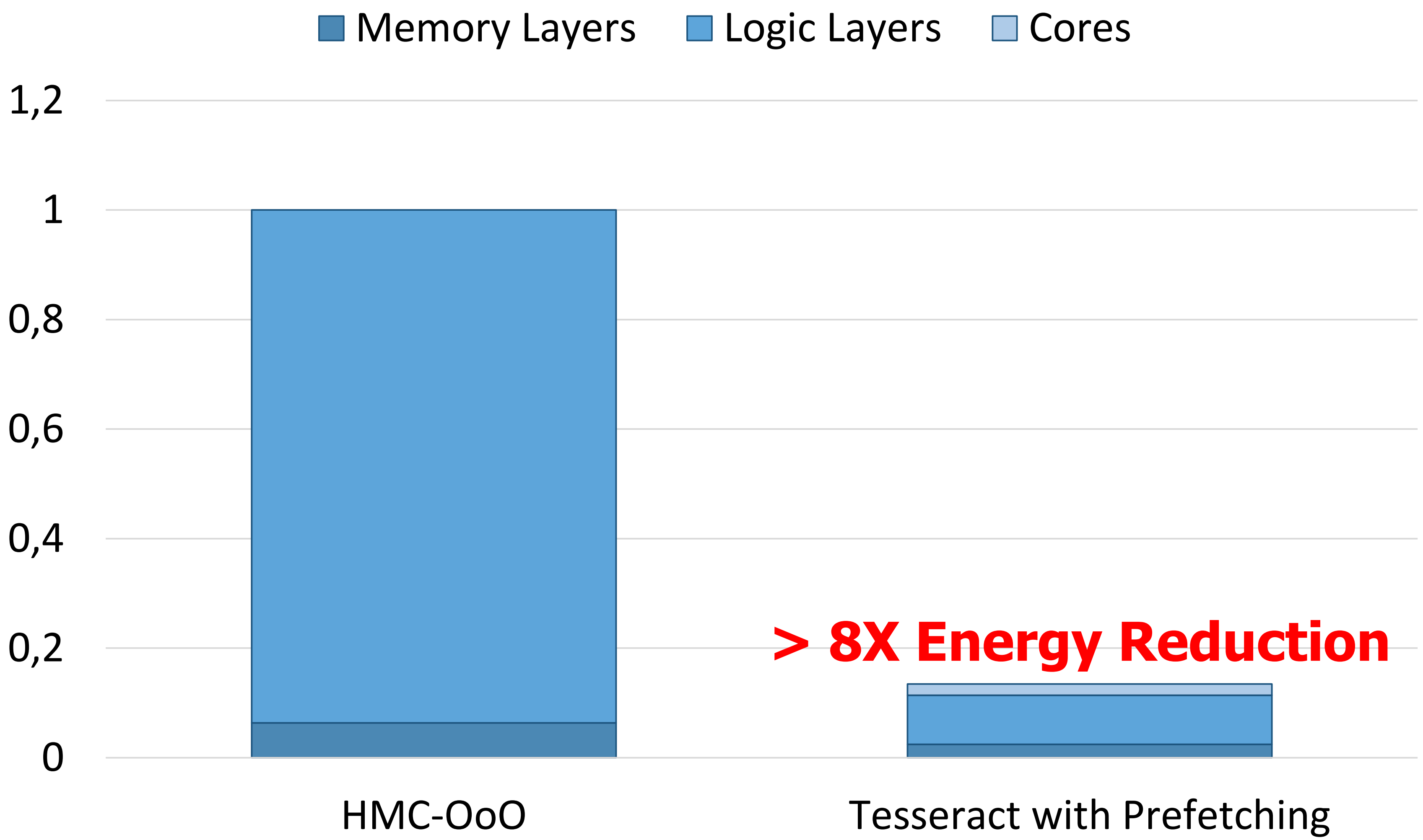


Ahn+, "A Scalable Processing-in-Memory Accelerator for Parallel Graph Processing" ISCA 2015.

Tesseract Graph Processing Performance



Tesseract Graph Processing System Energy

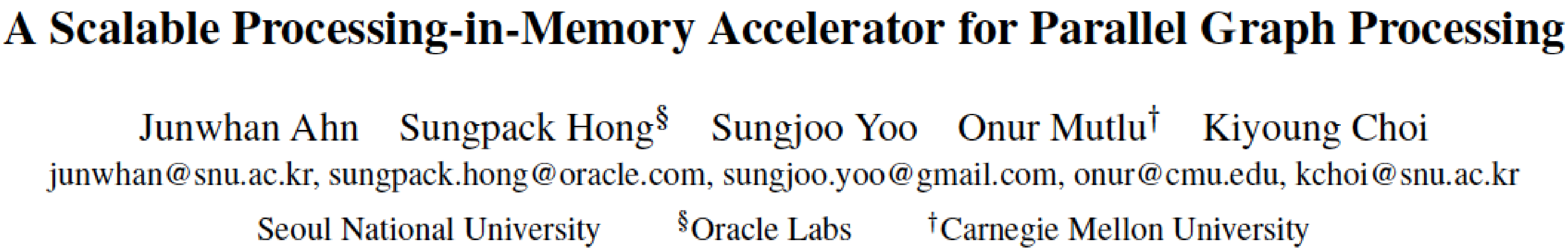


> 8X Energy Reduction

Ahn+, "A Scalable Processing-in-Memory Accelerator for Parallel Graph Processing" ISCA 2015.

More on Tesseract

- Junwhan Ahn, Sungpack Hong, Sungjoo Yoo, Onur Mutlu, and Kiyoung Choi,
  "A Scalable Processing-in-Memory Accelerator for Parallel Graph Processing"
  Proceedings of the 42nd International Symposium on Computer Architecture (***ISCA***), Portland, OR, June 2015.
  [Slides (pdf)] [Lightning Session Slides (pdf)]



A Scalable Processing-in-Memory Accelerator for Parallel Graph Processing

Junwhan Ahn Sungpack Hong§ Sungjoo Yoo Onur Mutlu† Kiyoung Choi
junwhan@snu.ac.kr, sungpack.hong@oracle.com, sungjoo.yoo@gmail.com, onur@cmu.edu, kchoi@snu.ac.kr
Seoul National University §Oracle Labs †Carnegie Mellon University

Challenge and Opportunity for Future

Fundamentally
Energy-Efficient
(Data-Centric)
Computing Architectures

Three Key Issues in Future Platforms

- Fundamentally Secure/Reliable/Safe Architectures

- Fundamentally Energy-Efficient Architectures
  - Memory-centric (Data-centric) Architectures

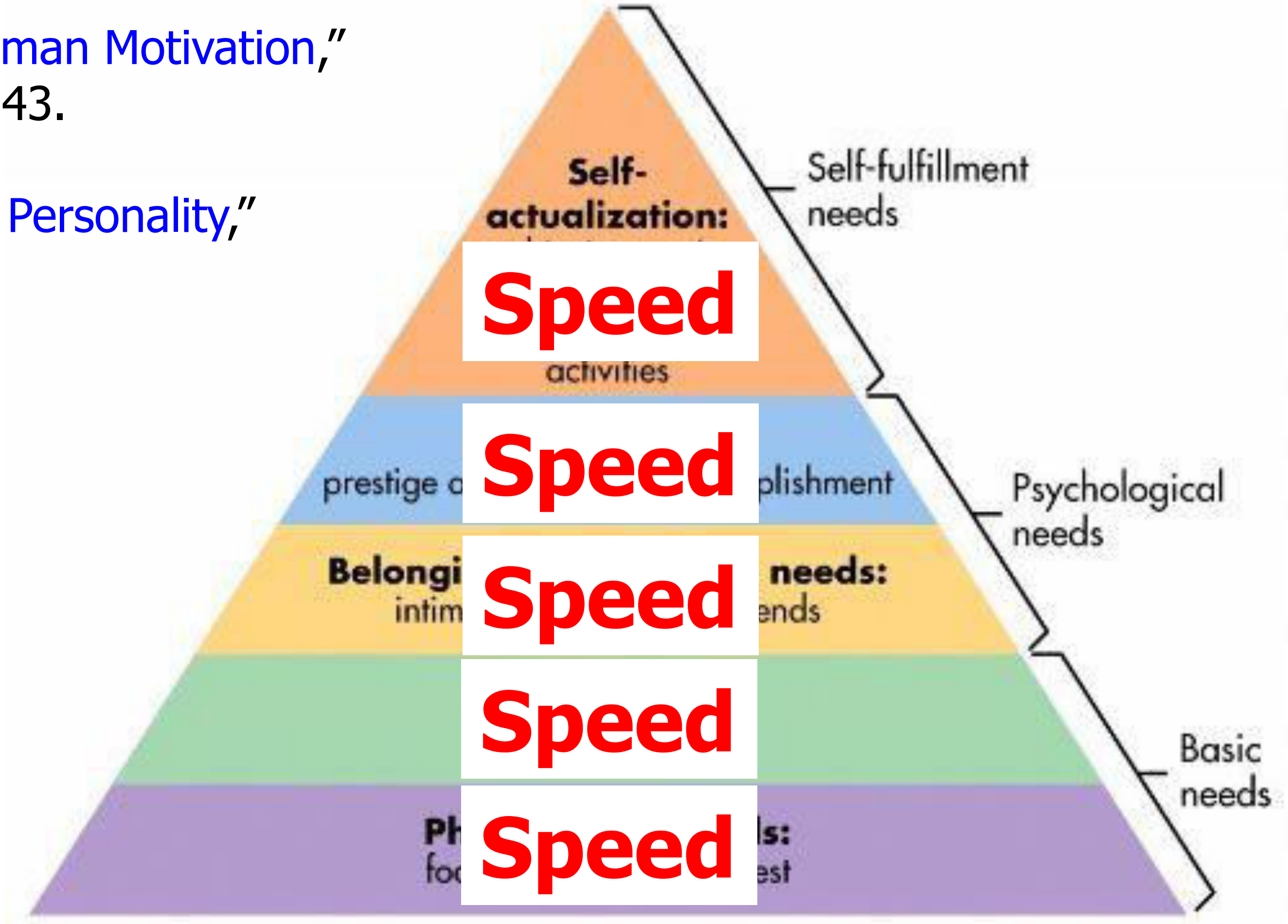
- Fundamentally Low Latency Architectures

Source: http://spectrum.ieee.org/image/MjYzMzAyMg.jpeg

Maslow's Hierarchy of Needs, A Third Time

Maslow, "A Theory of Human Motivation,"
Psychological Review, 1943.

Maslow, "Motivation and Personality,"
Book, 1954-1970.



Source: https://www.simplypsychology.org/maslow.html

See Backup Slides for Latency…

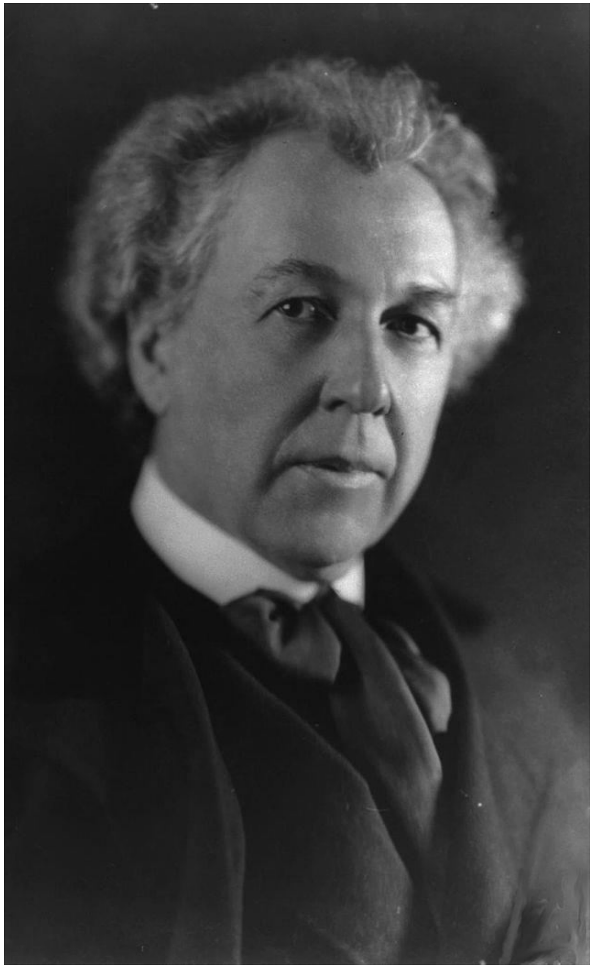
Challenge and Opportunity for Future

Fundamentally
Low-Latency
Computing Architectures

Concluding Remarks

A Quote from A Famous Architect

- "architecture […] based upon principle, and not upon precedent"

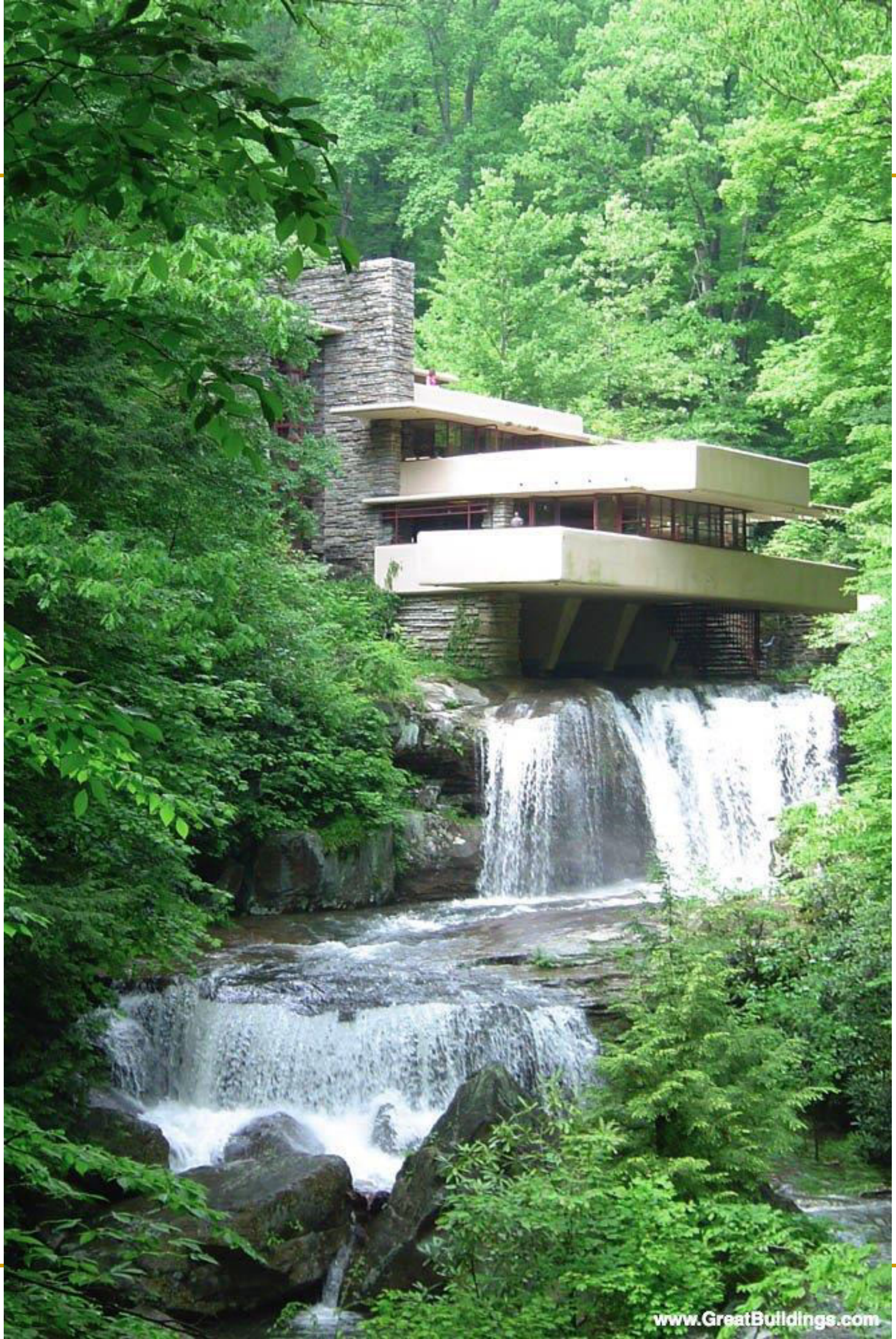


Precedent-Based Design?

- “architecture […] based upon principle, and not upon precedent”

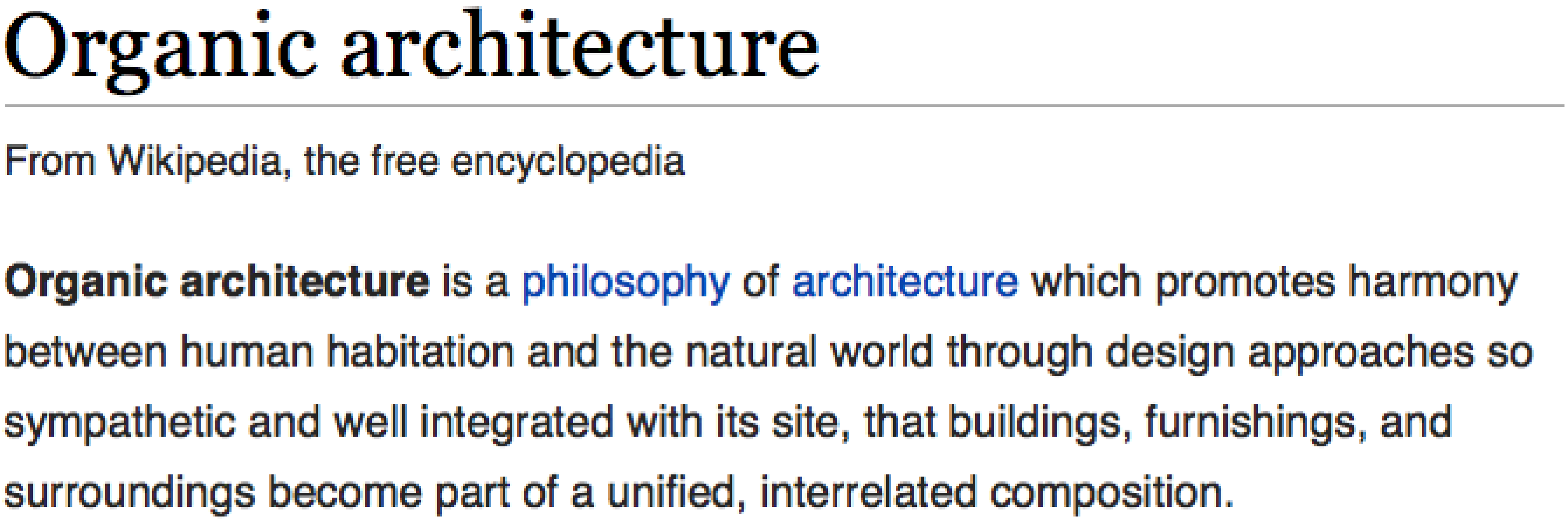
Principled Design

- “architecture […] based upon principle, and not upon precedent”



www.GreatBuildings.com

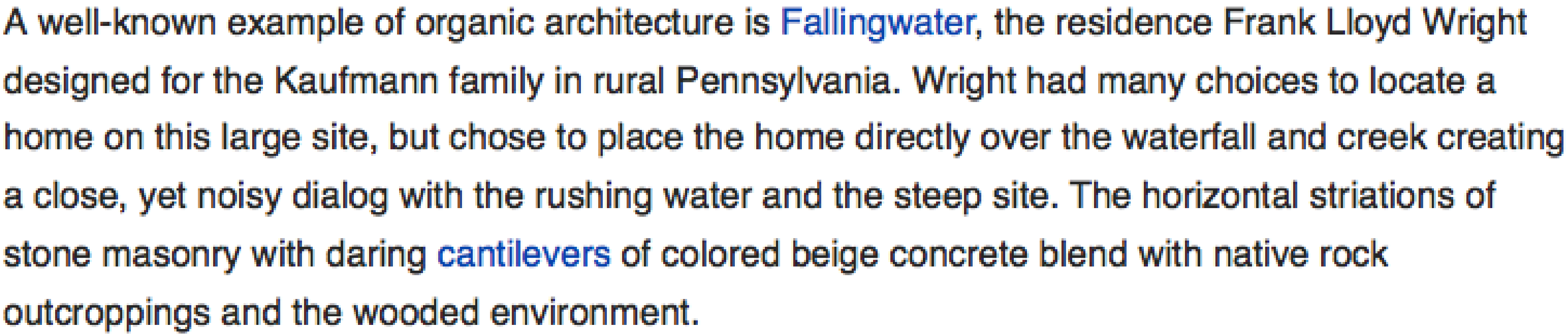
The Overarching Principle



Organic architecture

From Wikipedia, the free encyclopedia

Organic architecture is a philosophy of architecture which promotes harmony between human habitation and the natural world through design approaches so sympathetic and well integrated with its site, that buildings, furnishings, and surroundings become part of a unified, interrelated composition.



A well-known example of organic architecture is Fallingwater, the residence Frank Lloyd Wright designed for the Kaufmann family in rural Pennsylvania. Wright had many choices to locate a home on this large site, but chose to place the home directly over the waterfall and creek creating a close, yet noisy dialog with the rushing water and the steep site. The horizontal striations of stone masonry with daring cantilevers of colored beige concrete blend with native rock outcroppings and the wooded environment.

Another Example: Precedent-Based Design

Source: http://cookiemagik.deviantart.com/art/Train-station-207266944

Principled Design

Source: By Toni_V, CC BY-SA 2.0, https://commons.wikimedia.org/w/index.php?curid=4087256

Another Principled Design

Source: By Martín Gómez Tagle - Lisbon, Portugal, CC BY-SA 3.0, https://commons.wikimedia.org/w/index.php?curid=13764903

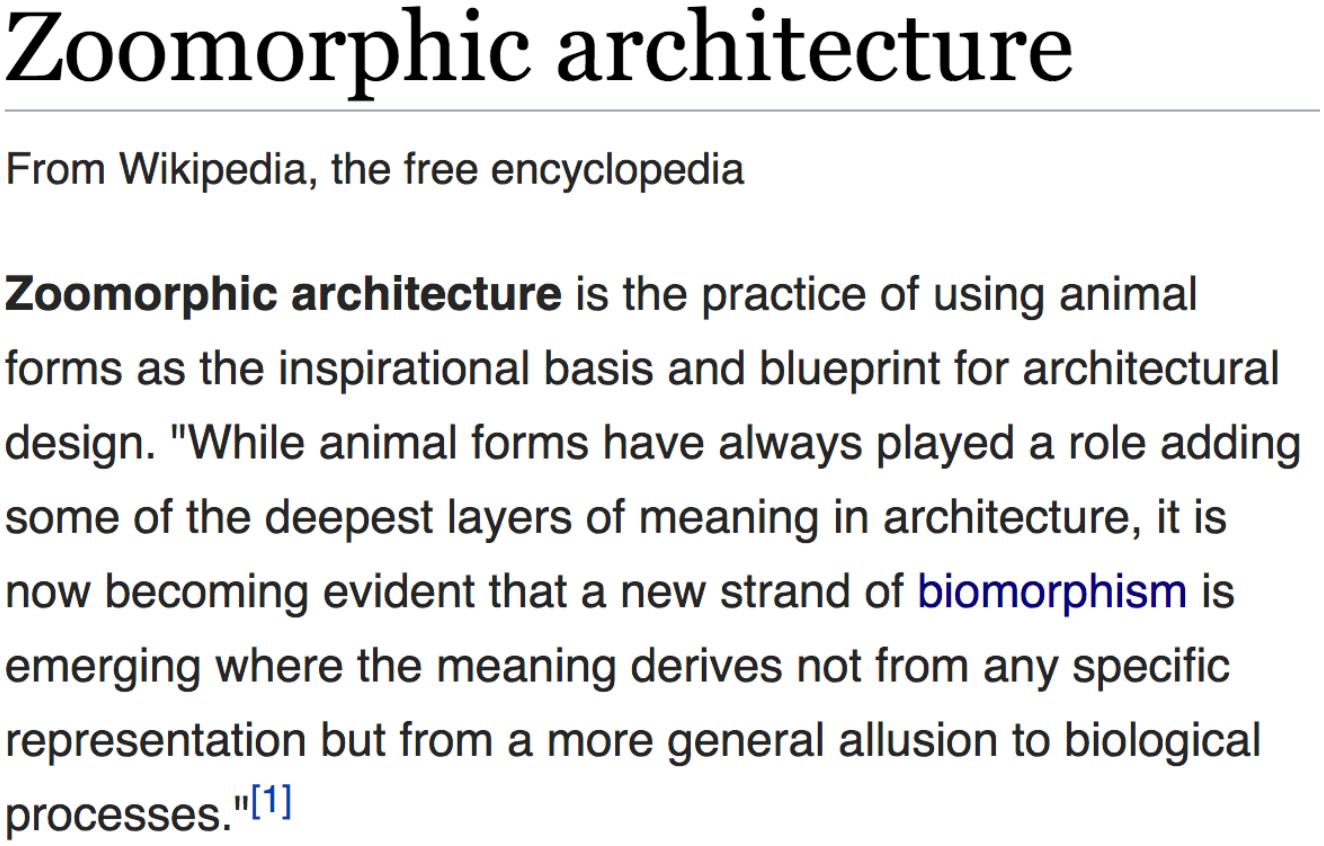
Source: http://www.arcspace.com/exhibitions/unsorted/santiago-calatrava/

Principle Applied to Another Structure

Source: By 準建築人手札網站 Forgemind ArchiMedia - Flickr: IMG_2489.JPG, CC BY 2.0, https://commons.wikimedia.org/w/index.php?curid=51493556, https://en.wikipedia.org/wiki/Santiago_Calatrava

Source: https://www.dezeen.com/2016/08/29/santiago-calatrava-oculus-world-trade-center-transportation-hub-new-york-photographs-hufton-crow/

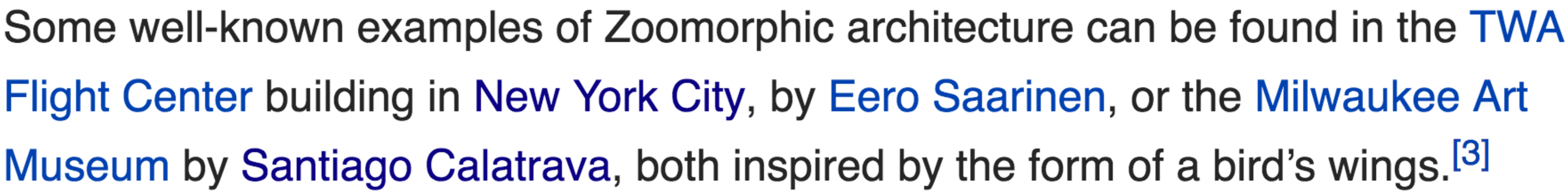
The Overarching Principle



Zoomorphic architecture

From Wikipedia, the free encyclopedia

Zoomorphic architecture is the practice of using animal forms as the inspirational basis and blueprint for architectural design. "While animal forms have always played a role adding some of the deepest layers of meaning in architecture, it is now becoming evident that a new strand of biomorphism is emerging where the meaning derives not from any specific representation but from a more general allusion to biological processes."[1]



Some well-known examples of Zoomorphic architecture can be found in the TWA Flight Center building in New York City, by Eero Saarinen, or the Milwaukee Art Museum by Santiago Calatrava, both inspired by the form of a bird’s wings.[3]

Overarching Principles for Computing?

Source: http://spectrum.ieee.org/image/MjYzMzAyMg.jpeg

Concluding Remarks

- It is time to design principled system architectures to solve the memory problem

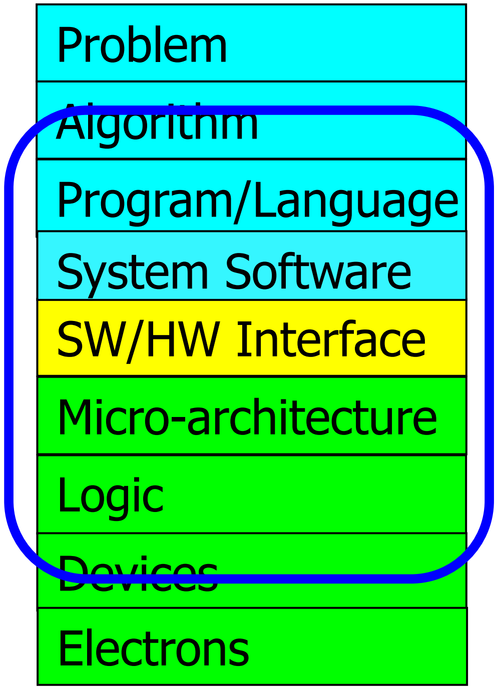
- Discover design principles for fundamentally secure and reliable computer architectures

- Design complete systems to be balanced and energy-efficient, i.e., data-centric (or memory-centric) and low latency

- Enable new and emerging memory architectures

- This can
  - Lead to **orders-of-magnitude** improvements
  - **Enable new applications & computing platforms**
  - **…**

We Need to Think Across the Stack



Problem

Algorithm

Program/Language

System Software

SW/HW Interface

Micro-architecture

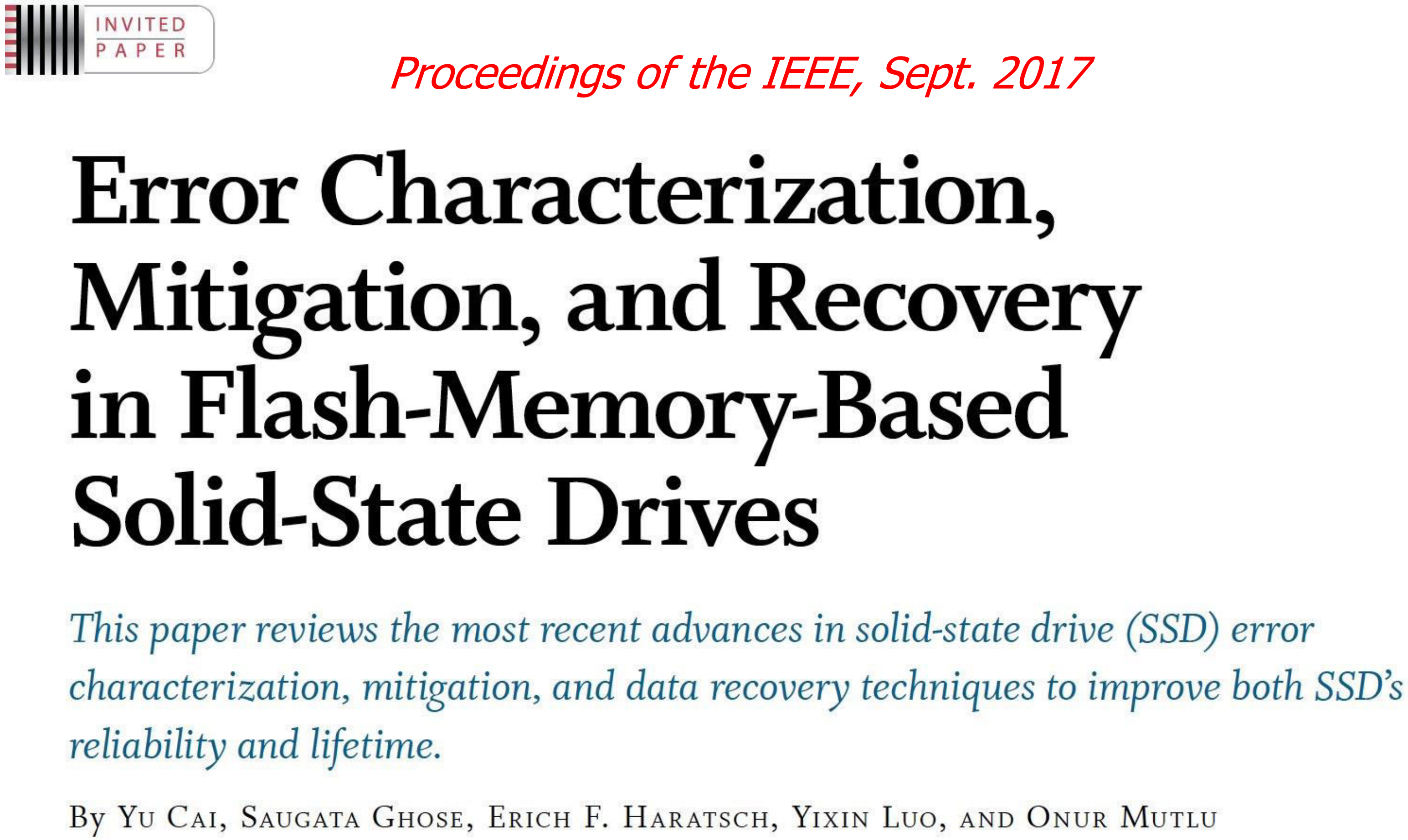
Logic

Devices

Electrons

If In Doubt, See Other Doubtful Technologies

- A very "doubtful" emerging technology
  - for at least two decades



INVITED PAPER

Proceedings of the IEEE, Sept. 2017

Error Characterization, Mitigation, and Recovery in Flash-Memory-Based Solid-State Drives

This paper reviews the most recent advances in solid-state drive (SSD) error characterization, mitigation, and data recovery techniques to improve both SSD's reliability and lifetime.

By Yu Cai, Saugata Ghose, Erich F. Haratsch, Yixin Luo, and Onur Mutlu

https://arxiv.org/pdf/1706.08642

Rethinking Memory System Design

(and the Platforms We Design Around It)

Onur Mutlu
omutlu@gmail.com
https://people.inf.ethz.ch/omutlu

January 17, 2018

Many-Core Computing: Hardware and Software

Acknowledgments

- My current and past students and postdocs
  - Rachata Ausavarungnirun, Abhishek Bhowmick, Amirali Boroumand, Rui Cai, Yu Cai, Kevin Chang, Saugata Ghose, Kevin Hsieh, Tyler Huberty, Ben Jaiyen, Samira Khan, Jeremie Kim, Yoongu Kim, Yang Li, Jamie Liu, Lavanya Subramanian, Donghyuk Lee, Yixin Luo, Justin Meza, Gennady Pekhimenko, Vivek Seshadri, Lavanya Subramanian, Nandita Vijaykumar, HanBin Yoon, Jishen Zhao, …
- My collaborators
  - Can Alkan, Chita Das, Phil Gibbons, Sriram Govindan, Norm Jouppi, Mahmut Kandemir, Mike Kozuch, Konrad Lai, Ken Mai, Todd Mowry, Yale Patt, Moinuddin Qureshi, Partha Ranganathan, Bikash Sharma, Kushagra Vaid, Chris Wilkerson, …

Funding Acknowledgments

- NSF
- GSRC
- SRC
- CyLab
- AMD, Google, Facebook, HP Labs, Huawei, IBM, Intel, Microsoft, Nvidia, Oracle, Qualcomm, Rambus, Samsung, Seagate, VMware

Some Open Source Tools

- Rowhammer
  - https://github.com/CMU-SAFARI/rowhammer
- Ramulator – Fast and Extensible DRAM Simulator
  - https://github.com/CMU-SAFARI/ramulator
- MemSim
  - https://github.com/CMU-SAFARI/memsim
- NOCulator
  - https://github.com/CMU-SAFARI/NOCulator
- DRAM Error Model
  - http://www.ece.cmu.edu/~safari/tools/memerr/index.html

- Other open-source software from my group
  - https://github.com/CMU-SAFARI/
  - http://www.ece.cmu.edu/~safari/tools.html

Slides Not Covered But Could Be Useful

Performance: In-DRAM Bitwise Operations

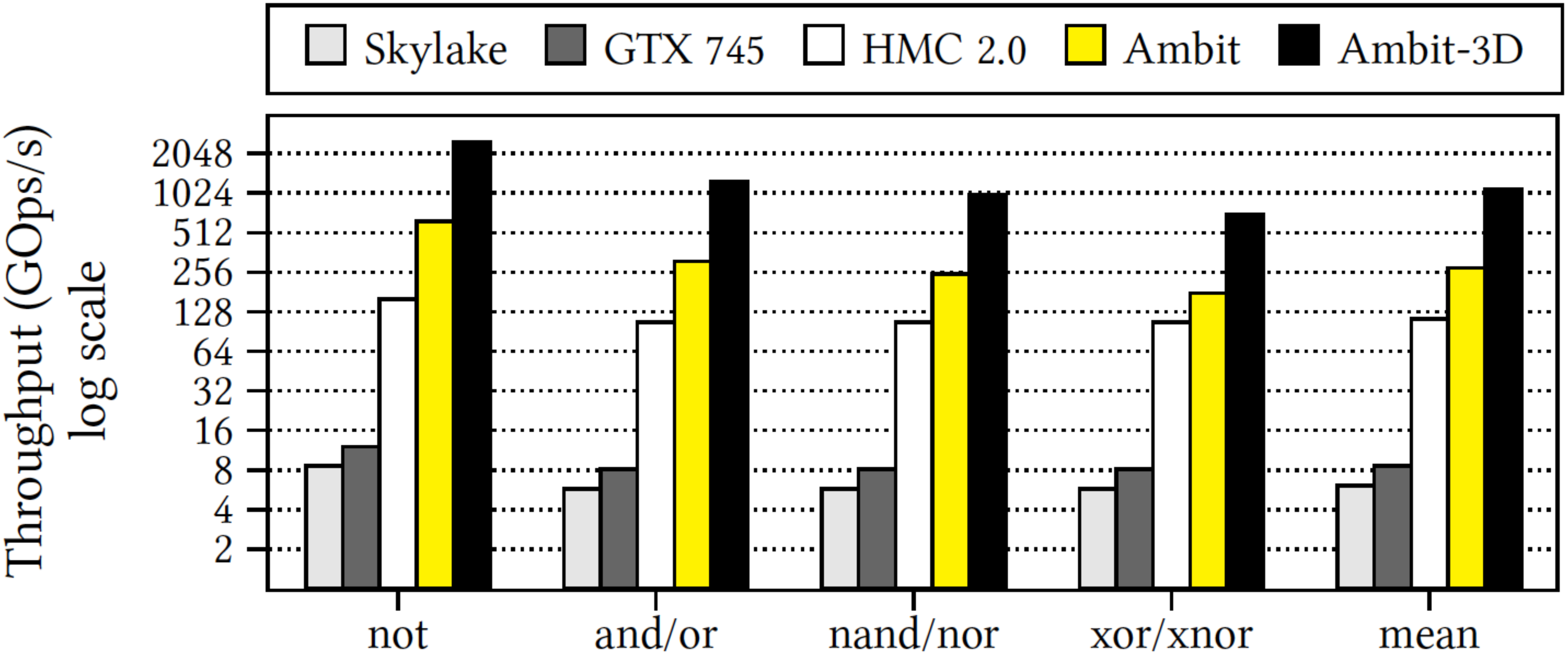
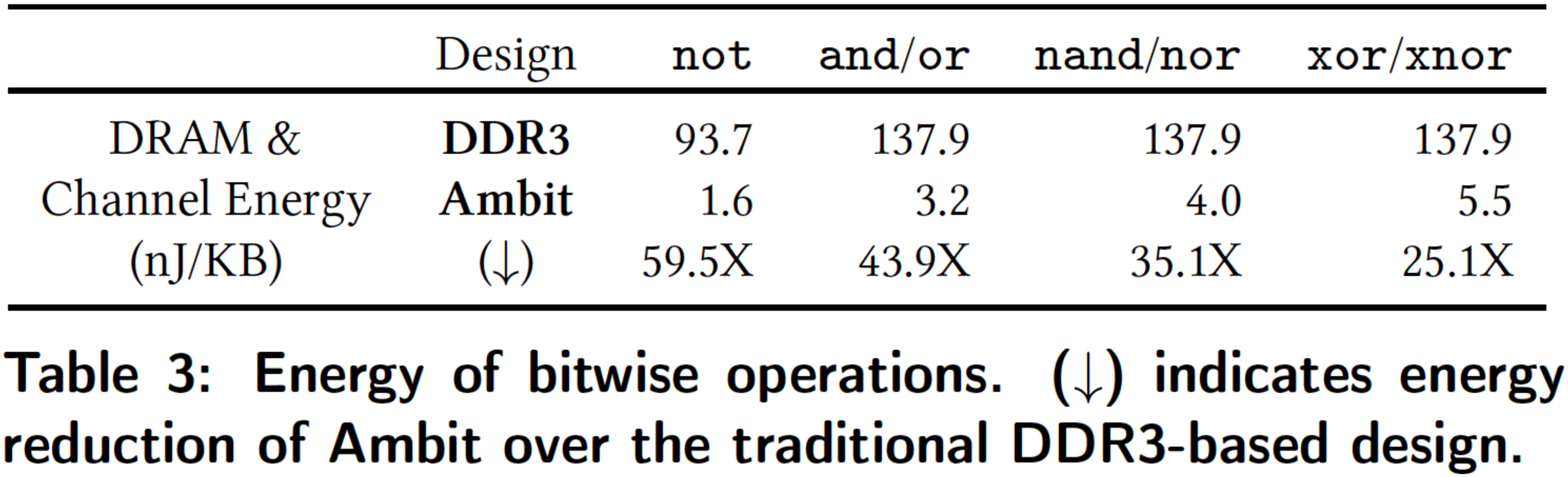


Figure 9: Throughput of bitwise operations on various systems.

Energy of In-DRAM Bitwise Operations



	Design	`not`	`and/or`	`nand/nor`	`xor/xnor`
DRAM & Channel Energy (nJ/KB)	**DDR3**	93.7	137.9	137.9	137.9
	Ambit	1.6	3.2	4.0	5.5
	(↓)	59.5X	43.9X	35.1X	25.1X

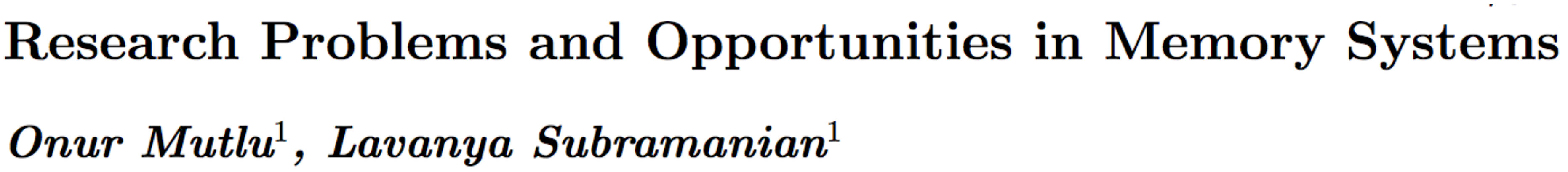
Table 3: Energy of bitwise operations. (↓) indicates energy reduction of Ambit over the traditional DDR3-based design.

Seshadri+, "Ambit: In-Memory Accelerator for Bulk Bitwise Operations using Commodity DRAM Technology," MICRO 2017.

Open Problems

For More Open Problems, See (I)

- Onur Mutlu and Lavanya Subramanian, **"Research Problems and Opportunities in Memory Systems"** *Invited Article in Supercomputing Frontiers and Innovations (**SUPERFRI**)*, 2014/2015.



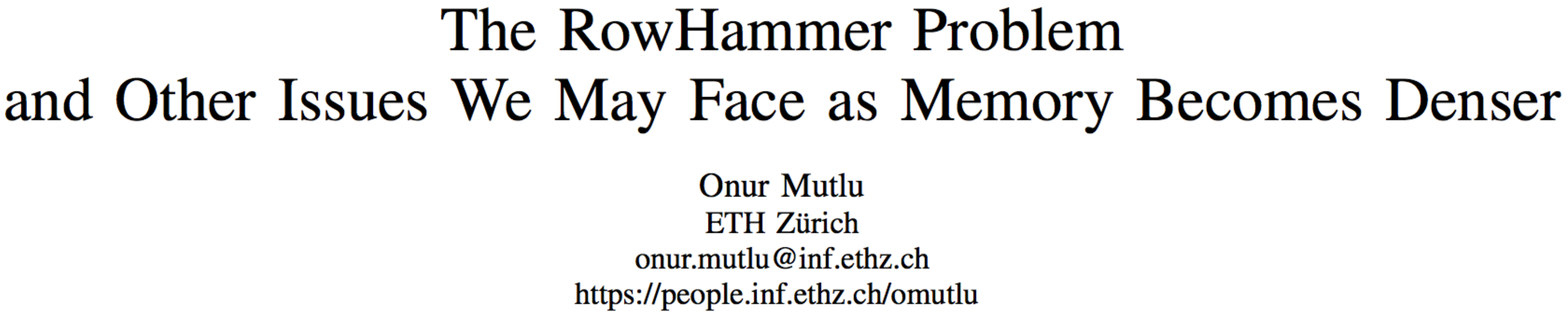
Research Problems and Opportunities in Memory Systems

Onur Mutlu[1], *Lavanya Subramanian*[1]

https://people.inf.ethz.ch/omutlu/pub/memory-systems-research_superfri14.pdf

For More Open Problems, See (II)

- Onur Mutlu,
  "The RowHammer Problem and Other Issues We May Face as Memory Becomes Denser"
  Invited Paper in Proceedings of the Design, Automation, and Test in Europe Conference (***DATE***), Lausanne, Switzerland, March 2017.
  [Slides (pptx) (pdf)]



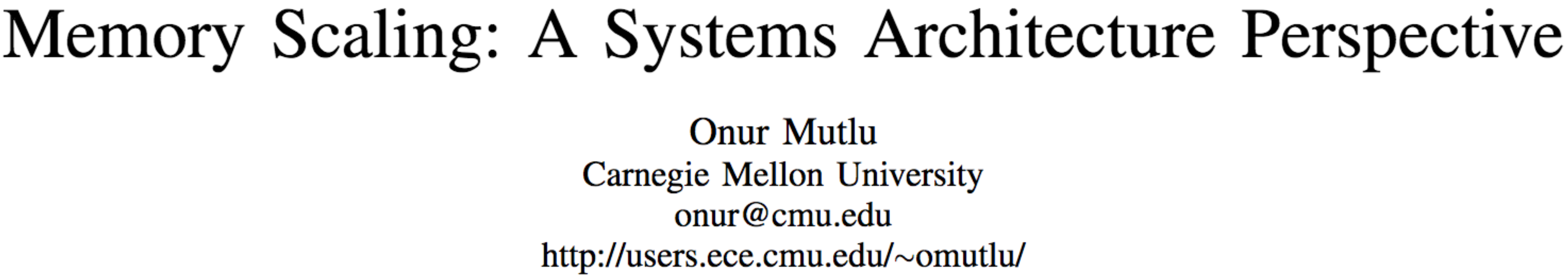
The RowHammer Problem
and Other Issues We May Face as Memory Becomes Denser

Onur Mutlu
ETH Zürich
onur.mutlu@inf.ethz.ch
https://people.inf.ethz.ch/omutlu

https://people.inf.ethz.ch/omutlu/pub/rowhammer-and-other-memory-issues_date17.pdf

For More Open Problems, See (III)

- Onur Mutlu,
  "Memory Scaling: A Systems Architecture Perspective"
  *Technical talk at MemCon 2013 (**MEMCON**)*, Santa Clara, CA, August 2013. [Slides (pptx) (pdf)]
  [Video] [Coverage on StorageSearch]



Memory Scaling: A Systems Architecture Perspective

Onur Mutlu
Carnegie Mellon University
onur@cmu.edu
http://users.ece.cmu.edu/~omutlu/

https://people.inf.ethz.ch/omutlu/pub/memory-scaling_memcon13.pdf

For More Open Problems, See (IV)

- Yu Cai, Saugata Ghose, Erich F. Haratsch, Yixin Luo, and Onur Mutlu,
  "Error Characterization, Mitigation, and Recovery in Flash Memory Based Solid State Drives"
  to appear in Proceedings of the IEEE, 2017.
  [Preliminary arxiv.org version]

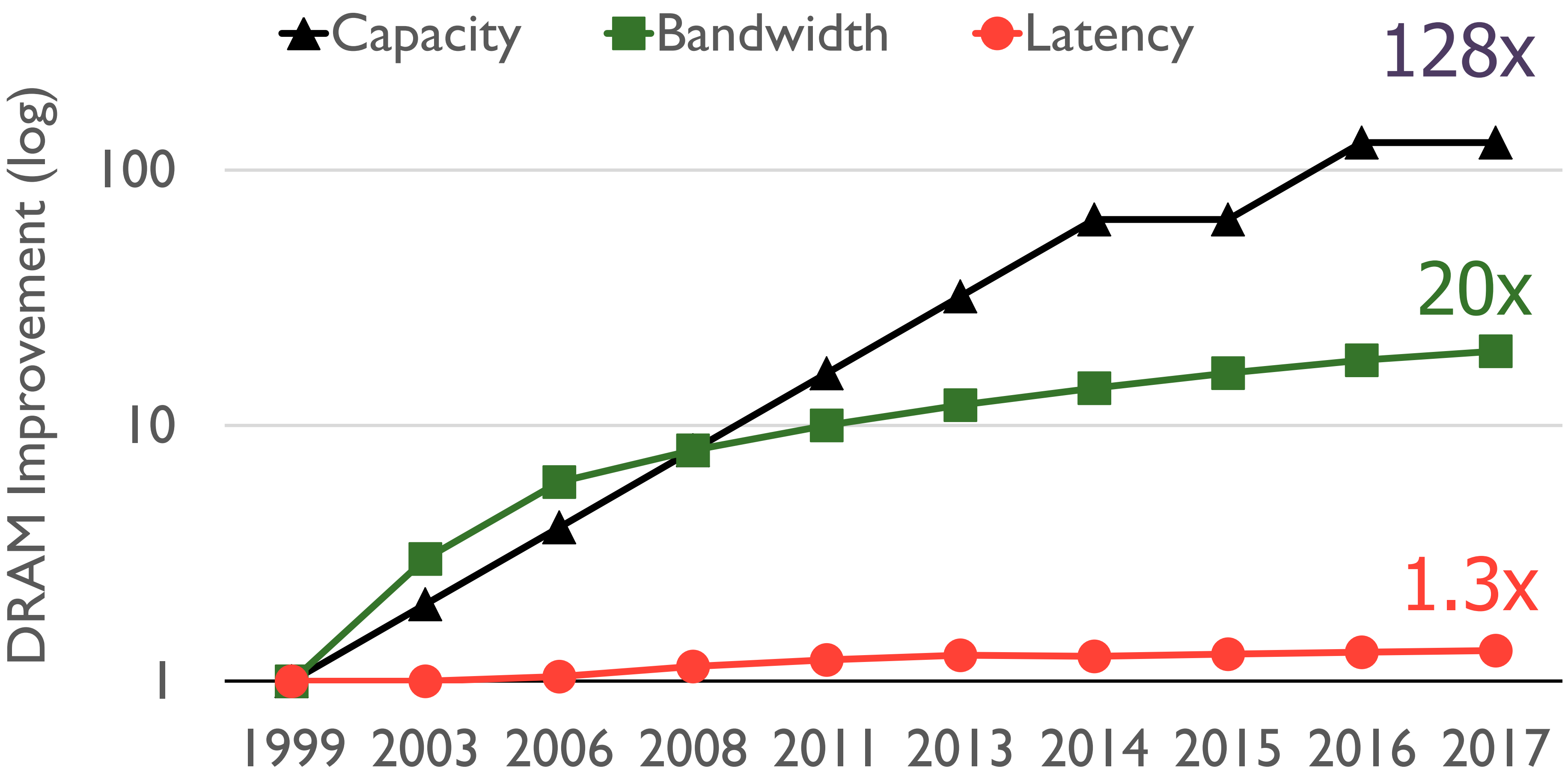
Error Characterization, Mitigation, and Recovery
in Flash Memory Based Solid State Drives

Yu Cai, Saugata Ghose, Erich F. Haratsch, Yixin Luo, and Onur Mutlu

https://arxiv.org/pdf/1706.08642.pdf

Reducing Memory Latency

Main Memory Latency Lags Behind



Memory latency remains almost constant

A Closer Look …

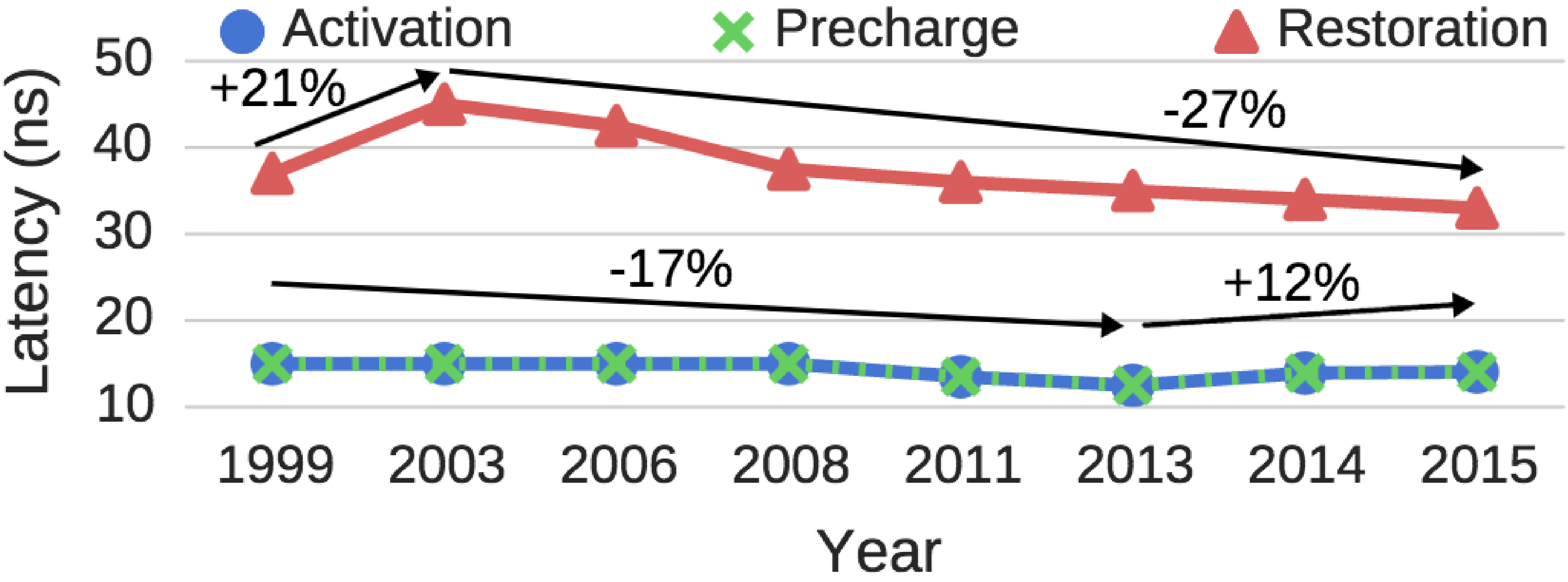
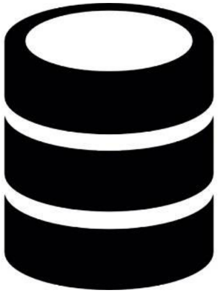


Figure 1: DRAM latency trends over time [20, 21, 23, 51].

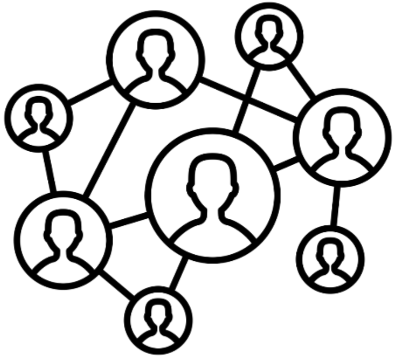
Chang+, "**Understanding Latency Variation in Modern DRAM Chips: Experimental Characterization, Analysis, and Optimization"**," SIGMETRICS 2016.

DRAM Latency Is Critical for Performance



In-memory Databases

[Mao+, EuroSys'12;
Clapp+ (**Intel**), IISWC'15]

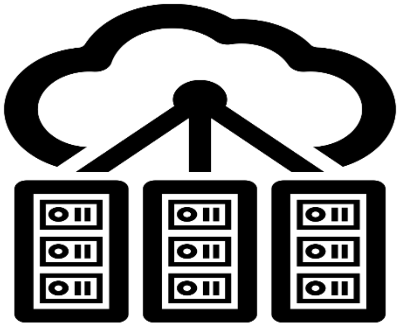


Graph/Tree Processing

[Xu+, IISWC'12; Umuroglu+, FPL'15]

In-Memory Data Analytics

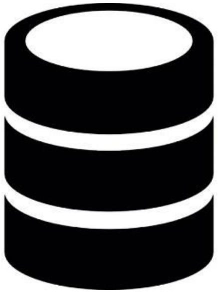
[Clapp+ (**Intel**), IISWC'15;
Awan+, BDCloud'15]



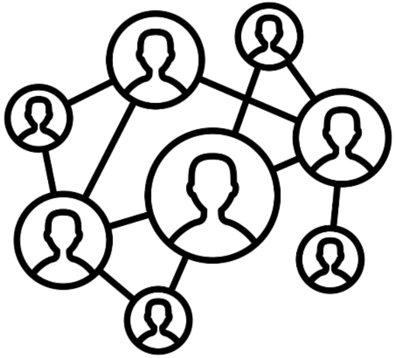
Datacenter Workloads

[Kanev+ (**Google**), ISCA'15]

DRAM Latency Is Critical for Performance



In-memory Databases

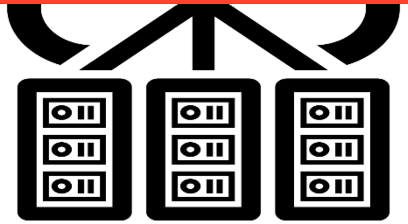


Graph/Tree Processing

Long memory latency → performance bottleneck

In-Memory Data Analytics

[Clapp+ (**Intel**), IISWC'15;
Awan+, BDCloud'15]



Datacenter Workloads

[Kanev+ (**Google**), ISCA'15]

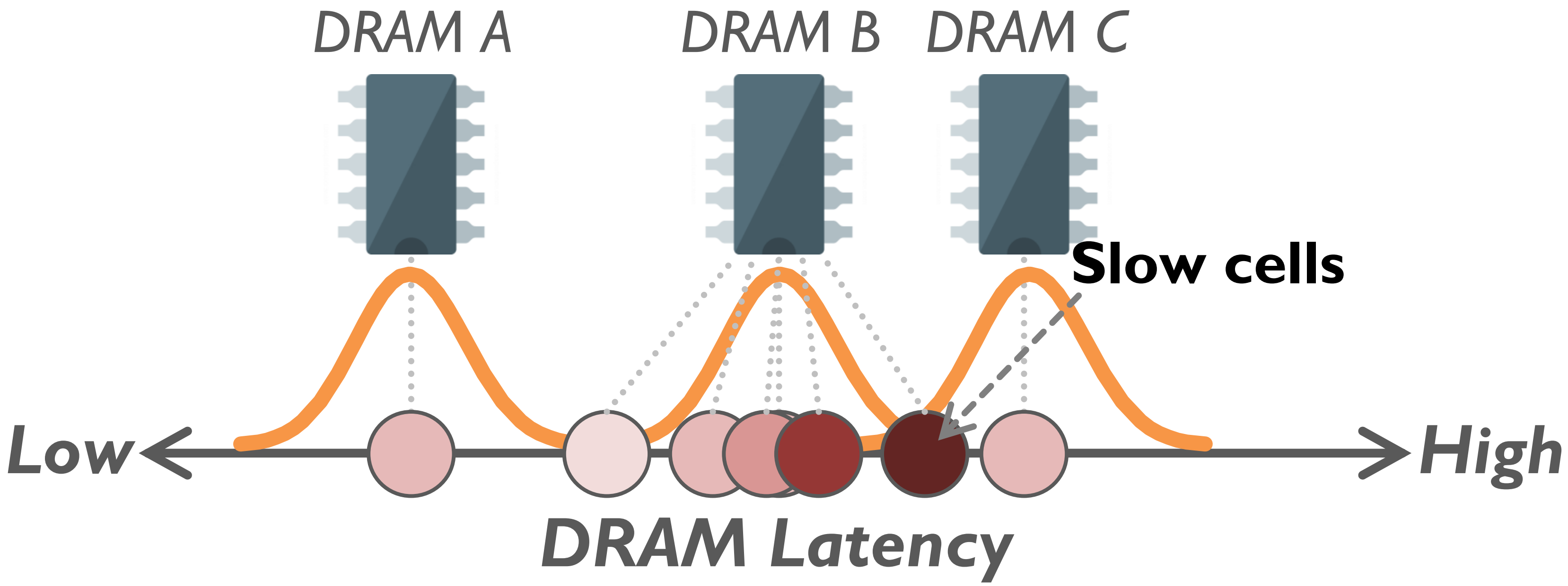
Why the Long Latency?

- Design of DRAM uArchitecture
  - Goal: Maximize capacity/area, not minimize latency

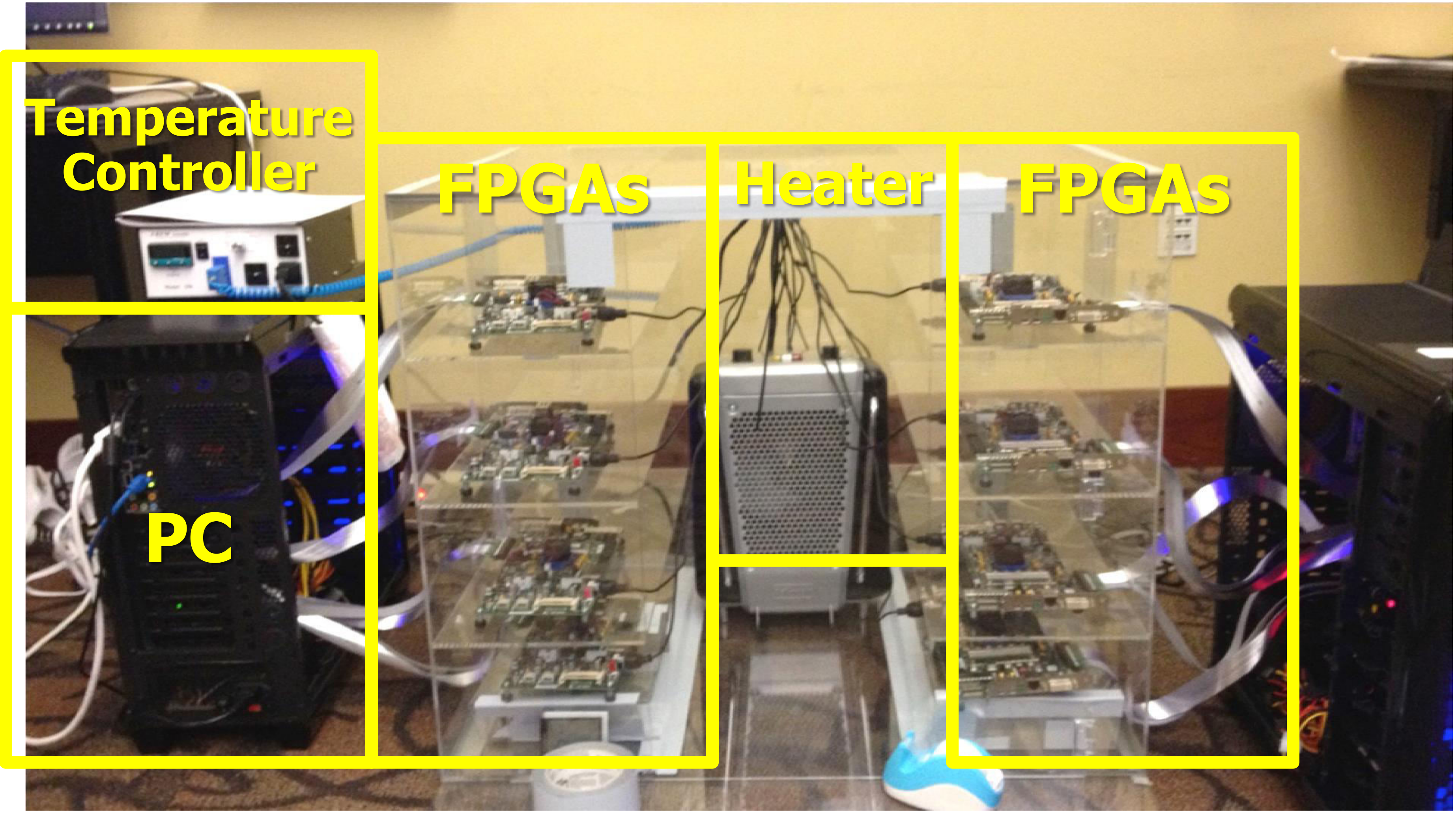
- "One size fits all" approach to latency specification
  - Same latency parameters for all temperatures
  - Same latency parameters for all DRAM chips (e.g., rows)
  - Same latency parameters for all parts of a DRAM chip
  - Same latency parameters for all supply voltage levels
  - Same latency parameters for all application data
  - …

Latency Variation in Memory Chips

Heterogeneous manufacturing & operating conditions →
latency variation in timing parameters



DRAM Characterization Infrastructure



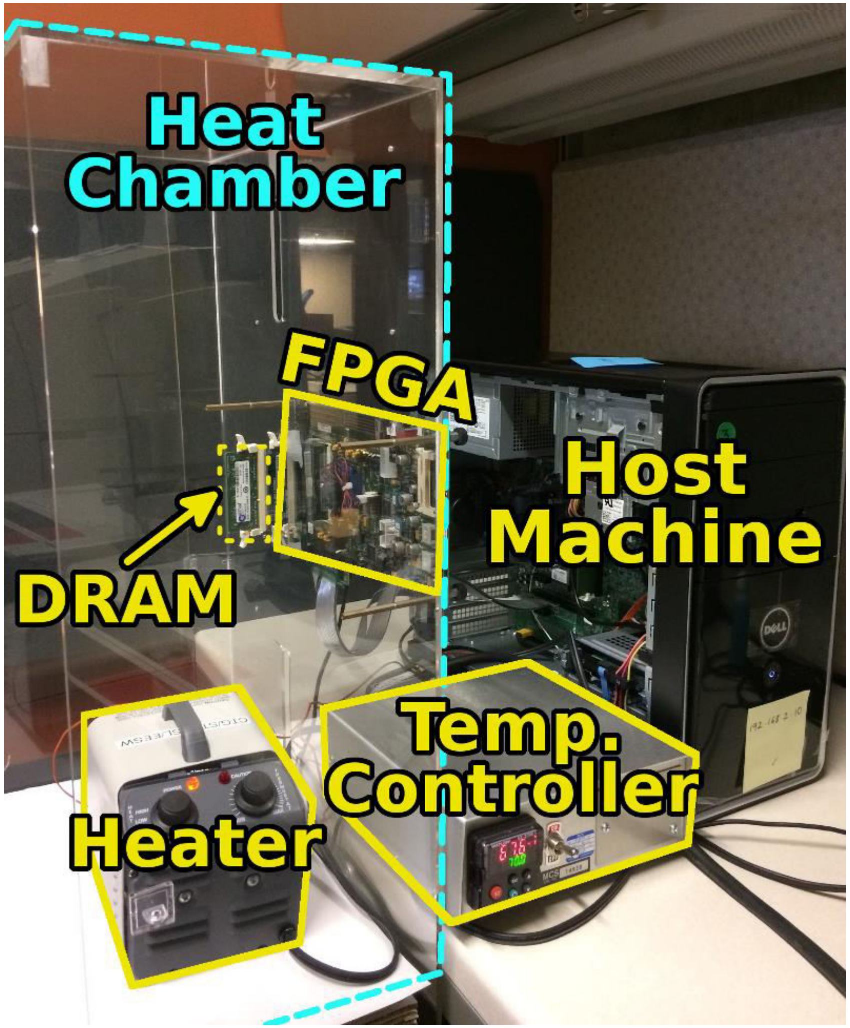
Kim+, "Flipping Bits in Memory Without Accessing Them: An Experimental Study of DRAM Disturbance Errors," ISCA 2014.

DRAM Characterization Infrastructure

- Hasan Hassan et al., **SoftMC: A Flexible and Practical Open-Source Infrastructure for Enabling Experimental DRAM Studies**, HPCA 2017.

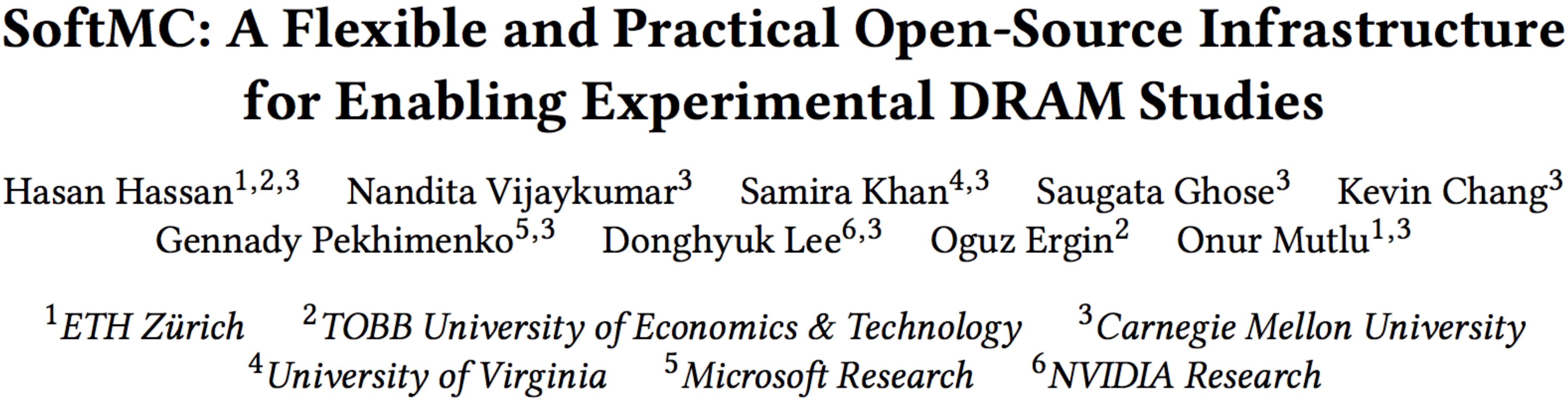
- **Flexible**
- **Easy to Use (C++ API)**
- **Open-source**

  github.com/CMU-SAFARI/SoftMC



SoftMC: Open Source DRAM Infrastructure

- https://github.com/CMU-SAFARI/SoftMC



SoftMC: A Flexible and Practical Open-Source Infrastructure for Enabling Experimental DRAM Studies

Hasan Hassan[1,2,3] Nandita Vijaykumar[3] Samira Khan[4,3] Saugata Ghose[3] Kevin Chang[3]
Gennady Pekhimenko[5,3] Donghyuk Lee[6,3] Oguz Ergin[2] Onur Mutlu[1,3]

[1]ETH Zürich [2]TOBB University of Economics & Technology [3]Carnegie Mellon University
[4]University of Virginia [5]Microsoft Research [6]NVIDIA Research

Tackling the Fixed Latency Mindset

- Reliable operation latency is actually very heterogeneous
  - Across temperatures, chips, parts of a chip, voltage levels, …

- Idea: Dynamically find out and use the lowest latency one can reliably access a memory location with
  - Adaptive-Latency DRAM [HPCA 2015]
  - Flexible-Latency DRAM [SIGMETRICS 2016]
  - Design-Induced Variation-Aware DRAM [SIGMETRICS 2017]
  - Voltron [SIGMETRICS 2017]
  - ...

- We would like to find sources of latency heterogeneity and exploit them to minimize latency

Adaptive-Latency DRAM

- *Key idea*
  - **Optimize DRAM timing parameters online**

- *Two components*
  - DRAM manufacturer provides multiple sets of reliable DRAM timing parameters at different temperatures for each DIMM
  - System monitors DRAM temperature & uses appropriate DRAM timing parameters

Lee+, "Adaptive-Latency DRAM: Optimizing DRAM Timing for the Common-Case," HPCA 2015.

Latency Reduction Summary of 115 DIMMs

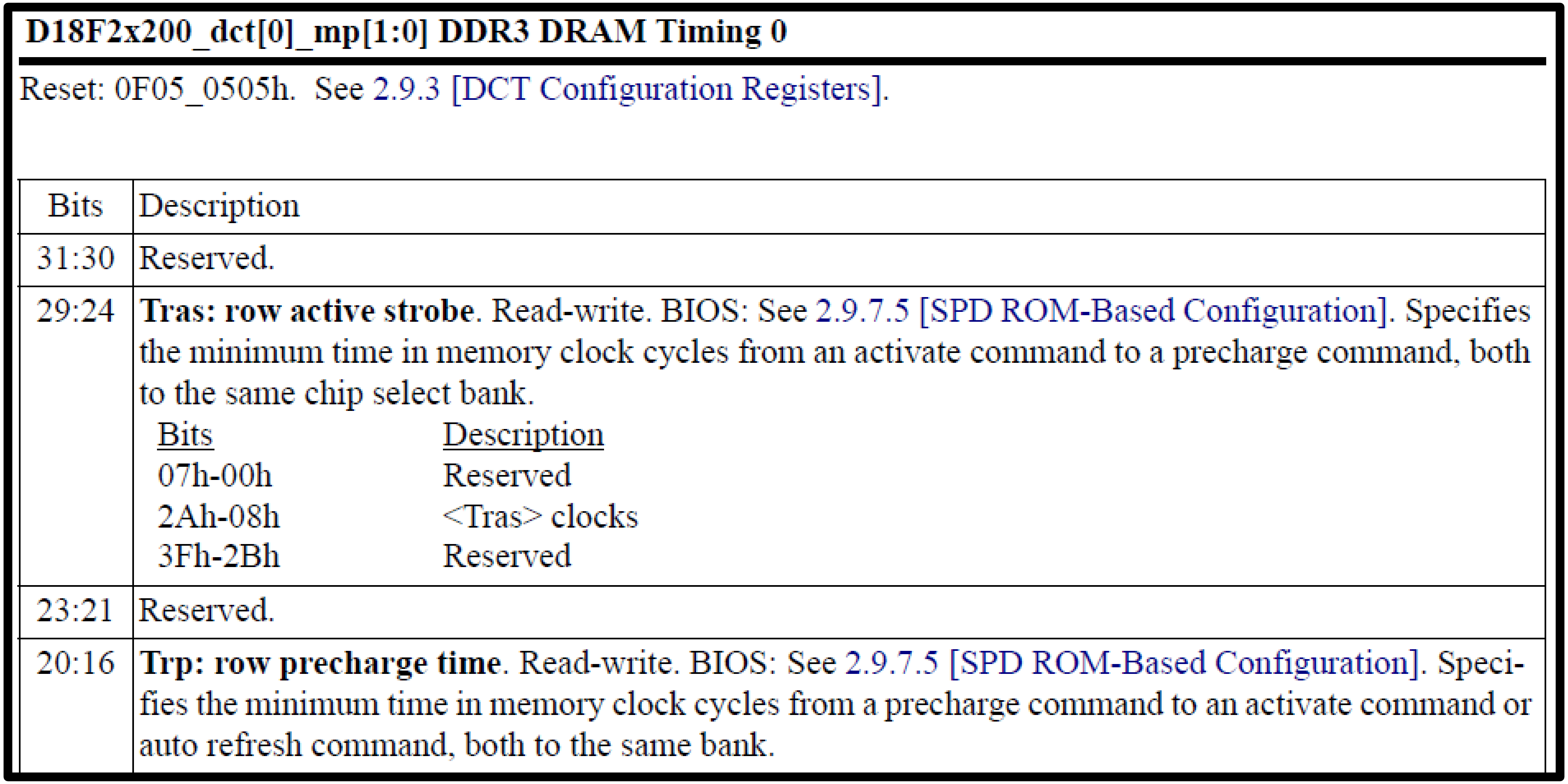
- *Latency reduction for read & write (55°C)*
  - *Read Latency:* ***32.7%***
  - *Write Latency:* ***55.1%***

- *Latency reduction for each timing parameter (55°C)*
  - *Sensing:* ***17.3%***
  - *Restore:* ***37.3%*** *(read),* ***54.8%*** *(write)*
  - *Precharge:* ***35.2%***

Lee+, "Adaptive-Latency DRAM: Optimizing DRAM Timing for the Common-Case," HPCA 2015.

AL-DRAM: Real System Evaluation

- *System*
  - *– CPU: AMD 4386 (8 Cores, 3.1GHz, 8MB LLC)*

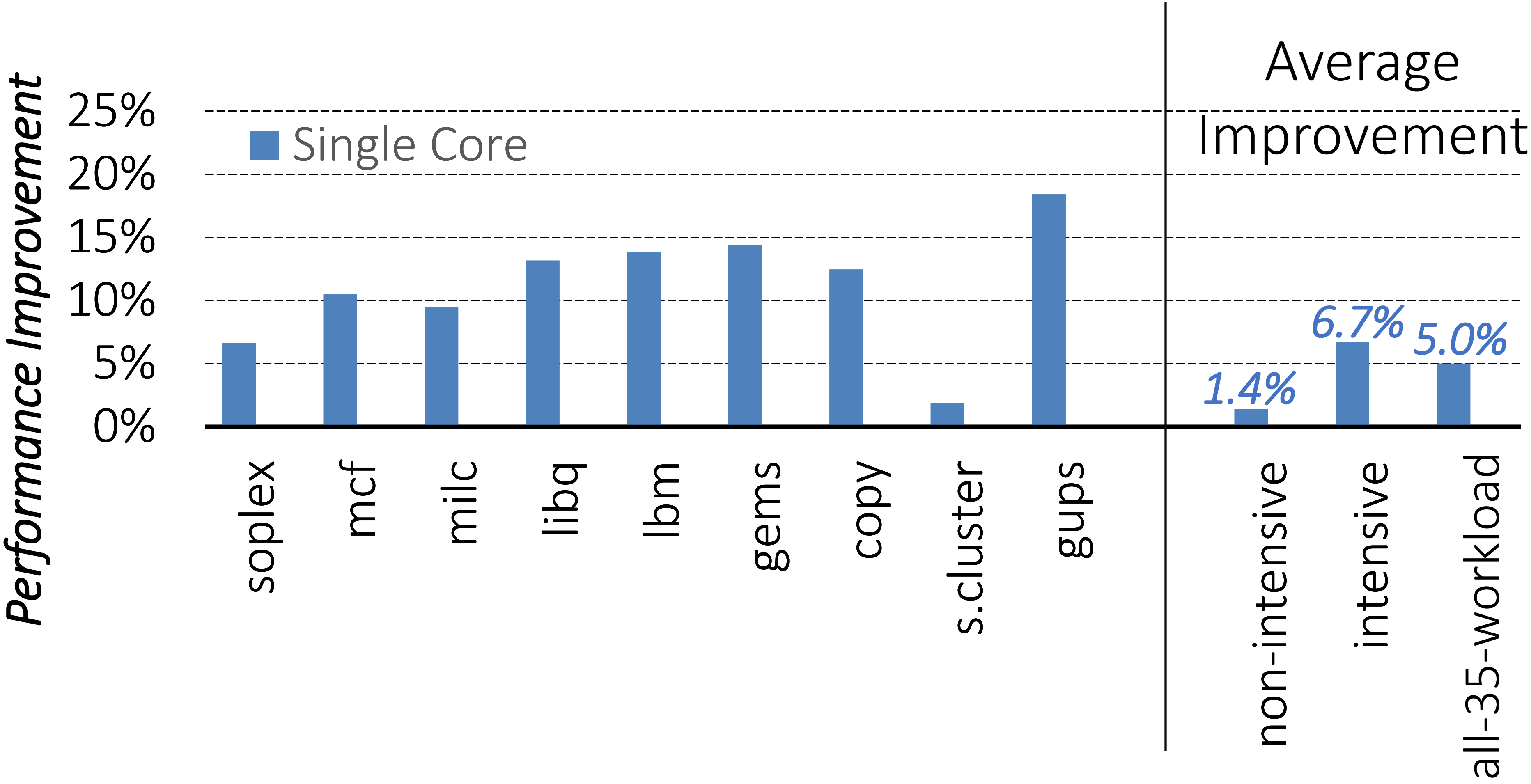


D18F2x200_dct[0]_mp[1:0] DDR3 DRAM Timing 0

Reset: 0F05_0505h. See 2.9.3 [DCT Configuration Registers].

Bits	Description
31:30	Reserved.
29:24	**Tras: row active strobe**. Read-write. BIOS: See 2.9.7.5 [SPD ROM-Based Configuration]. Specifies the minimum time in memory clock cycles from an activate command to a precharge command, both to the same chip select bank. Bits Description 07h-00h Reserved 2Ah-08h <Tras> clocks 3Fh-2Bh Reserved
23:21	Reserved.
20:16	**Trp: row precharge time**. Read-write. BIOS: See 2.9.7.5 [SPD ROM-Based Configuration]. Specifies the minimum time in memory clock cycles from a precharge command to an activate command or auto refresh command, both to the same bank.

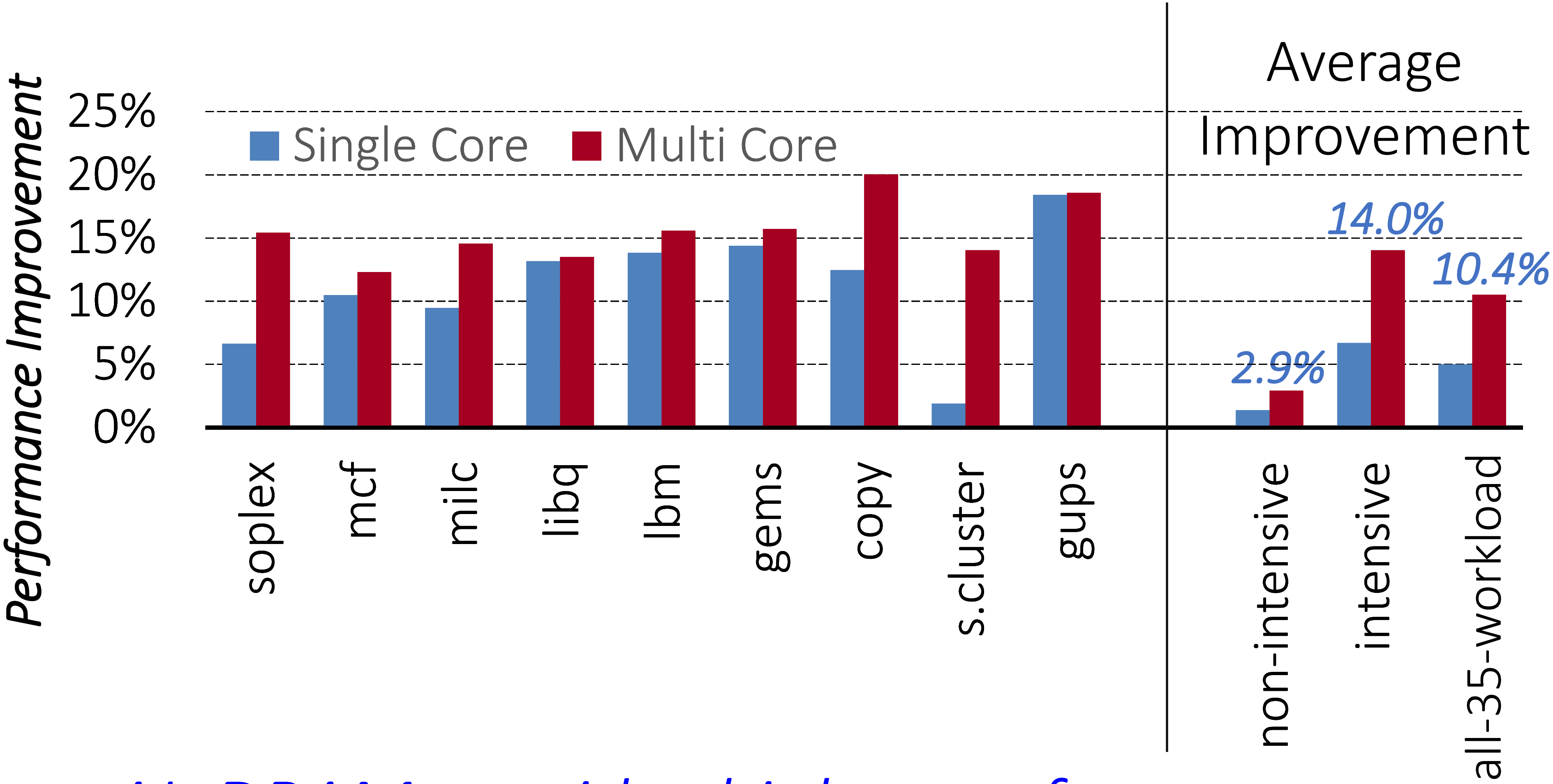
AL-DRAM: Single-Core Evaluation



*AL-DRAM **improves single-core performance***

on a real system

AL-DRAM: Multi-Core Evaluation



AL-DRAM provides higher performance on ***multi-programmed & multi-threaded workloads***

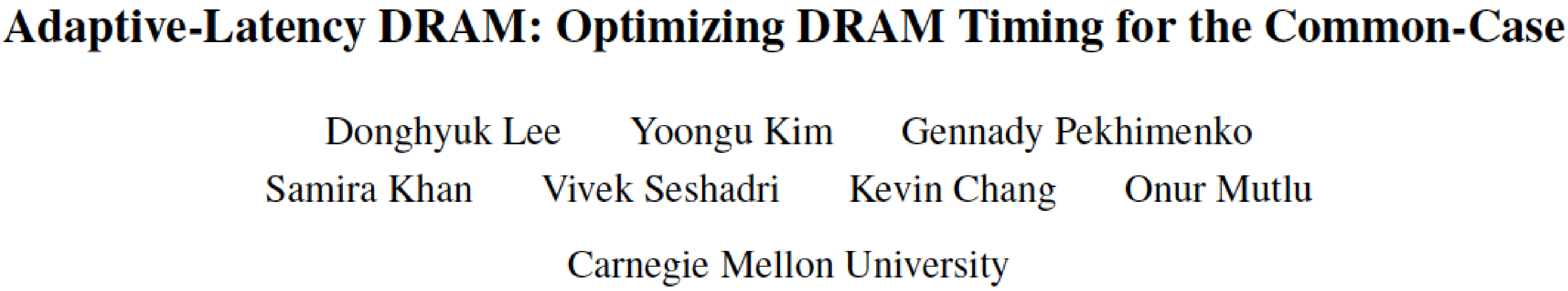
Reducing Latency Also Reduces Energy

- AL-DRAM reduces DRAM power consumption by 5.8%

- Major reason: reduction in row activation time

More on Adaptive-Latency DRAM

- Donghyuk Lee, Yoongu Kim, Gennady Pekhimenko, Samira Khan, Vivek Seshadri, Kevin Chang, and Onur Mutlu, **"Adaptive-Latency DRAM: Optimizing DRAM Timing for the Common-Case"** *Proceedings of the 21st International Symposium on High-Performance Computer Architecture* (***HPCA***), Bay Area, CA, February 2015.
  [Slides (pptx) (pdf)] [Full data sets]

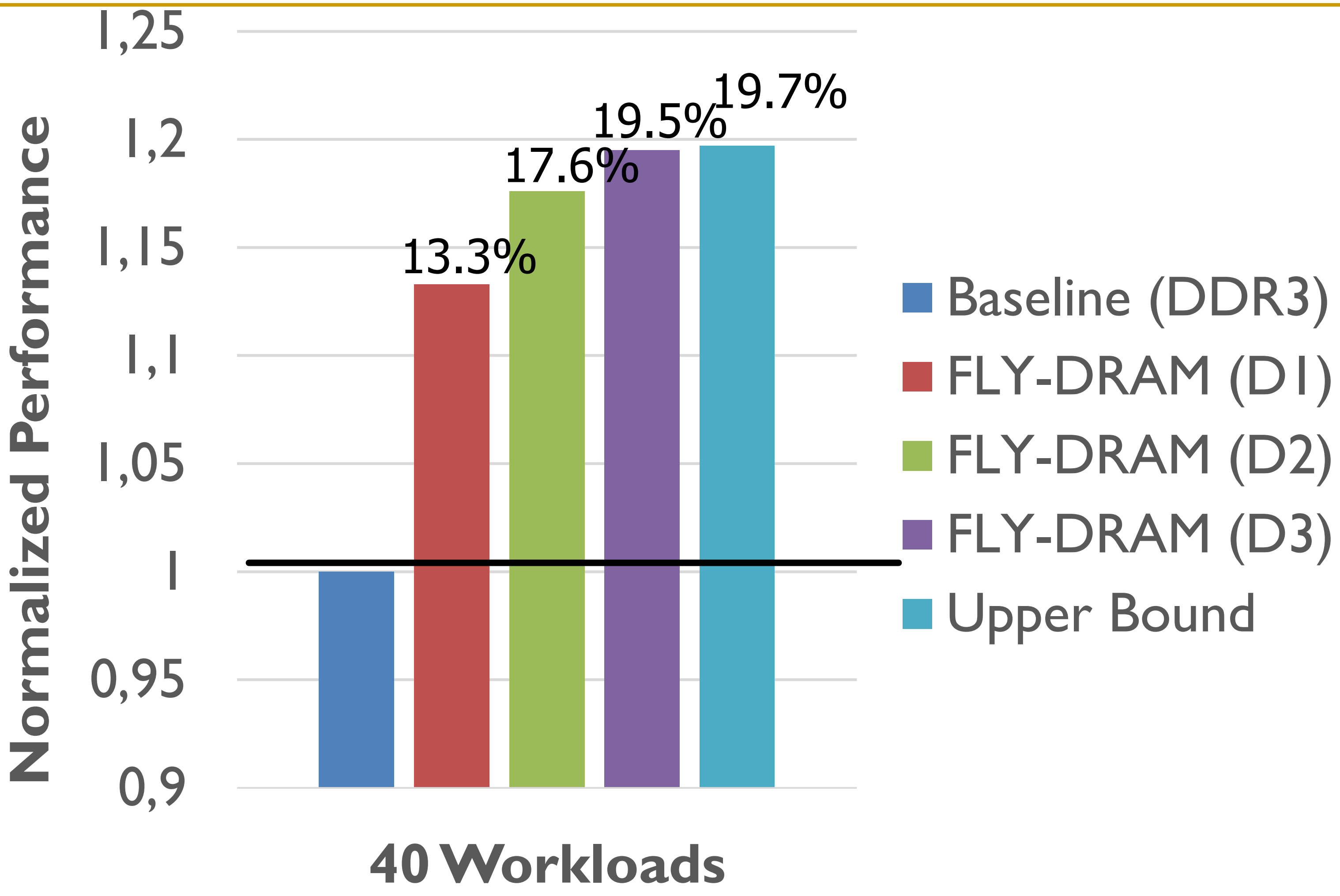


Adaptive-Latency DRAM: Optimizing DRAM Timing for the Common-Case

Donghyuk Lee Yoongu Kim Gennady Pekhimenko
Samira Khan Vivek Seshadri Kevin Chang Onur Mutlu

Carnegie Mellon University

Heterogeneous Latency within A Chip



Chang+, "**Understanding Latency Variation in Modern DRAM Chips: Experimental Characterization, Analysis, and Optimization"**," SIGMETRICS 2016.

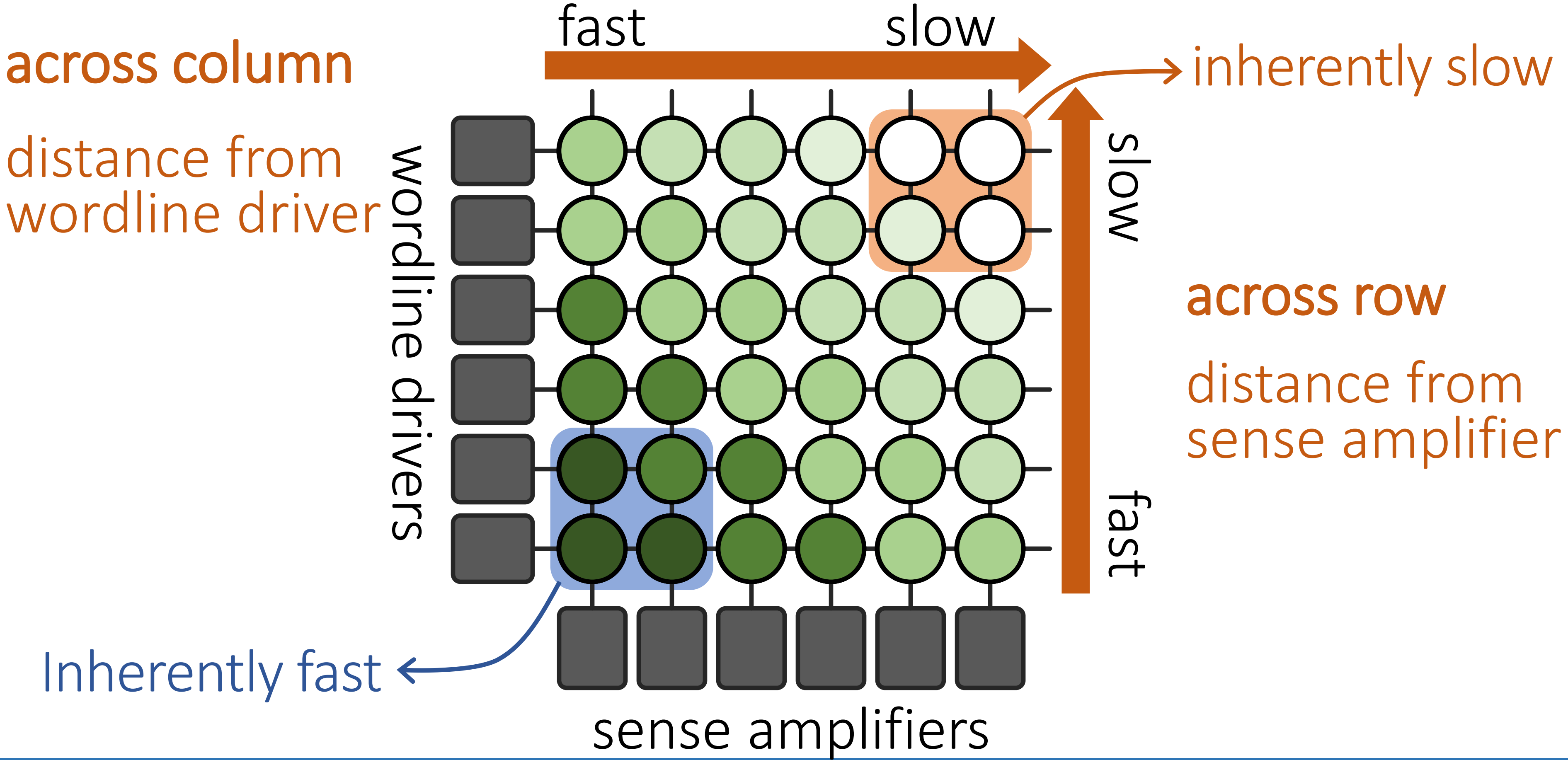
Analysis of Latency Variation in DRAM Chips

- Kevin Chang, Abhijith Kashyap, Hasan Hassan, Samira Khan, Kevin Hsieh, Donghyuk Lee, Saugata Ghose, Gennady Pekhimenko, Tianshi Li, and Onur Mutlu,
  "Understanding Latency Variation in Modern DRAM Chips: Experimental Characterization, Analysis, and Optimization"
  Proceedings of the ACM International Conference on Measurement and Modeling of Computer Systems (***SIGMETRICS***), Antibes Juan-Les-Pins, France, June 2016.
  [Slides (pptx) (pdf)]
  [Source Code]

Understanding Latency Variation in Modern DRAM Chips: Experimental Characterization, Analysis, and Optimization

Kevin K. Chang[1] Abhijith Kashyap[1] Hasan Hassan[1,2]
Saugata Ghose[1] Kevin Hsieh[1] Donghyuk Lee[1] Tianshi Li[1,3]
Gennady Pekhimenko[1] Samira Khan[4] Onur Mutlu[5,1]
[1]Carnegie Mellon University [2]TOBB ETÜ [3]Peking University [4]University of Virginia [5]ETH Zürich

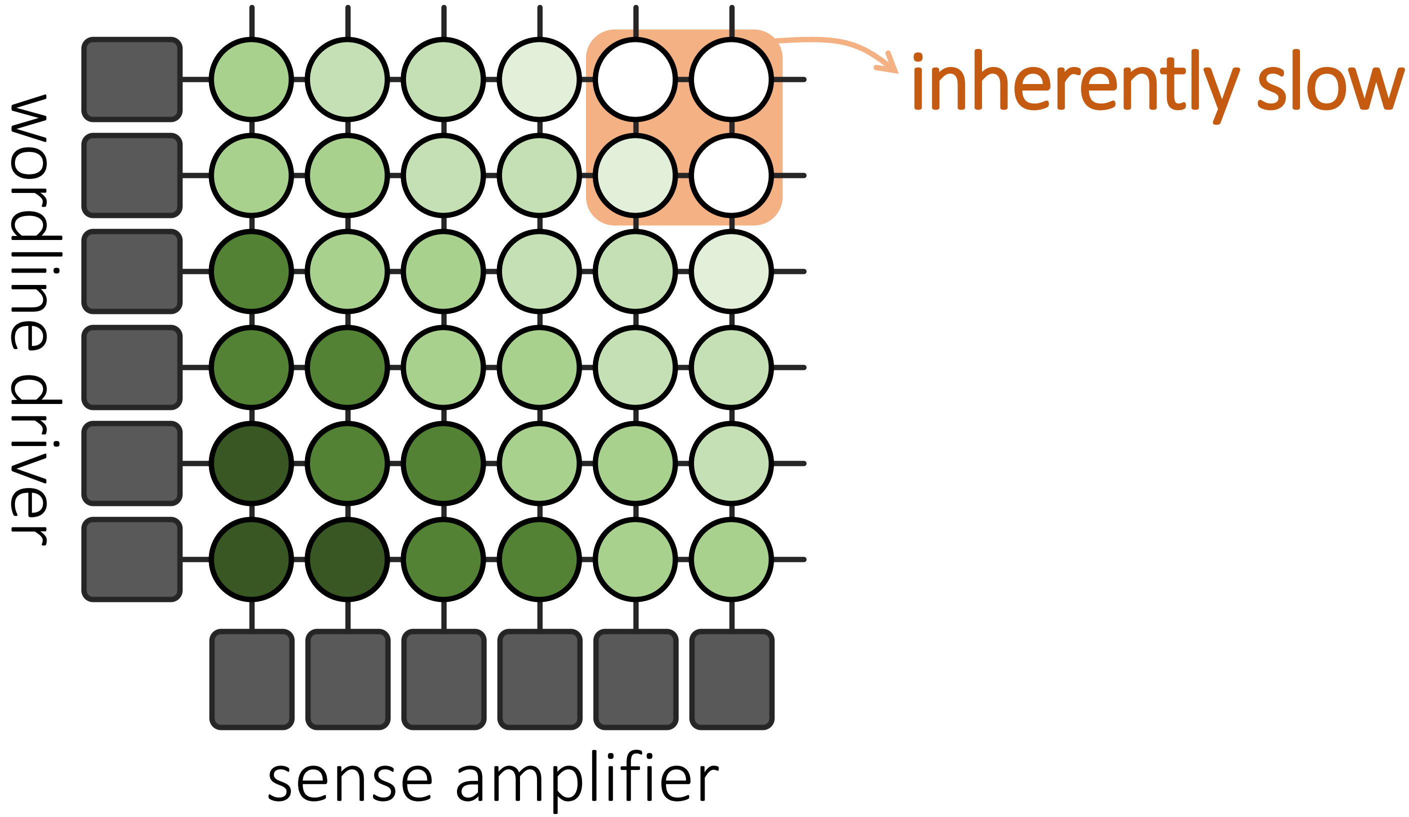
What Is Design-Induced Variation?



Systematic variation in cell access times caused by the ***physical organization*** of DRAM

DIVA Online **Profiling**

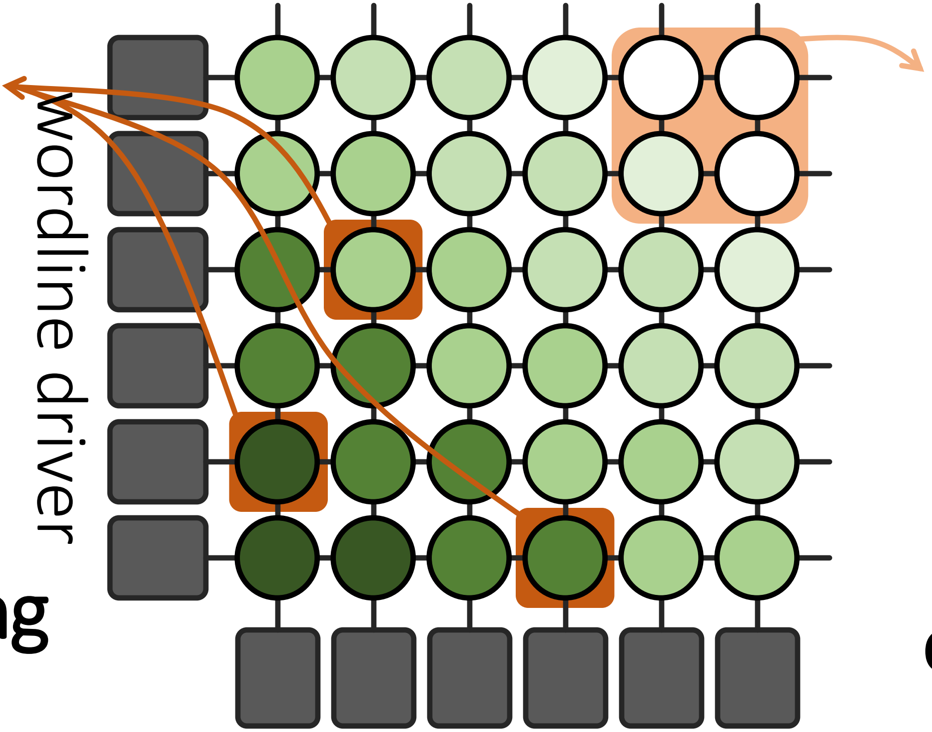
Design-**I**nduced-**V**ariation-**A**ware



Profile *only slow regions* to determine min. latency
→ *Dynamic* & *low cost* latency optimization

DIVA Online **Profiling**

Design-**I**nduced-**V**ariation-**A**ware



slow cells

process variation

random error

error-correcting code

inherently slow

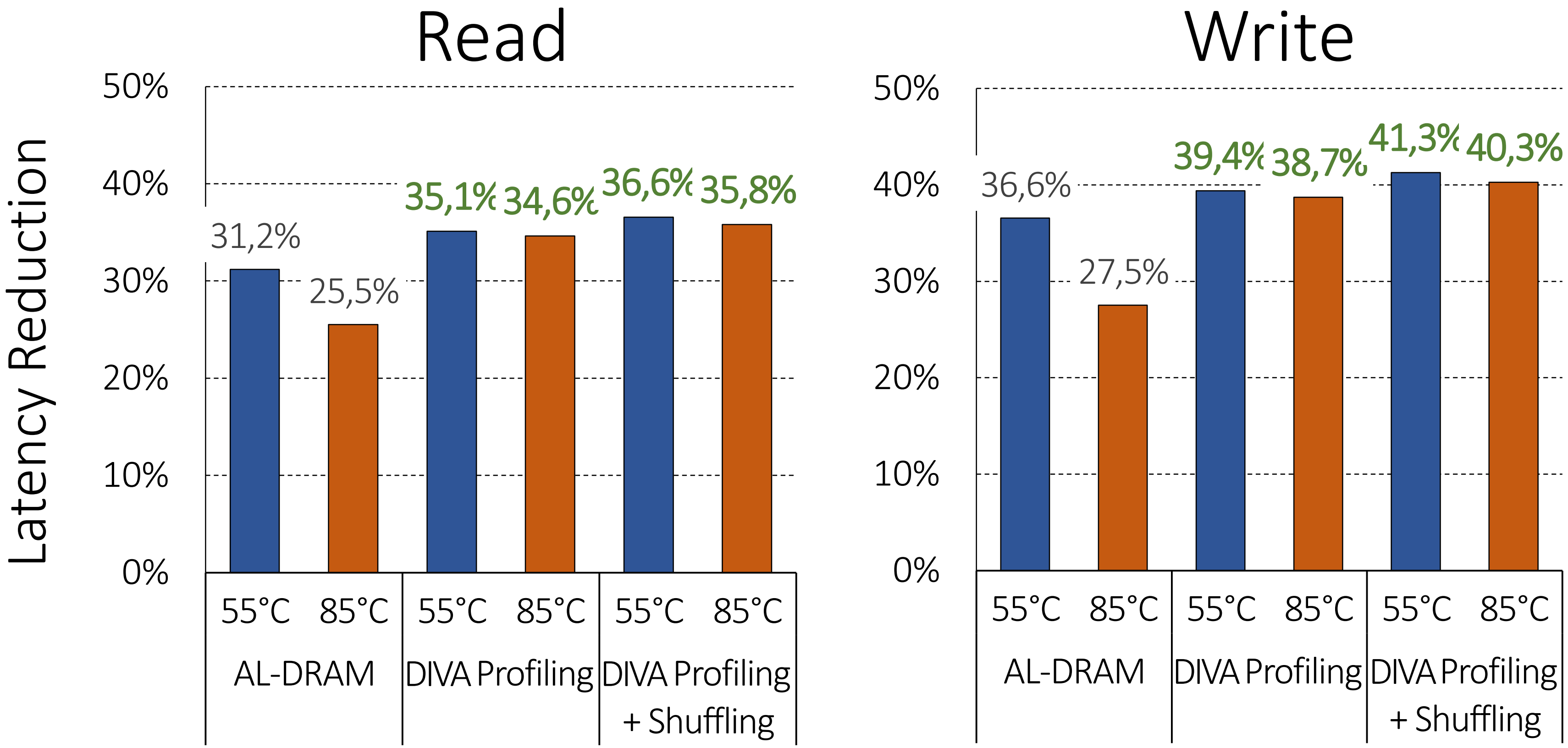
design-induced variation

localized error

online profiling

Combine error-correcting codes & online profiling
→ Reliably reduce DRAM latency

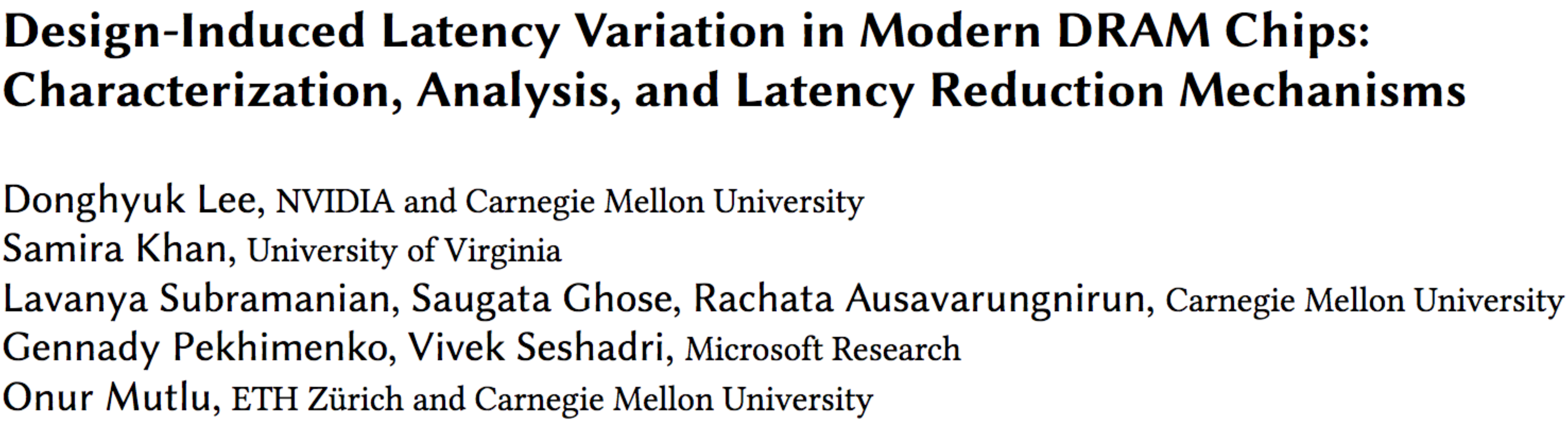
DIVA-DRAM Reduces Latency



DIVA-DRAM ***reduces latency more aggressively*** and uses ECC to correct random slow cells

Design-Induced Latency Variation in DRAM

- Donghyuk Lee, Samira Khan, Lavanya Subramanian, Saugata Ghose, Rachata Ausavarungnirun, Gennady Pekhimenko, Vivek Seshadri, and Onur Mutlu,
"Design-Induced Latency Variation in Modern DRAM Chips: Characterization, Analysis, and Latency Reduction Mechanisms"
Proceedings of the ACM International Conference on Measurement and Modeling of Computer Systems (***SIGMETRICS***), Urbana-Champaign, IL, USA, June 2017.



Design-Induced Latency Variation in Modern DRAM Chips: Characterization, Analysis, and Latency Reduction Mechanisms

Donghyuk Lee, NVIDIA and Carnegie Mellon University
Samira Khan, University of Virginia
Lavanya Subramanian, Saugata Ghose, Rachata Ausavarungnirun, Carnegie Mellon University
Gennady Pekhimenko, Vivek Seshadri, Microsoft Research
Onur Mutlu, ETH Zürich and Carnegie Mellon University

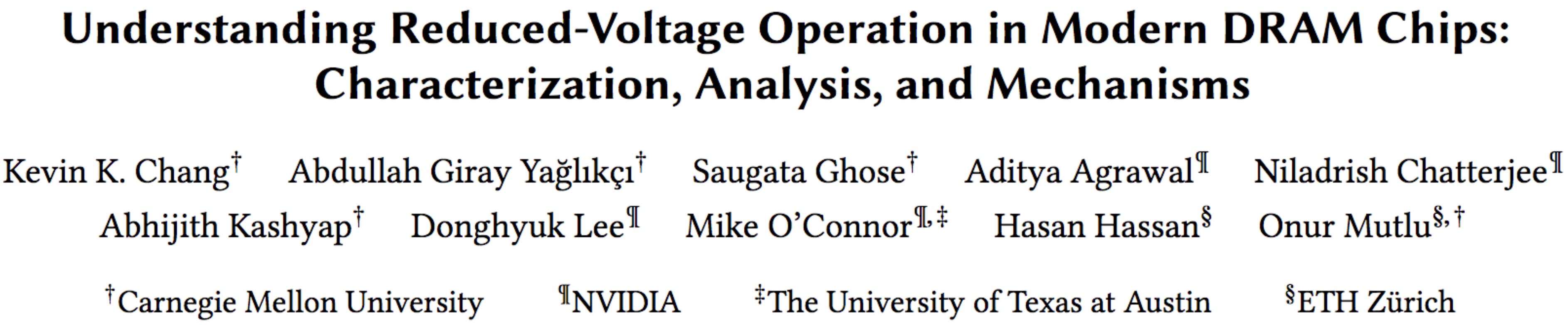
Voltron: Exploiting the Voltage-Latency-Reliability Relationship

Executive Summary

- DRAM (memory) power is significant in today's systems
  - Existing low-voltage DRAM reduces voltage **conservatively**
- Goal: Understand and exploit the reliability and latency behavior of real DRAM chips under ***aggressive reduced-voltage operation***
- Key experimental observations:
  - Huge voltage margin -- Errors occur beyond some voltage
  - Errors exhibit spatial locality
  - Higher operation latency mitigates voltage-induced errors
- **Voltron**: A new DRAM energy reduction mechanism
  - Reduce DRAM voltage **without introducing errors**
  - Use a **regression model** to select voltage that does not degrade performance beyond a chosen target → 7.3% system energy reduction

Analysis of Latency-Voltage in DRAM Chips

- Kevin Chang, A. Giray Yaglikci, Saugata Ghose, Aditya Agrawal, Niladrish Chatterjee, Abhijith Kashyap, Donghyuk Lee, Mike O'Connor, Hasan Hassan, and Onur Mutlu,
"Understanding Reduced-Voltage Operation in Modern DRAM Devices: Experimental Characterization, Analysis, and Mechanisms"
Proceedings of the ACM International Conference on Measurement and Modeling of Computer Systems (***SIGMETRICS***), Urbana-Champaign, IL, USA, June 2017.



Understanding Reduced-Voltage Operation in Modern DRAM Chips: Characterization, Analysis, and Mechanisms

Kevin K. Chang[†] Abdullah Giray Yağlıkçı[†] Saugata Ghose[†] Aditya Agrawal[¶] Niladrish Chatterjee[¶]
Abhijith Kashyap[†] Donghyuk Lee[¶] Mike O'Connor[¶,‡] Hasan Hassan[§] Onur Mutlu[§,†]

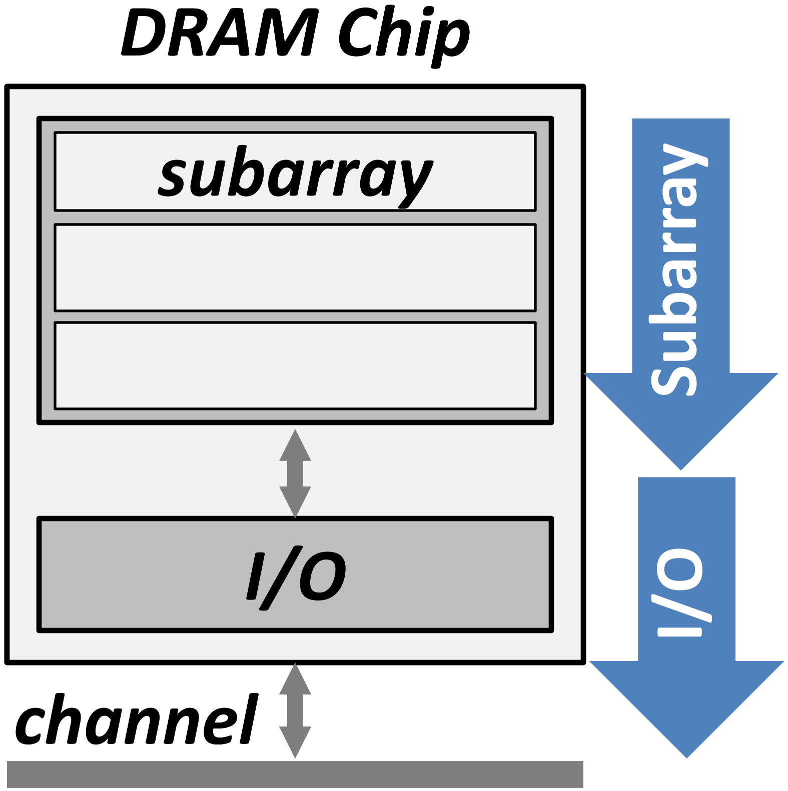
[†]Carnegie Mellon University [¶]NVIDIA [‡]The University of Texas at Austin [§]ETH Zürich

And, What If …

- … we can sacrifice reliability of some data to access it with even lower latency?

Tiered Latency DRAM

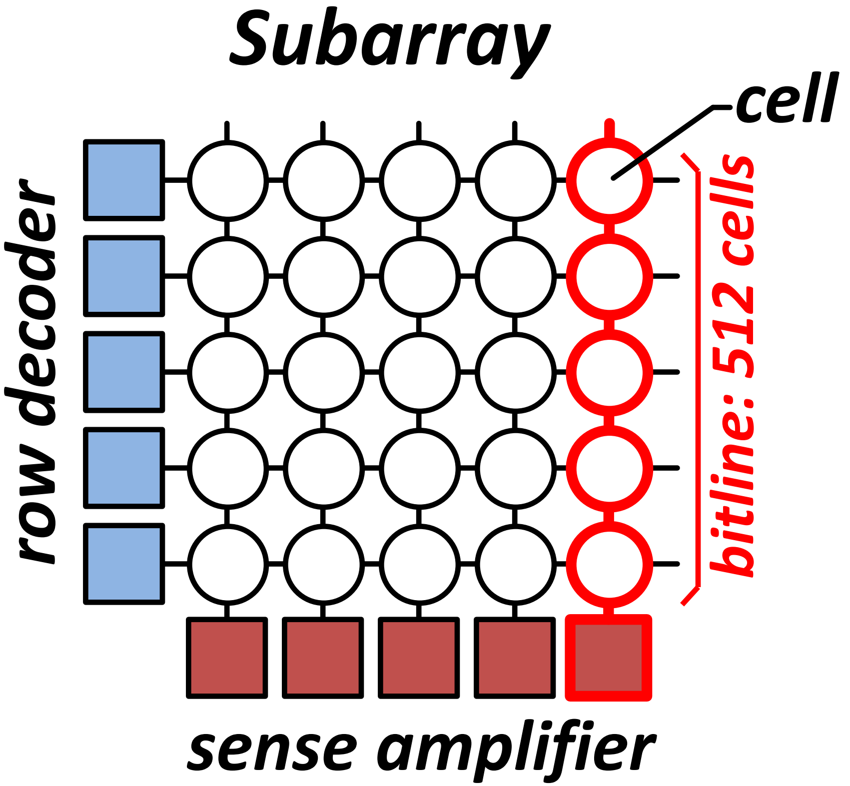
What Causes the Long Latency?

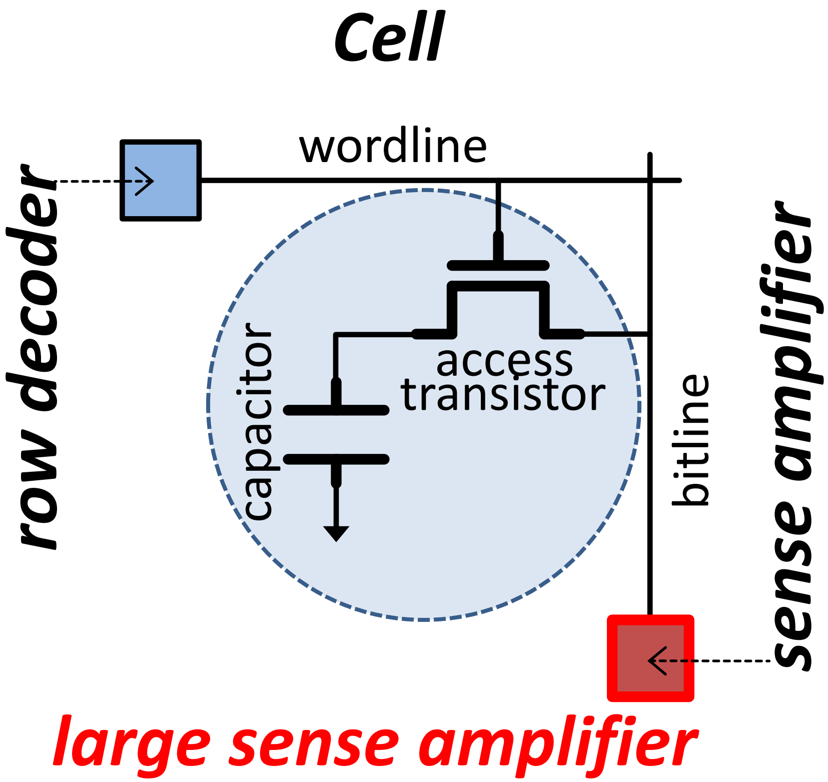


DRAM Latency = Subarray Latency + I/O Latency

Dominant

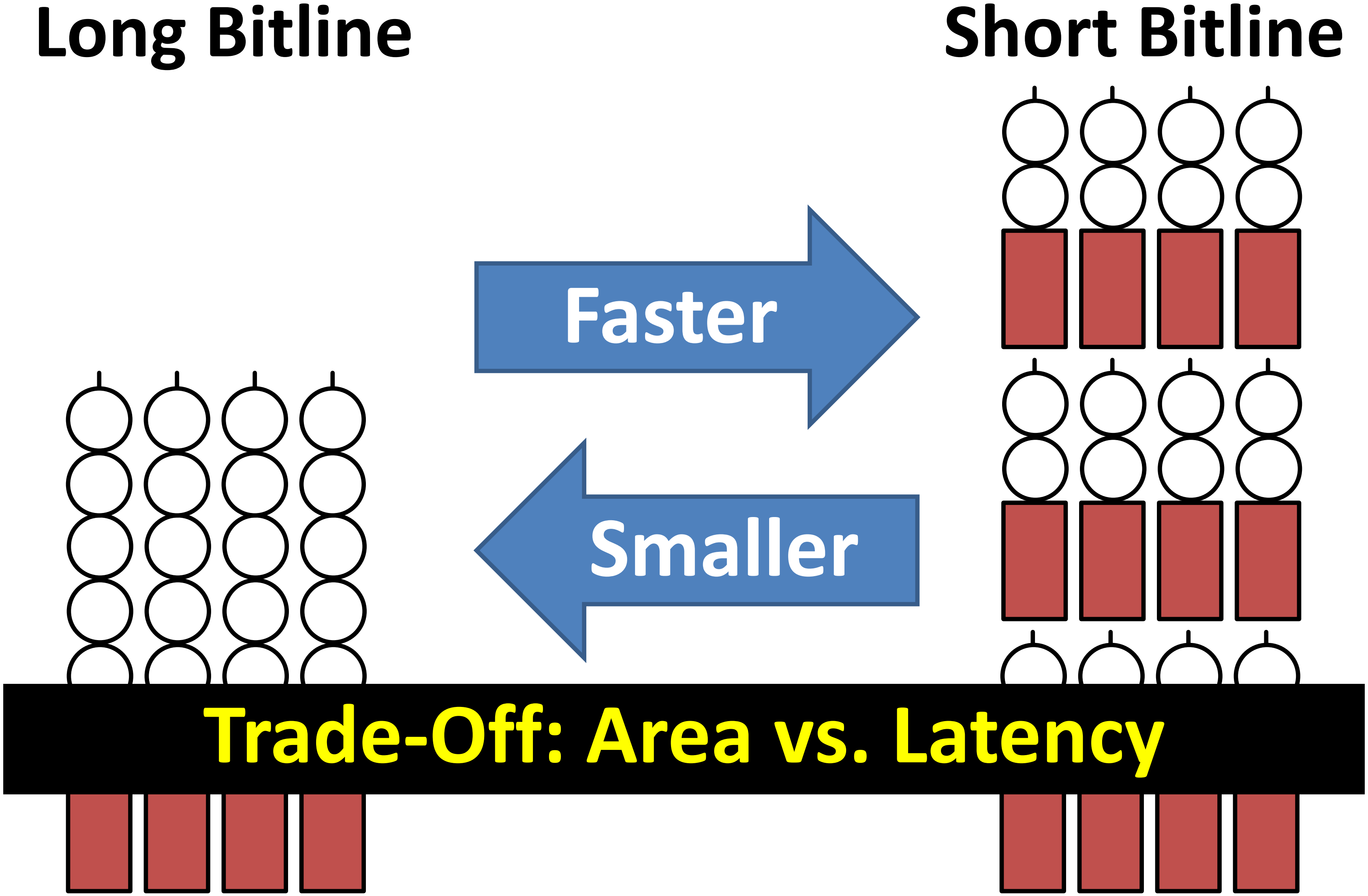
Why is the Subarray So Slow?





- **Long bitline**
  - – Amortizes sense amplifier cost → Small area
  - – Large bitline capacitance → High latency & power

Trade-Off: Area (Die Size) vs. Latency



Long Bitline

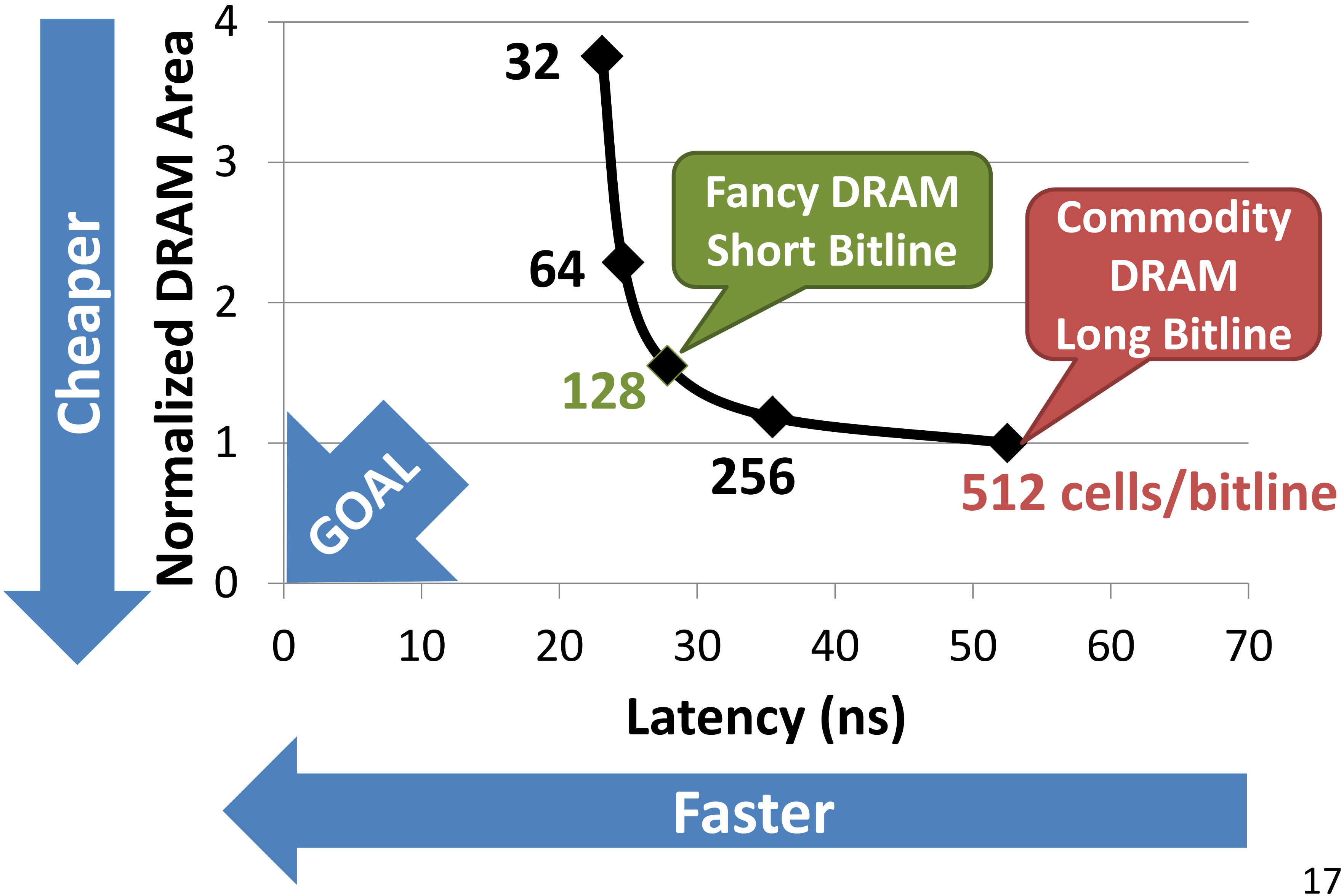
Short Bitline

Faster

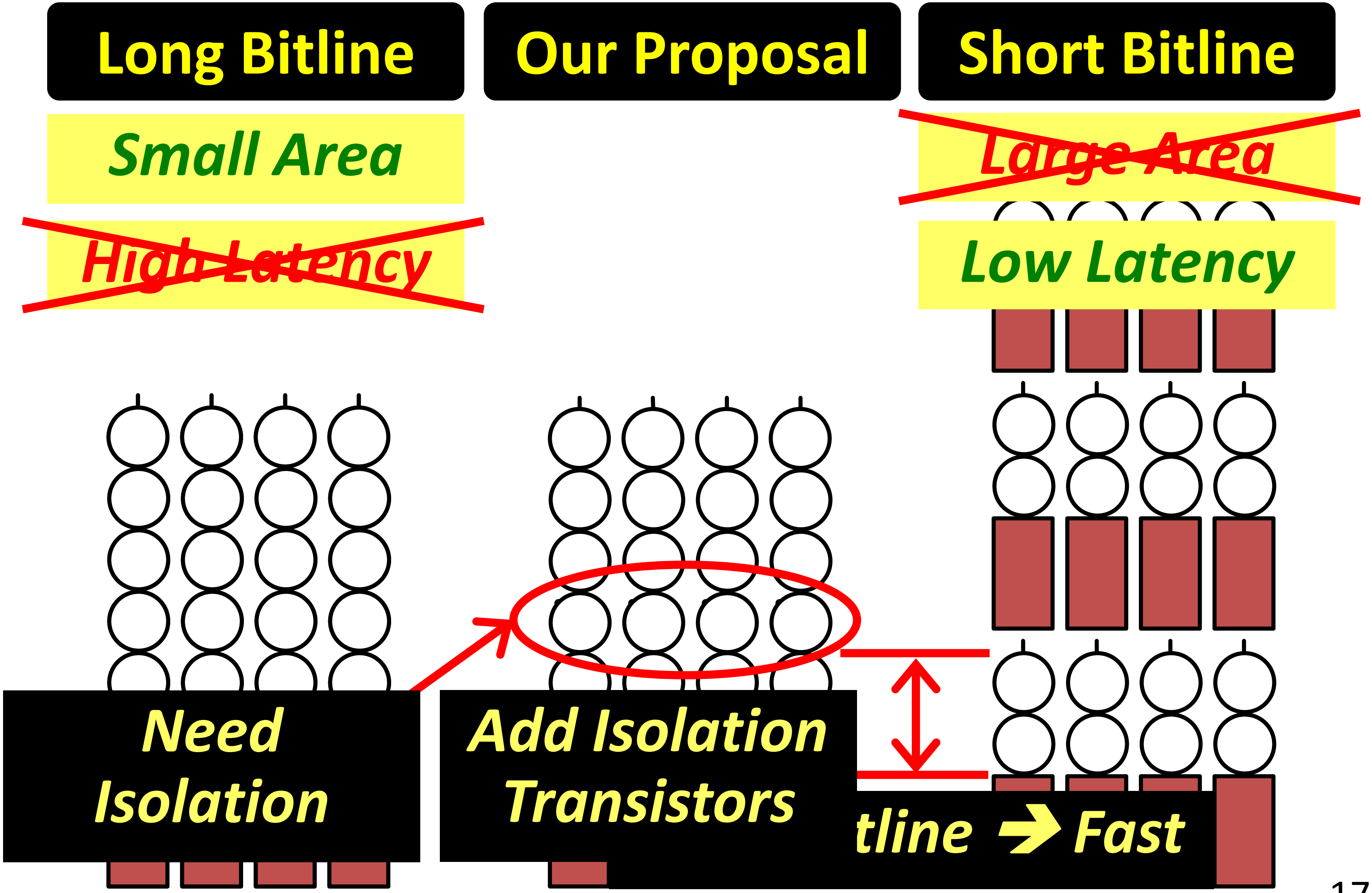
Smaller

Trade-Off: Area vs. Latency

Trade-Off: Area (Die Size) vs. Latency



Approximating the Best of Both Worlds



Long Bitline

Our Proposal

Short Bitline

Small Area

~~High Latency~~

~~Large Area~~

Low Latency

Need Isolation

Add Isolation Transistors

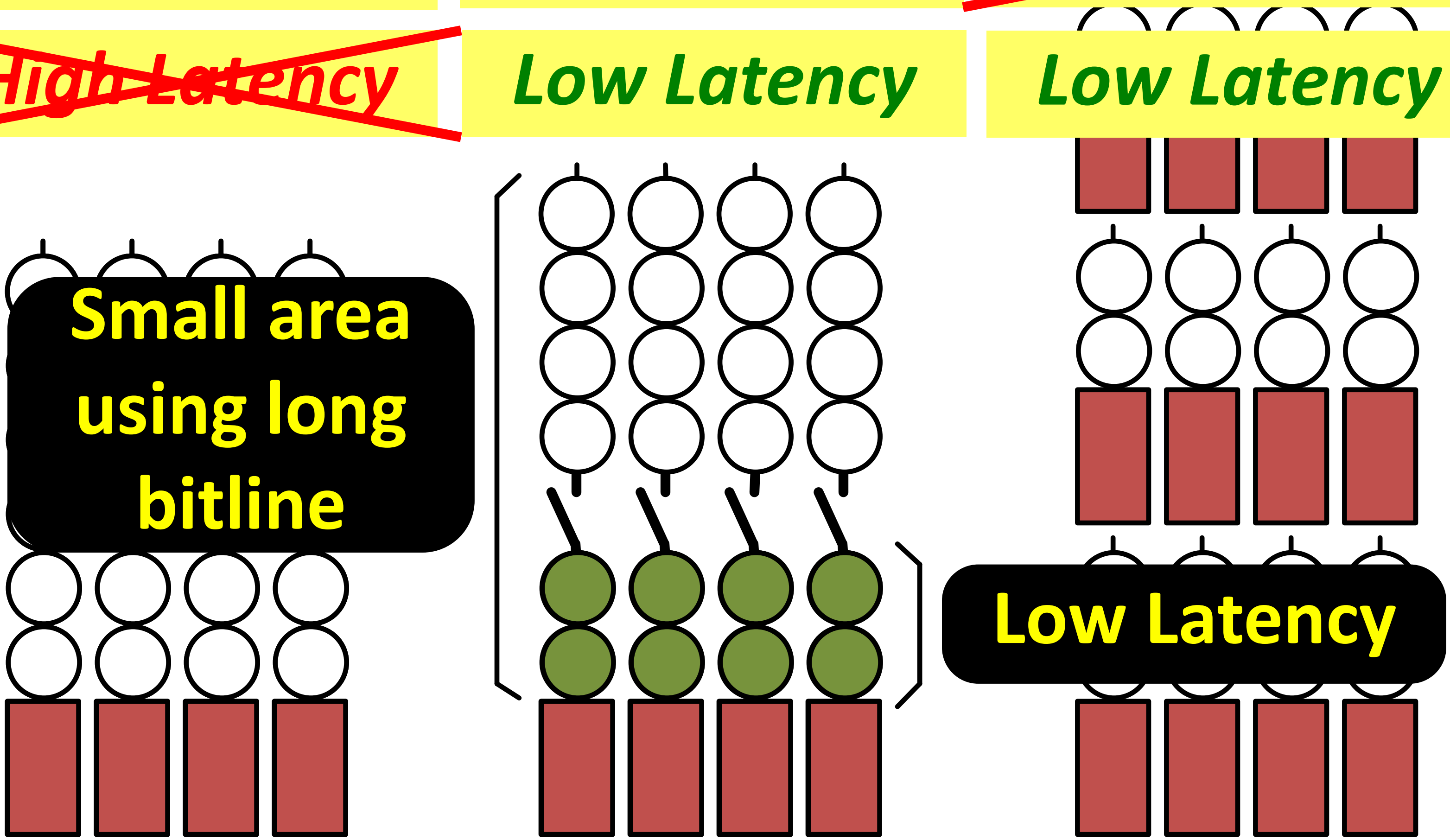
tline → Fast

Approximating the Best of Both Worlds

Long Bitlin Tiered-Latency DRAM ort Bitline

Small Area | *Small Area* | *~~Large Area~~*

~~High Latency~~ | *Low Latency* | *Low Latency*

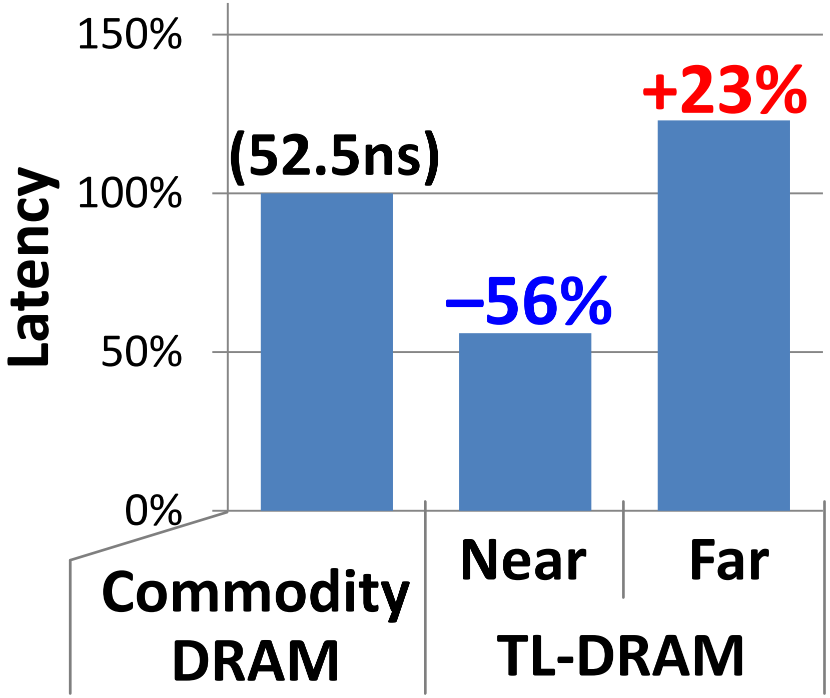


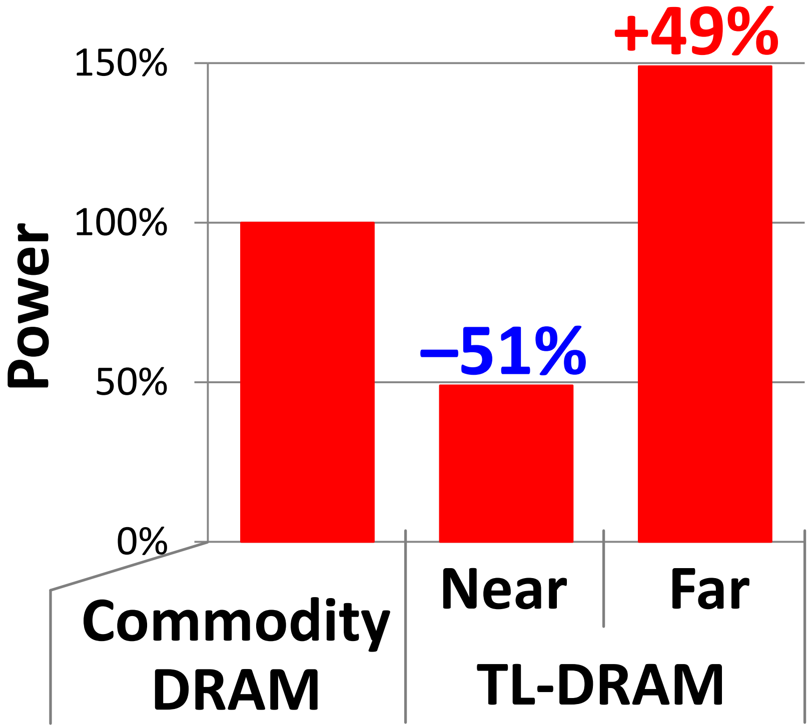
Small area using long bitline

Low Latency

Commodity DRAM vs. TL-DRAM [HPCA 2013]

- **DRAM Latency** (tRC)
- **DRAM Power**

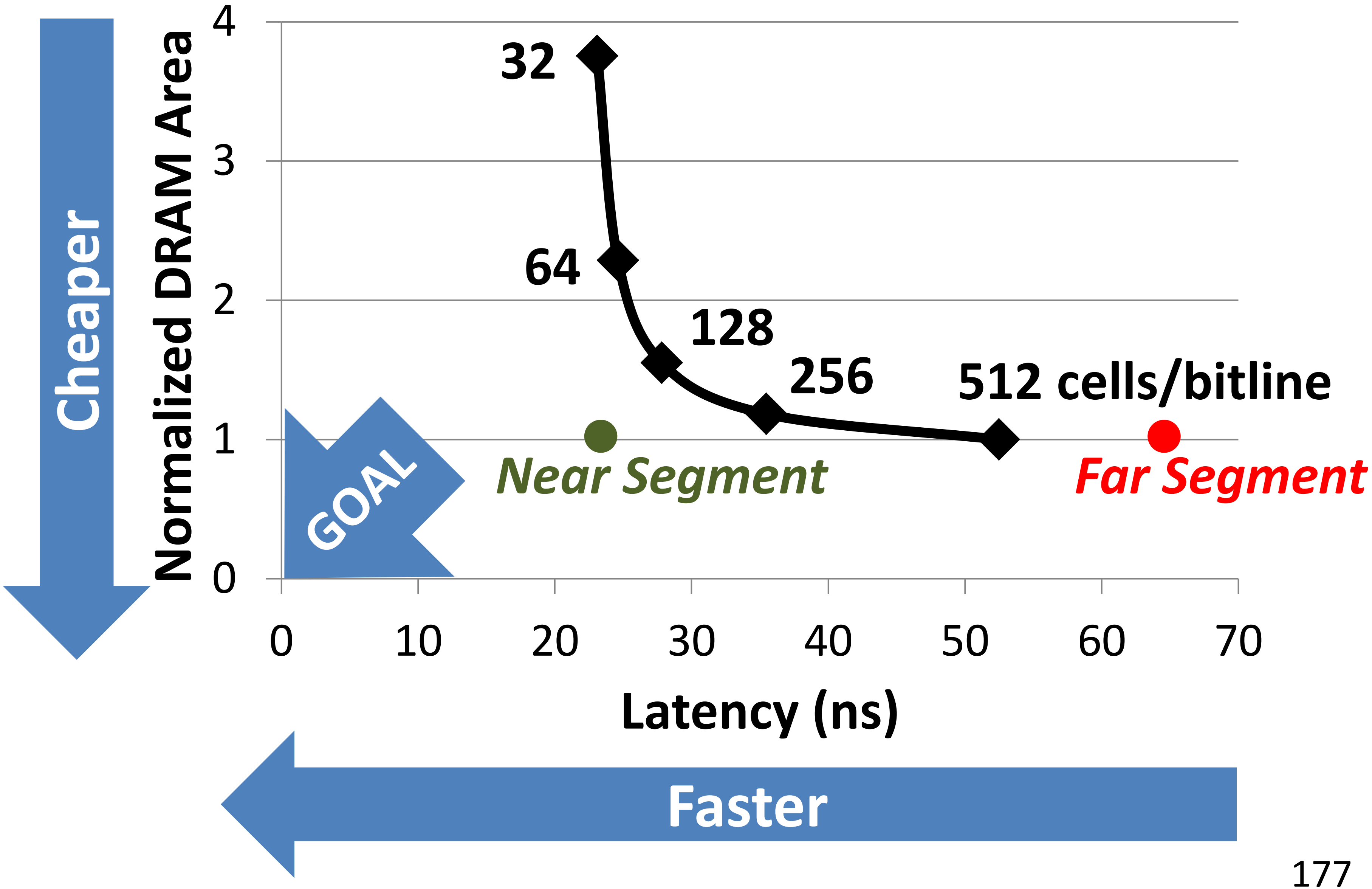




- **DRAM Area Overhead**

  ~3%: mainly due to the isolation transistors

Trade-Off: Area (Die-Area) vs. Latency



Leveraging Tiered-Latency DRAM

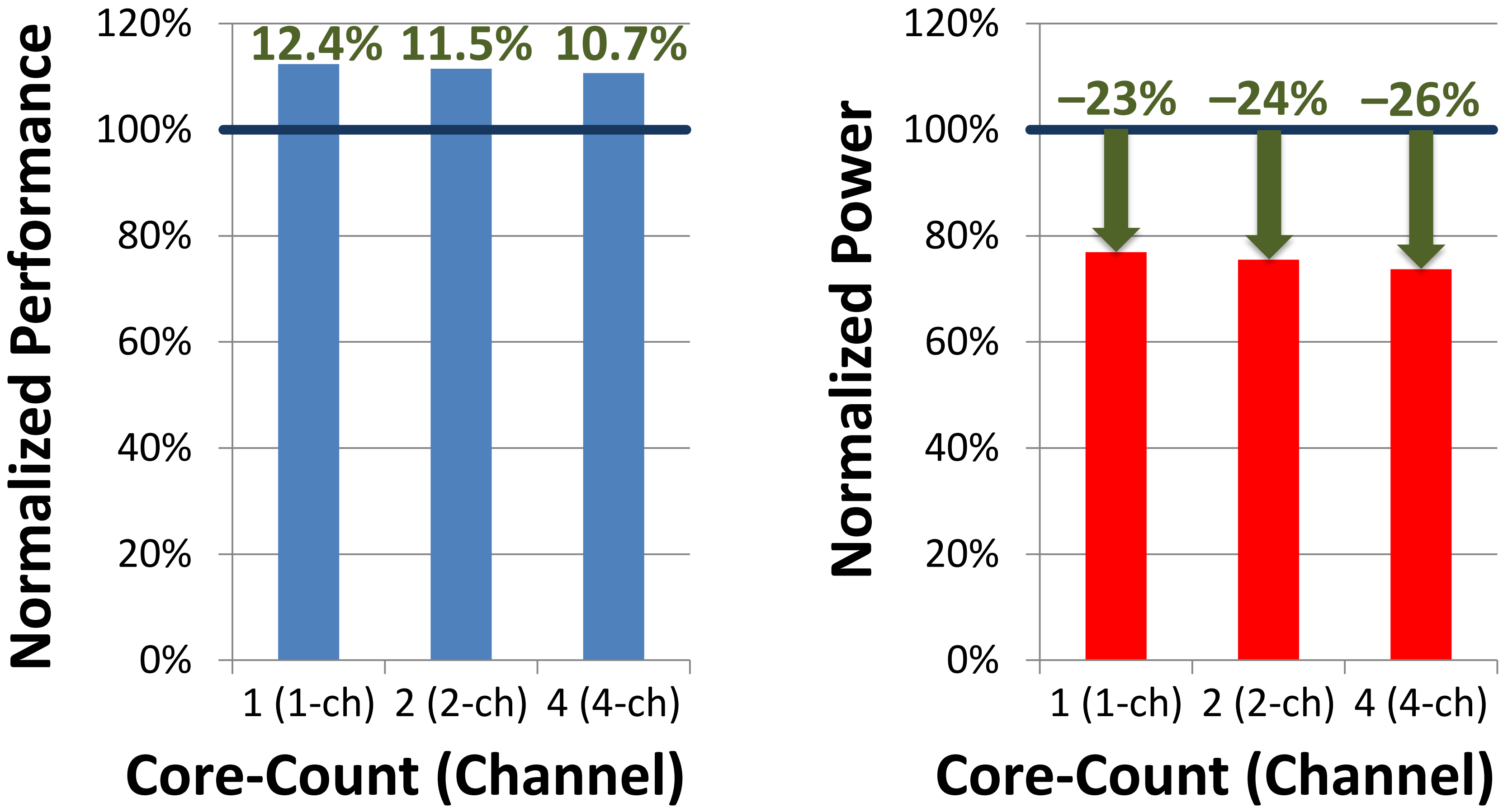
- TL-DRAM is a ***substrate*** that can be leveraged by the hardware and/or software

- Many potential uses

1. Use near segment as hardware-managed ***inclusive*** cache to far segment
2. Use near segment as hardware-managed ***exclusive*** cache to far segment
3. Profile-based page mapping by operating system
4. Simply replace DRAM with TL-DRAM

Lee+, "Tiered-Latency DRAM: A Low Latency and Low Cost DRAM Architecture," HPCA 2013.

Performance & Power Consumption



Using near segment as a cache improves performance and reduces power consumption

Lee+, "Tiered-Latency DRAM: A Low Latency and Low Cost DRAM Architecture," HPCA 2013.

More on PIM

Eliminating the Adoption Barriers

How to Enable Adoption of Processing in Memory

Barriers to Adoption of PIM

1. Functionality of and applications for PIM

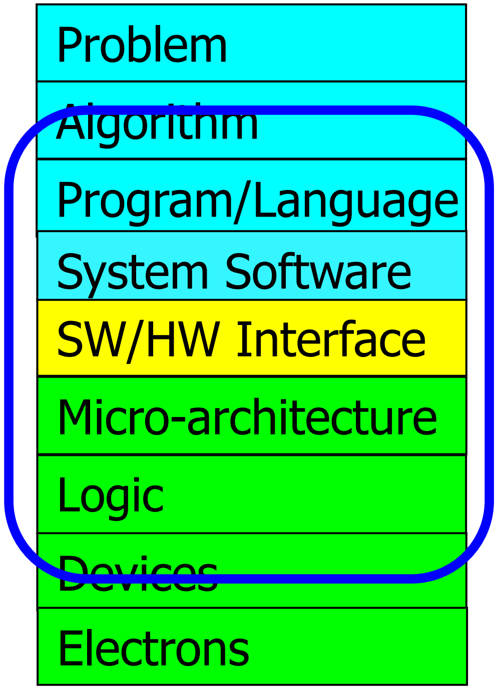
2. Ease of programming (interfaces and compiler/HW support)

3. System support: coherence & virtual memory

4. Runtime systems for adaptive scheduling, data mapping, access/sharing control

5. Infrastructures to assess benefits and feasibility

We Need to Revisit the Entire Stack



Problem

Algorithm

Program/Language

System Software

SW/HW Interface

Micro-architecture

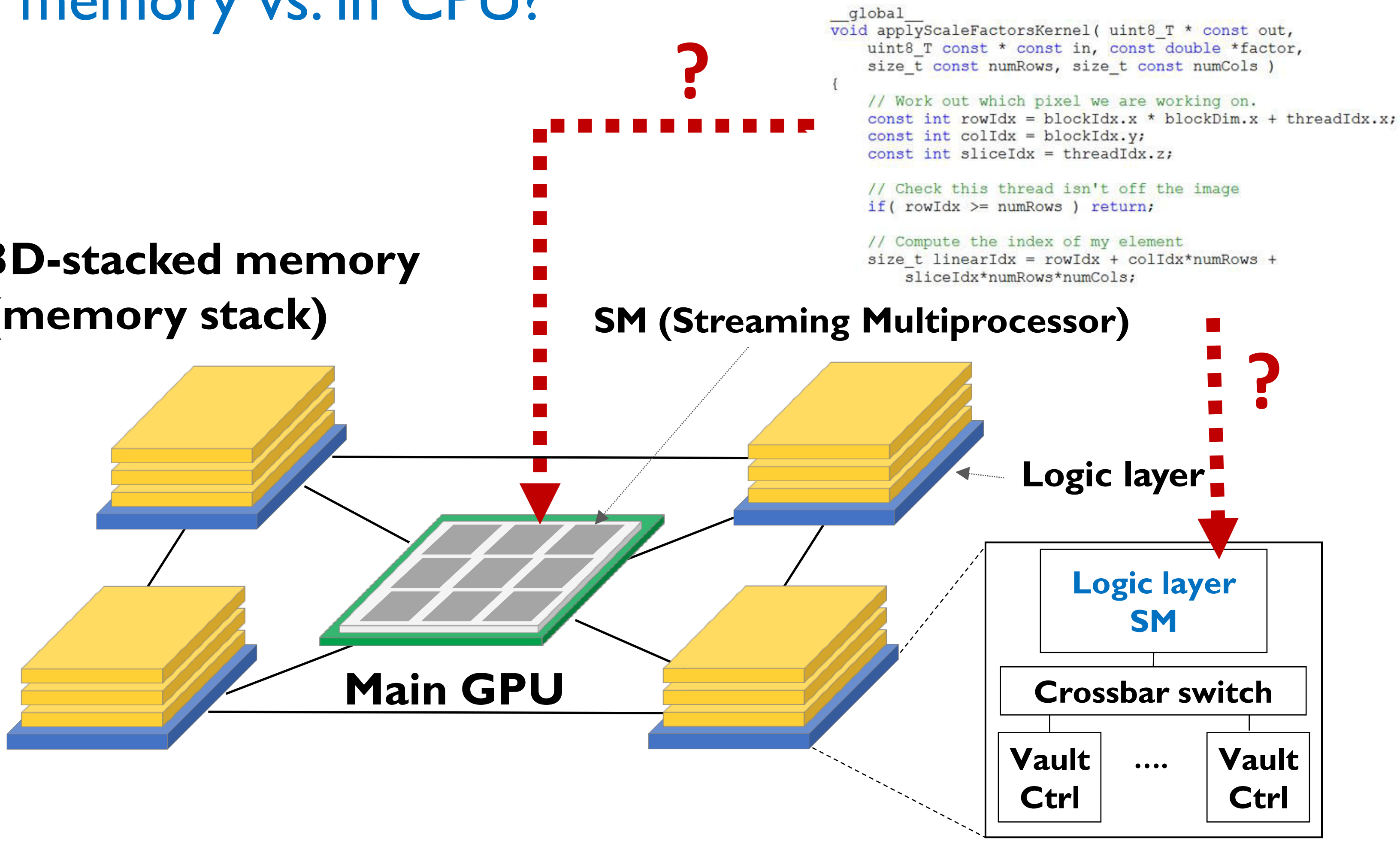
Logic

Devices

Electrons

Key Challenge 1: Code Mapping

- **Challenge 1:** Which operations should be executed in memory vs. in CPU?



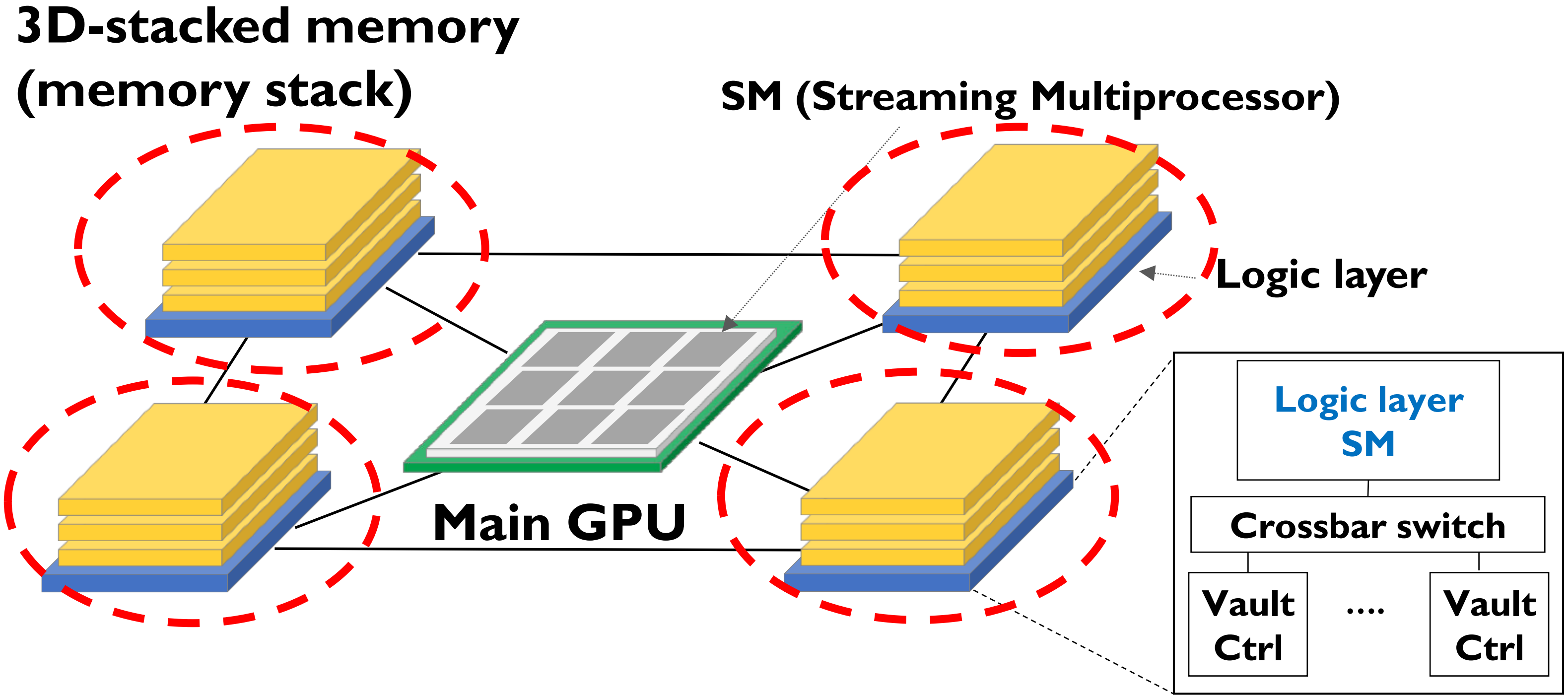
```
__global__
void applyScaleFactorsKernel( uint8_T * const out,
    uint8_T const * const in, const double *factor,
    size_t const numRows, size_t const numCols )
{
    // Work out which pixel we are working on.
    const int rowIdx = blockIdx.x * blockDim.x + threadIdx.x;
    const int colIdx = blockIdx.y;
    const int sliceIdx = threadIdx.z;

    // Check this thread isn't off the image
    if( rowIdx >= numRows ) return;

    // Compute the index of my element
    size_t linearIdx = rowIdx + colIdx*numRows +
        sliceIdx*numRows*numCols;
```

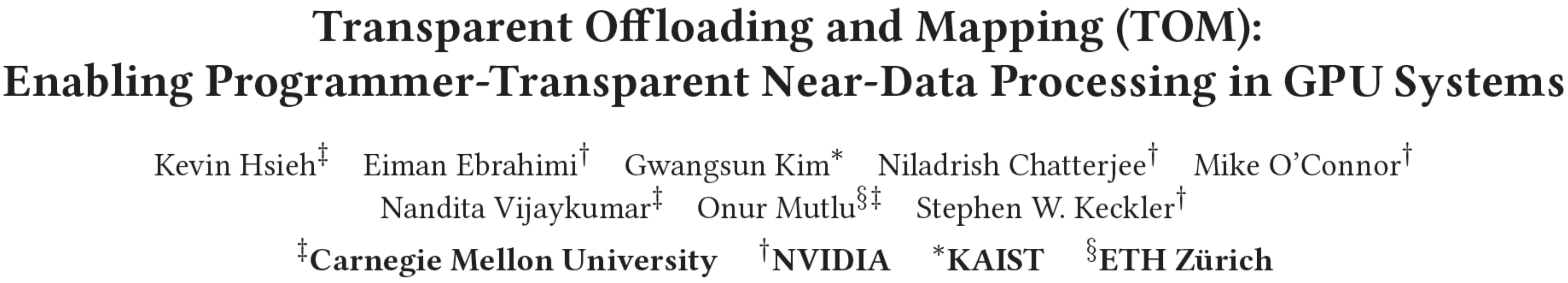
Key Challenge 2: Data Mapping

- **Challenge 2:** How should data be mapped to different 3D memory stacks?



How to Do the Code and Data Mapping?

- Kevin Hsieh, Eiman Ebrahimi, Gwangsun Kim, Niladrish Chatterjee, Mike O'Connor, Nandita Vijaykumar, Onur Mutlu, and Stephen W. Keckler, **"Transparent Offloading and Mapping (TOM): Enabling Programmer-Transparent Near-Data Processing in GPU Systems"**
  Proceedings of the 43rd International Symposium on Computer Architecture (***ISCA***), Seoul, South Korea, June 2016.
  [Slides (pptx) (pdf)]
  [Lightning Session Slides (pptx) (pdf)]

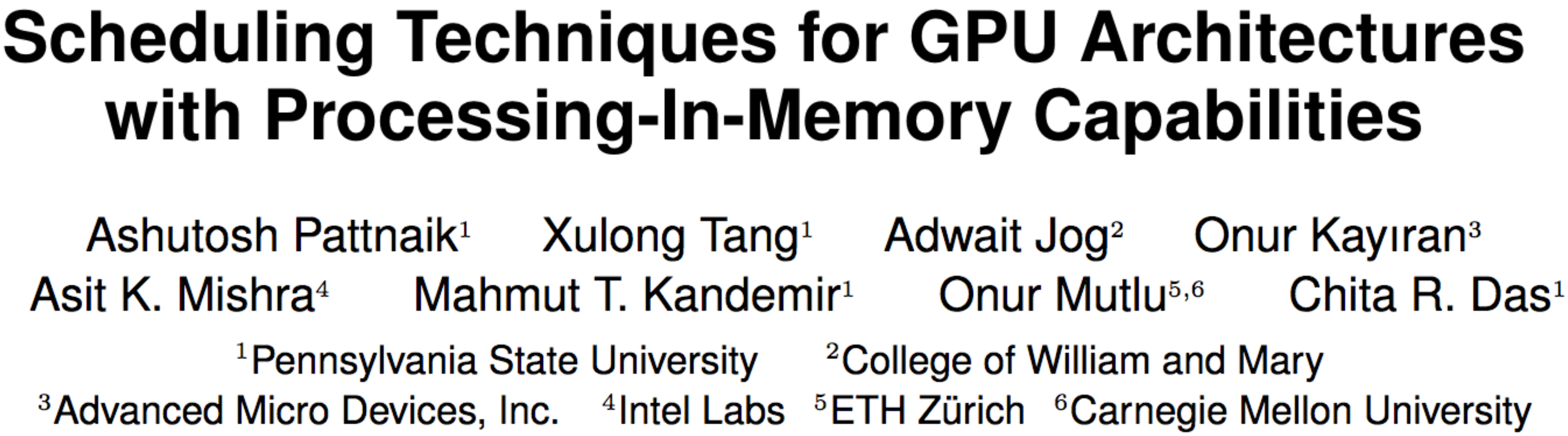


Transparent Offloading and Mapping (TOM):
Enabling Programmer-Transparent Near-Data Processing in GPU Systems

Kevin Hsieh[‡] Eiman Ebrahimi[†] Gwangsun Kim[*] Niladrish Chatterjee[†] Mike O'Connor[†]
Nandita Vijaykumar[‡] Onur Mutlu[§‡] Stephen W. Keckler[†]
[‡]**Carnegie Mellon University** [†]**NVIDIA** [*]**KAIST** [§]**ETH Zürich**

How to Schedule Code?

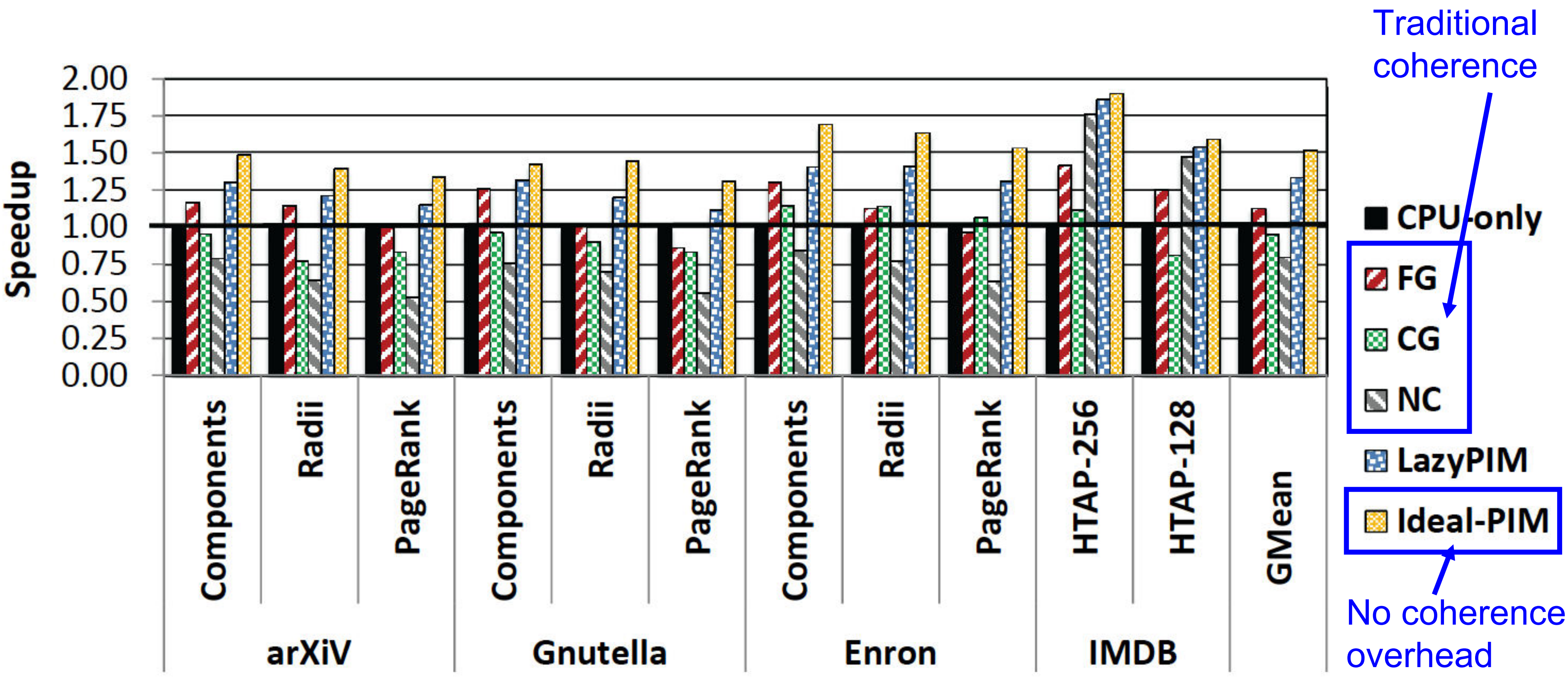
- Ashutosh Pattnaik, Xulong Tang, Adwait Jog, Onur Kayiran, Asit K. Mishra, Mahmut T. Kandemir, Onur Mutlu, and Chita R. Das, **"Scheduling Techniques for GPU Architectures with Processing-In-Memory Capabilities"** *Proceedings of the 25th International Conference on Parallel Architectures and Compilation Techniques (**PACT**)*, Haifa, Israel, September 2016.



Scheduling Techniques for GPU Architectures with Processing-In-Memory Capabilities

Ashutosh Pattnaik[1] Xulong Tang[1] Adwait Jog[2] Onur Kayıran[3]
Asit K. Mishra[4] Mahmut T. Kandemir[1] Onur Mutlu[5,6] Chita R. Das[1]
[1]Pennsylvania State University [2]College of William and Mary
[3]Advanced Micro Devices, Inc. [4]Intel Labs [5]ETH Zürich [6]Carnegie Mellon University

Challenge: Coherence for Hybrid CPU-PIM Apps

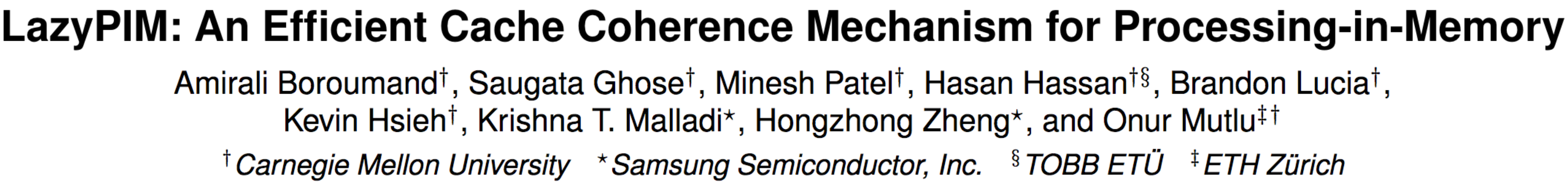


Traditional coherence

No coherence overhead

How to Maintain Coherence?

- Amirali Boroumand, Saugata Ghose, Minesh Patel, Hasan Hassan, Brandon Lucia, Kevin Hsieh, Krishna T. Malladi, Hongzhong Zheng, and Onur Mutlu,
  "LazyPIM: An Efficient Cache Coherence Mechanism for Processing-in-Memory"
  IEEE Computer Architecture Letters ***(CAL)***, June 2016.

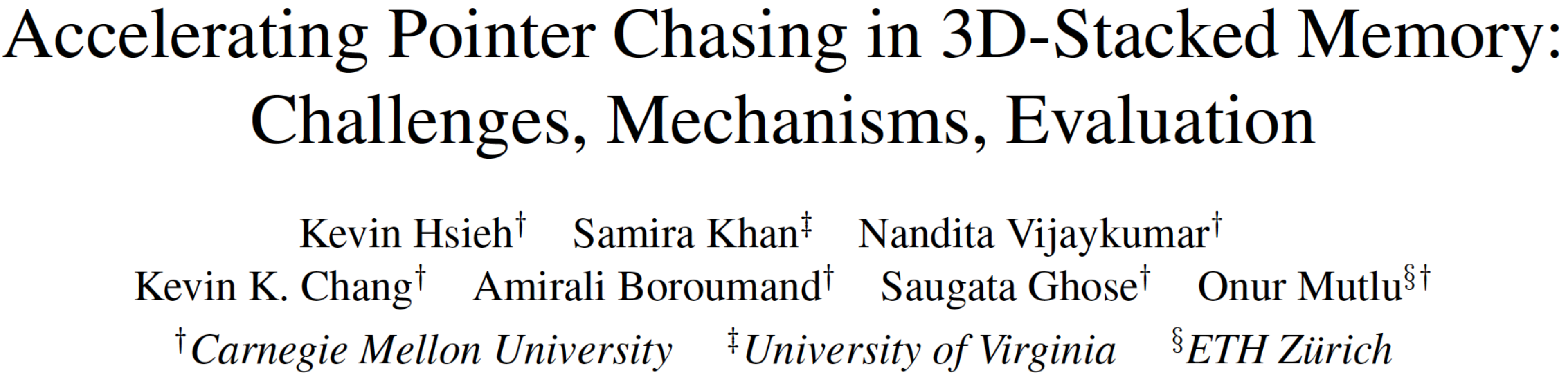


LazyPIM: An Efficient Cache Coherence Mechanism for Processing-in-Memory

Amirali Boroumand[†], Saugata Ghose[†], Minesh Patel[†], Hasan Hassan[†§], Brandon Lucia[†],
Kevin Hsieh[†], Krishna T. Malladi[⋆], Hongzhong Zheng[⋆], and Onur Mutlu[‡†]
[†] *Carnegie Mellon University* [⋆] *Samsung Semiconductor, Inc.* [§] *TOBB ETÜ* [‡] *ETH Zürich*

How to Support Virtual Memory?

- Kevin Hsieh, Samira Khan, Nandita Vijaykumar, Kevin K. Chang, Amirali Boroumand, Saugata Ghose, and Onur Mutlu, **"Accelerating Pointer Chasing in 3D-Stacked Memory: Challenges, Mechanisms, Evaluation"** *Proceedings of the 34th IEEE International Conference on Computer Design* (***ICCD***), Phoenix, AZ, USA, October 2016.



Accelerating Pointer Chasing in 3D-Stacked Memory: Challenges, Mechanisms, Evaluation

Kevin Hsieh[†] Samira Khan[‡] Nandita Vijaykumar[†]
Kevin K. Chang[†] Amirali Boroumand[†] Saugata Ghose[†] Onur Mutlu[§†]
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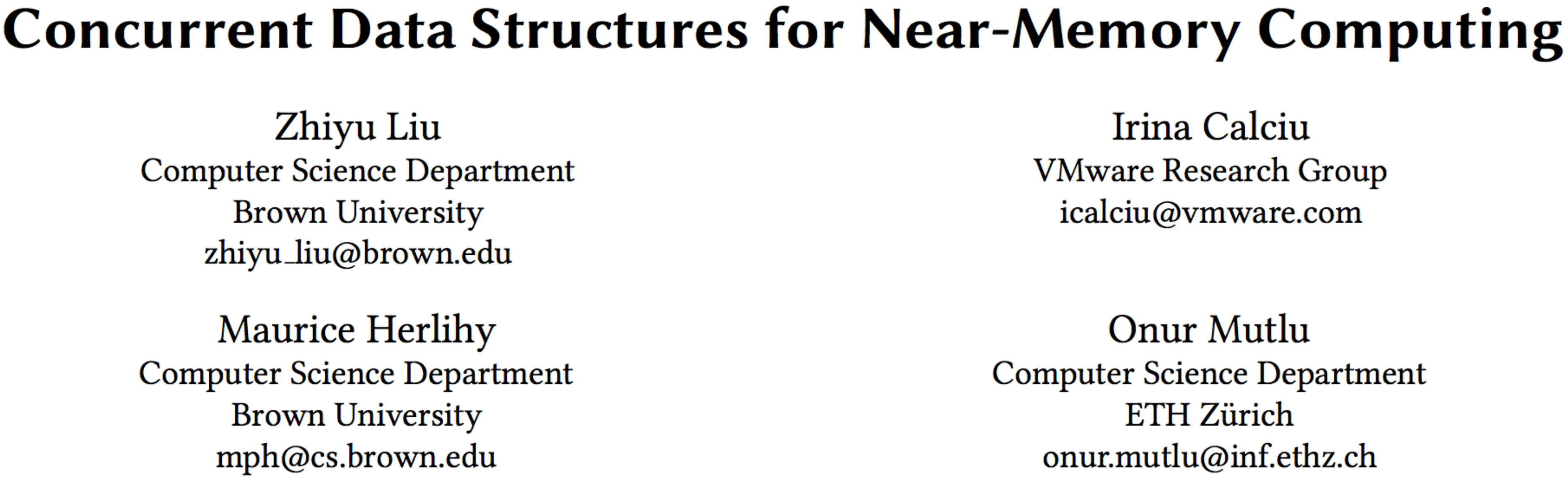
How to Design Data Structures for PIM?

- Zhiyu Liu, Irina Calciu, Maurice Herlihy, and Onur Mutlu, **"Concurrent Data Structures for Near-Memory Computing"** *Proceedings of the 29th ACM Symposium on Parallelism in Algorithms and Architectures* (***SPAA***), Washington, DC, USA, July 2017. [Slides (pptx) (pdf)]



Concurrent Data Structures for Near-Memory Computing

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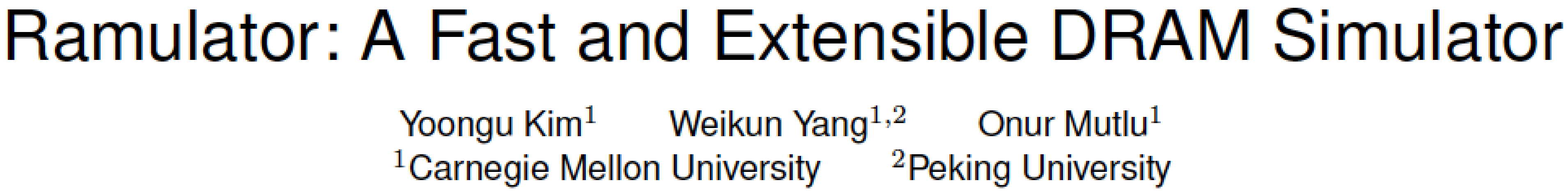
Simulation Infrastructures for PIM

- Ramulator extended for PIM
  - Flexible and extensible DRAM simulator
  - Can model many different memory standards and proposals
  - Kim+, "**Ramulator: A Flexible and Extensible DRAM Simulator**", IEEE CAL 2015.
  - https://github.com/CMU-SAFARI/ramulator

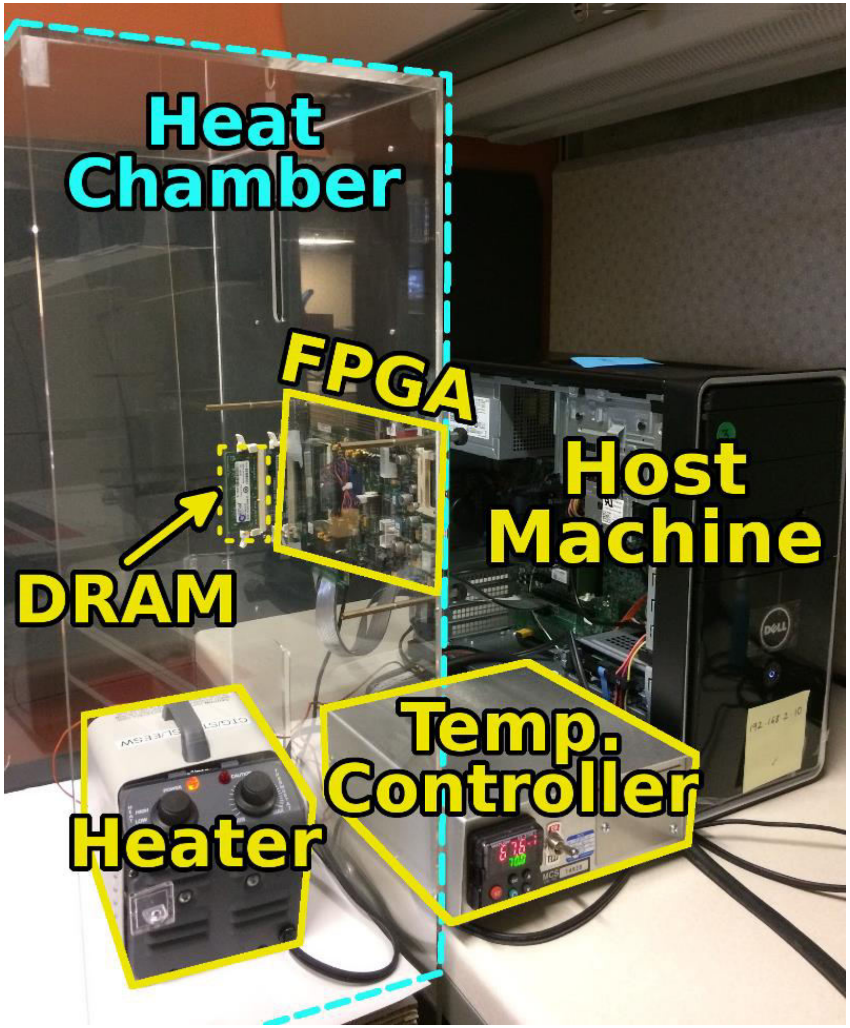


Ramulator: A Fast and Extensible DRAM Simulator

Yoongu Kim[1] Weikun Yang[1,2] Onur Mutlu[1]
[1]Carnegie Mellon University [2]Peking University

An FPGA-based Test-bed for PIM?

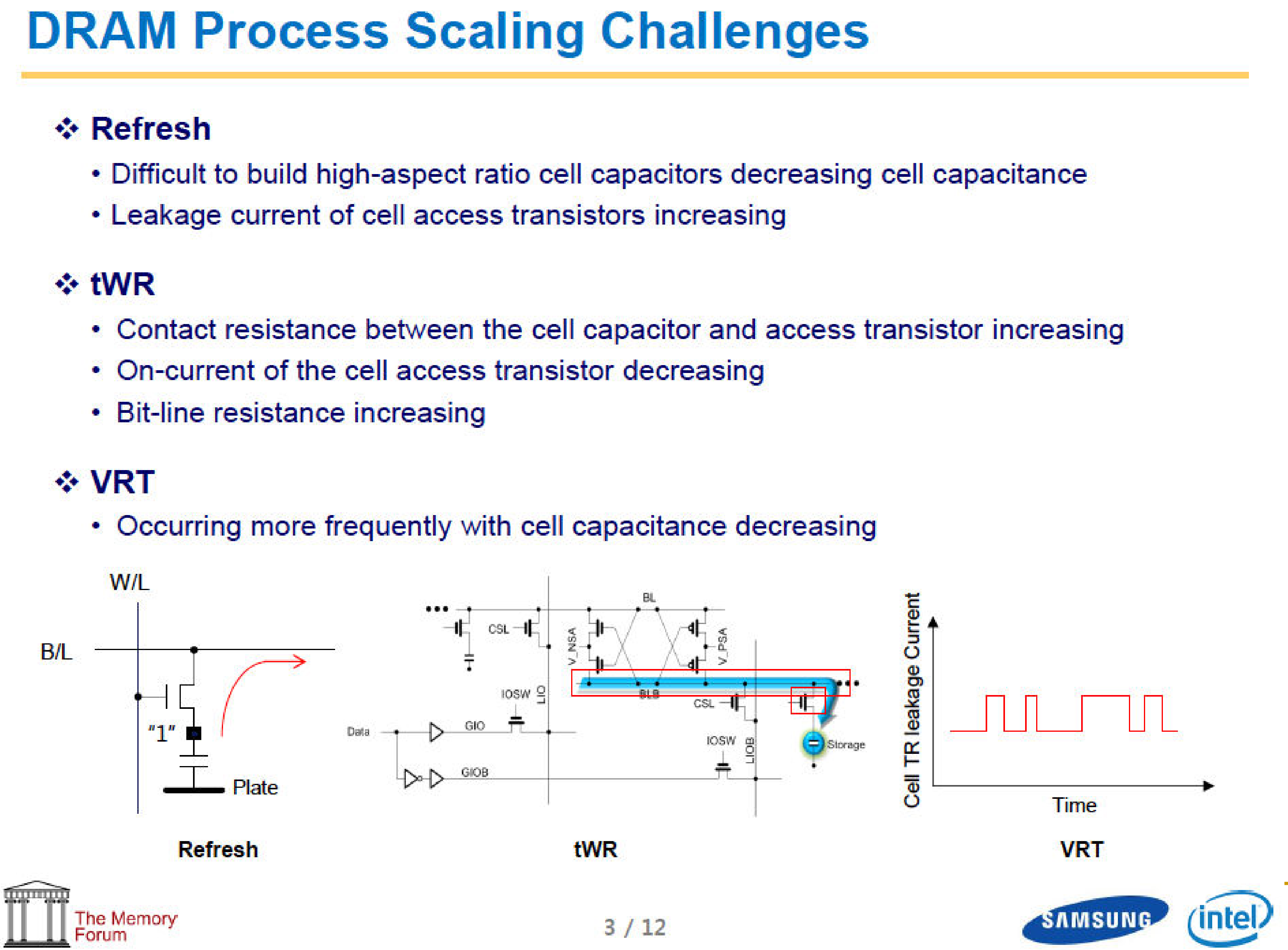
- Hasan Hassan et al., **SoftMC: A Flexible and Practical Open-Source Infrastructure for Enabling Experimental DRAM Studies** HPCA 2017.



- **Flexible**
- **Easy to Use (C++ API)**
- **Open-source**

github.com/CMU-SAFARI/SoftMC

Industry Is Writing Papers About It, Too



DRAM Process Scaling Challenges

- **Refresh**
  - Difficult to build high-aspect ratio cell capacitors decreasing cell capacitance
  - Leakage current of cell access transistors increasing
- **tWR**
  - Contact resistance between the cell capacitor and access transistor increasing
  - On-current of the cell access transistor decreasing
  - Bit-line resistance increasing
- **VRT**
  - Occurring more frequently with cell capacitance decreasing

Refresh **tWR** **VRT**

The Memory Forum

3 / 12

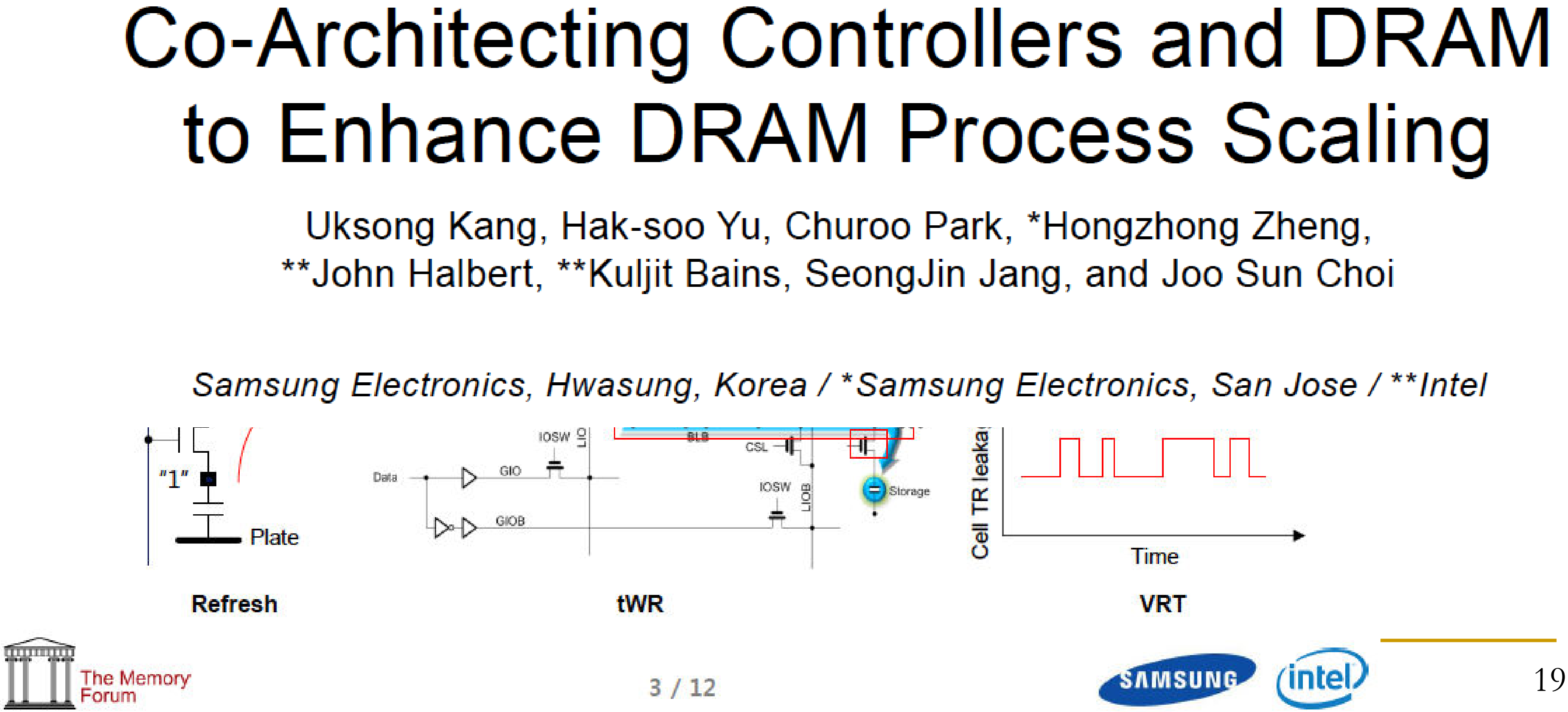
Industry Is Writing Papers About It, Too

DRAM Process Scaling Challenges

❖ **Refresh**

- Difficult to build high-aspect ratio cell capacitors decreasing cell capacitance

THE MEMORY FORUM 2014



Co-Architecting Controllers and DRAM to Enhance DRAM Process Scaling

Uksong Kang, Hak-soo Yu, Churoo Park, *Hongzhong Zheng,
**John Halbert, **Kuljit Bains, SeongJin Jang, and Joo Sun Choi

*Samsung Electronics, Hwasung, Korea / *Samsung Electronics, San Jose / **Intel*

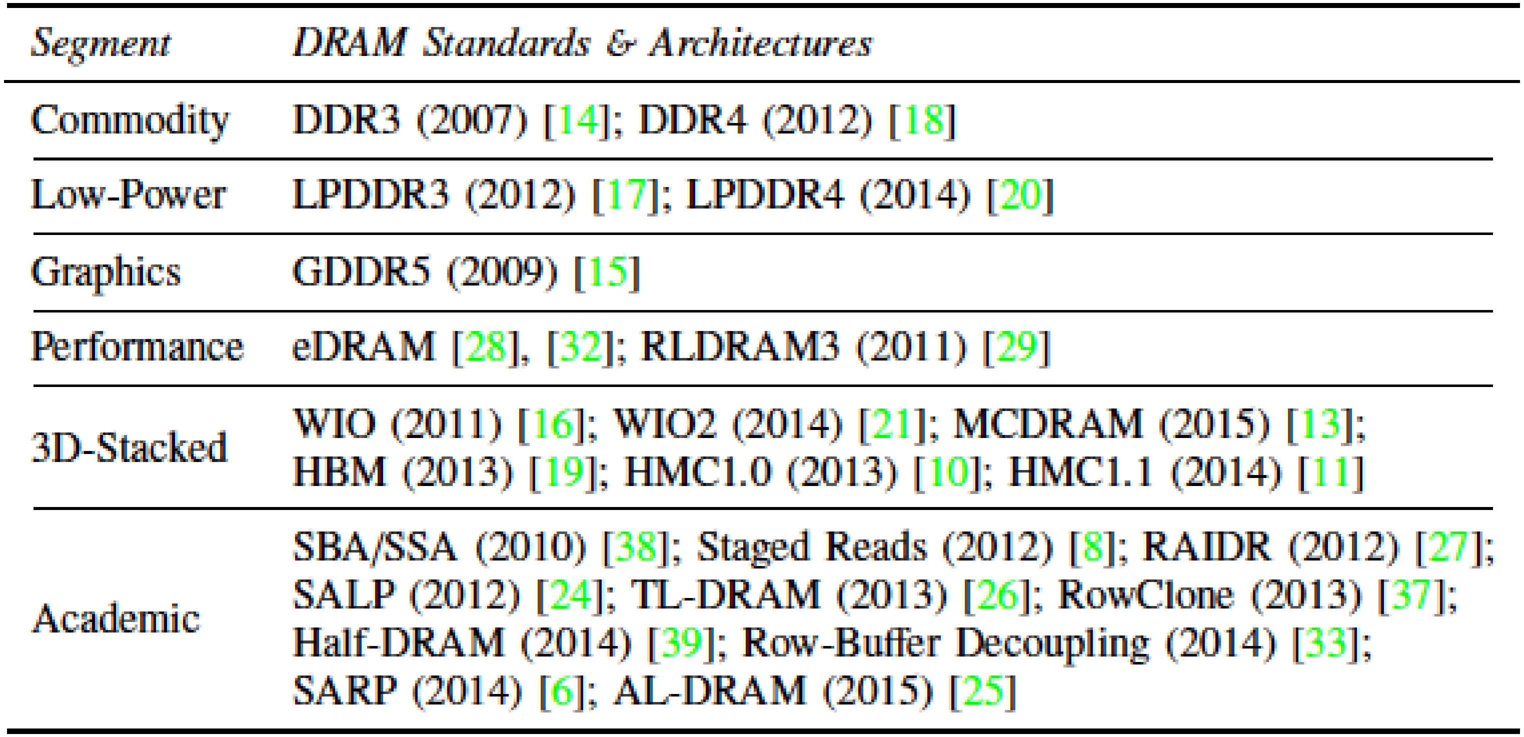
3 / 12

Ramulator: A Fast and Extensible DRAM Simulator

[IEEE Comp Arch Letters'15]

Ramulator Motivation

- DRAM and Memory Controller landscape is changing
- Many new and upcoming standards
- Many new controller designs
- A fast and easy-to-extend simulator is very much needed

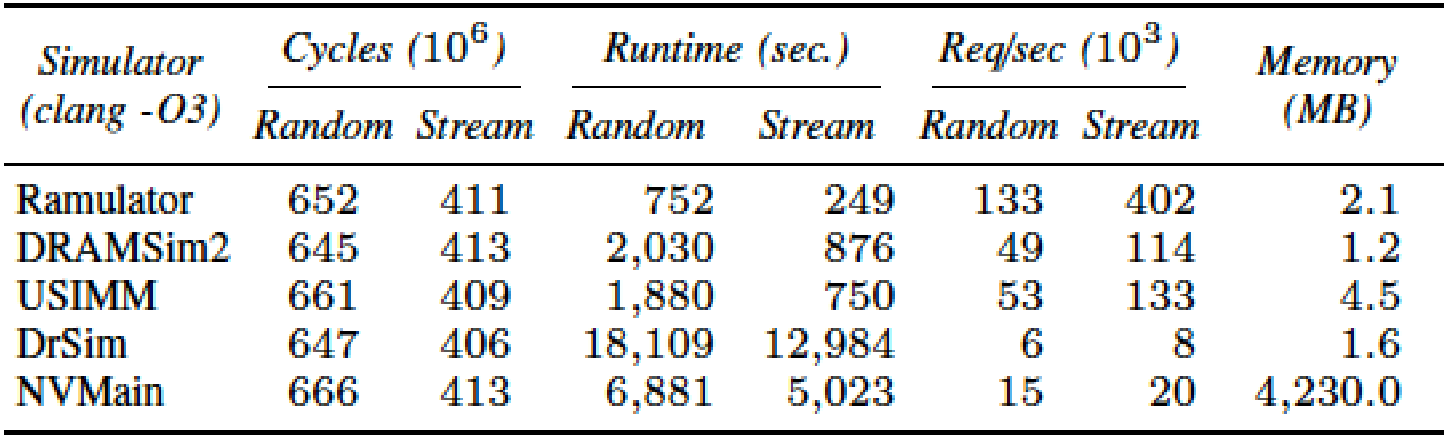


Segment	*DRAM Standards & Architectures*
Commodity	DDR3 (2007) [14]; DDR4 (2012) [18]
Low-Power	LPDDR3 (2012) [17]; LPDDR4 (2014) [20]
Graphics	GDDR5 (2009) [15]
Performance	eDRAM [28], [32]; RLDRAM3 (2011) [29]
3D-Stacked	WIO (2011) [16]; WIO2 (2014) [21]; MCDRAM (2015) [13]; HBM (2013) [19]; HMC1.0 (2013) [10]; HMC1.1 (2014) [11]
Academic	SBA/SSA (2010) [38]; Staged Reads (2012) [8]; RAIDR (2012) [27]; SALP (2012) [24]; TL-DRAM (2013) [26]; RowClone (2013) [37]; Half-DRAM (2014) [39]; Row-Buffer Decoupling (2014) [33]; SARP (2014) [6]; AL-DRAM (2015) [25]

Table 1. Landscape of DRAM-based memory

Ramulator

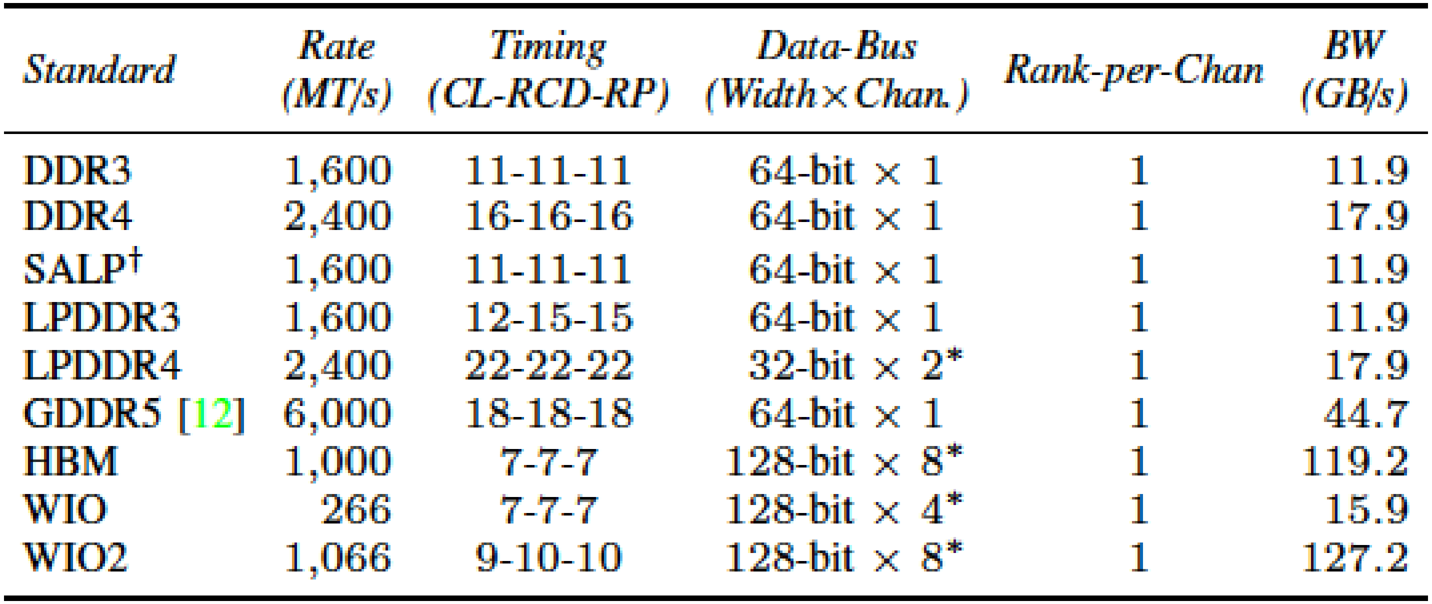
- Provides out-of-the box support for many DRAM standards:
  - DDR3/4, LPDDR3/4, GDDR5, WIO1/2, HBM, plus new proposals (SALP, AL-DRAM, TLDRAM, RowClone, and SARP)
- ~2.5X faster than fastest open-source simulator
- Modular and extensible to different standards



Simulator (clang -O3)	*Cycles (10^6)*		*Runtime (sec.)*		*Req/sec (10^3)*		*Memory (MB)*
	Random	*Stream*	*Random*	*Stream*	*Random*	*Stream*	
Ramulator	652	411	752	249	133	402	2.1
DRAMSim2	645	413	2,030	876	49	114	1.2
USIMM	661	409	1,880	750	53	133	4.5
DrSim	647	406	18,109	12,984	6	8	1.6
NVMain	666	413	6,881	5,023	15	20	4,230.0

Table 3. Comparison of five simulators using two traces

Case Study: Comparison of DRAM Standards



Standard	*Rate (MT/s)*	*Timing (CL-RCD-RP)*	*Data-Bus (Width×Chan.)*	*Rank-per-Chan*	*BW (GB/s)*
DDR3	1,600	11-11-11	64-bit × 1	1	11.9
DDR4	2,400	16-16-16	64-bit × 1	1	17.9
SALP†	1,600	11-11-11	64-bit × 1	1	11.9
LPDDR3	1,600	12-15-15	64-bit × 1	1	11.9
LPDDR4	2,400	22-22-22	32-bit × 2*	1	17.9
GDDR5 [12]	6,000	18-18-18	64-bit × 1	1	44.7
HBM	1,000	7-7-7	128-bit × 8*	1	119.2
WIO	266	7-7-7	128-bit × 4*	1	15.9
WIO2	1,066	9-10-10	128-bit × 8*	1	127.2

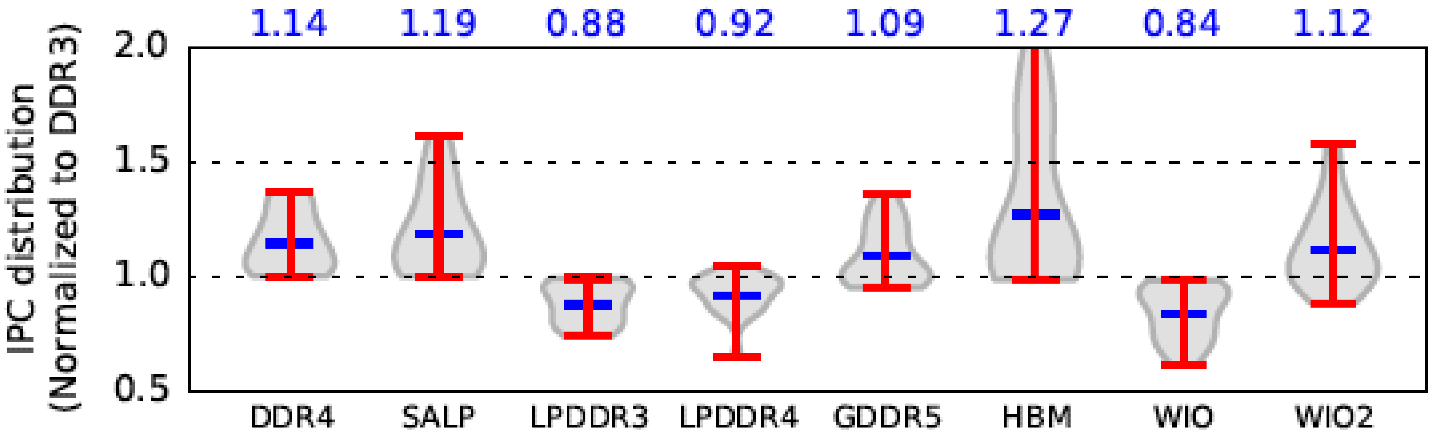


Figure 2. Performance comparison of DRAM standards

Across 22 workloads, simple CPU model

Ramulator Paper and Source Code

- Yoongu Kim, Weikun Yang, and Onur Mutlu, **"Ramulator: A Fast and Extensible DRAM Simulator"** *IEEE Computer Architecture Letters* (***CAL***), March 2015. [Source Code]

- Source code is released under the liberal MIT License
  - https://github.com/CMU-SAFARI/ramulator

End of Backup Slides

Brief Self Introduction

- Onur Mutlu
  - Full Professor @ ETH Zurich CS, since September 2015
  - Strecker Professor @ Carnegie Mellon University ECE/CS, 2009-2016, 2016-…
  - PhD from UT-Austin, worked @ Google, VMware, Microsoft Research, Intel, AMD
  - https://people.inf.ethz.ch/omutlu/
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  - https://people.inf.ethz.ch/omutlu/projects.htm
- Research, Education, Consulting in
  - Computer architecture and systems, bioinformatics
  - Memory and storage systems, emerging technologies
  - Many-core systems, heterogeneous systems, core design
  - Interconnects
  - Hardware/software interaction and co-design (PL, OS, Architecture)
  - Predictable and QoS-aware systems
  - Hardware fault tolerance and security
  - Algorithms and architectures for genome analysis
  - …